

EFR32FG25 Gecko Wireless SoC Family Data Sheet



The EFR32FG25 Gecko SoC is an ideal solution for sub-GHz Wi-SUN applications for metering, lighting, and distribution automation.

The high-performance sub-GHz radio provides long range and is not susceptible to 2.4 GHz interference from technologies like Wi-Fi.

The single die, multi-core solution, provides industry leading security, high throughput, and an integrated power amplifier to enable the next level of secure connectivity for IoT devices.

EFR32FG25 applications include:

- · Smart Electric Metering
- Street Lighting
- · Distribution automation
- Industrial applications
- Municipal infrastructure

KEY FEATURES

- 32-bit ARM® Cortex®-M33 core with 97.5 MHz maximum operating frequency
- Up to 1920 kB of flash and 512 kB of RAM
- Wi-SUN Multi-rate OFDM, FSK, and O-QPSK modulations
- Integrated PA with up to 16 dBm (Sub-GHz) TX power
- · Robust peripheral set and up to 37 GPIO
- Operation up to 125 °C



1. Feature List

The EFR32FG25 highlighted features are listed below.

- Low Power Wireless System-on-Chip
 - High Performance 32-bit 97.5 MHz ARM Cortex[®]-M33 with DSP instruction and floating-point unit for efficient signal processing
 - Up to 1920 kB flash program memory
 - Up to 512 kB RAM data memory
 - Sub-GHz radio operation
 - TX power up to 16 dBm
- Low Energy Consumption
 - 6.3 mA RX current at 924 MHz (400 kbps 4-GFSK)
 - 58.6 mA TX current @ 13 dBm output power at 923.6 MHz with CW from FSK PA
 - 76.6 mA TX current @ 16 dBm output power at 915 MHz with CW from FSK PA
 - 186 mA TX current @ 16 dBm output power at 914 MHz (2.4 Mbps Wi-SUN OFDM Option 1, MCS6)
 - 30 µA/MHz in Active Mode (EM0) at 97.5 MHz
 - 4.6 µA EM2 DeepSleep current (512 kB RAM retention and RTC running from LFXO)
 - 2.6 µA EM2 DeepSleep current (32 kB RAM retention and RTC running from LFRCO)
- High Receiver Performance
 - -107.5 dBm sensitivity @ 300 kbps 923.7 MHz Wi-SUN OFDM Option 3, MCS4
 - -114.5 dBm sensitivity @ 50 kbps 923.6 MHz Wi-SUN FSK #1b with FEC
 - -115.8 dBm sensitivity @ 12.5 kbps 923.6 MHz Wi-SUN OFDM Option 4, MCS0
 - · -125.8 dBm sensitivity @ 4.8 kbps 915 MHz O-QPSK
 - -123.9 dBm sensitivity @ 6.25 kbps 914 MHz SUN O-QPSK
 - -114.6 dBm sensitivity @ 50 kbps 914 MHz Wi-SUN FSK #1b with FEC
 - -95.3 dBm sensitivity @ 2.4 Mbps 914 MHz Wi-SUN OFDM Option 1, MCS6
 - -116.0 dBm sensitivity @ 12.5 kbps 914 MHz Wi-SUN OFDM Option 4, MCS0
 - -114.1 dBm sensitivity @ 50 kbps 866.5 MHz Wi-SUN FSK #1a with FEC
 - -113.2 dBm sensitivity @ 50 kbps 866.5 MHz OFDM Option 4, MCS2
 - -114.5 dBm sensitivity @ 50 kbps 490 MHz OFDM Option 4, MCS2

Supported Modulation Format

- Wi-SUN MR OFDM MCS 0-6 (all 4 Options)
- 802.15.4 SUN MR O-QPSK with DSSS
- Wi-SUN FSK
- 2 (G)FSK with fully configurable shaping
- (G)MSK
- Protocol Support
 - Proprietary
 - Wi-SUN

Wide selection of MCU peripherals

- Analog to Digital Converter (ADC)
 - 12-bit @ 1 Msps
 - 16-bit @ 76.9 ksps
- 2 × Analog Comparator (ACMP)
- Digital to Analog Converter (VDAC) with two channels
- Low-Energy Sensor Interface (LESENSE)
- Up to 37 General Purpose I/O pins with output state retention and asynchronous interrupts
- 16 Channel DMA Controller
- 12 Channel Peripheral Reflex System (PRS)
- 6 × 16-bit Timer/Counter with 3 Compare/Capture/PWM channels
- 2 × 32-bit Timer/Counter with 3 Compare/Capture/PWM channels
- 32-bit Real Time Counter
- · 24-bit Low Energy Timer for waveform generation
- 2 × Watchdog Timer
- 1 × USB2.0 Full Speed port, Device only
- 5 × EUSART (Enhanced Universal Synchronous/Asynchronous Receiver/Transmitter)
 - EUSART0 operates in EM2
 - · SPI and IrDA supported by EUSART
- 2 × I²C interface with SMBus support
- High Frequency Crystal Oscillator clock sharing using buffered sine wave clock output
- Die temperature sensor with ±2 °C typical accuracy across temperature range

Wide Operating Range

- 1.71 to 3.8 V VDD power supply
- 3.45 to 3.8 V PAVDD power supply for OFDM
- 3.0 to 3.8 V PAVDD power supply without OFDM
- -40 °C to +125 °C
- Secure Vault
 - Hardware Cryptographic Acceleration for AES128/192/256, ChaCha20-Poly1305, SHA-1, SHA-2/256/384/512, ECDSA +ECDH(P-192, P-256, P-384, P-521), Ed25519 and Curve25519, J-PAKE, PBKDF2
 - True Random Number Generator (TRNG)
 - ARM® TrustZone®
 - Secure Boot (Root of Trust Secure Loader)
 - Secure Debug Unlock
 - DPA Countermeasures
 - · Secure Key Management with PUF
 - Anti-Tamper
 - External Tamper Detection with dedicated external Active Tamper I/O pairs for use with tamper shields or protecting PCB traces
 - · Secure Attestation
- Packages
 - QFN56 7 mm × 7 mm × 0.85 mm

2. Ordering Information

Ordering Code	Modem Feature	Max TX Power	Flash (kB)	RAM (kB)	Secure Vault	GPIO	Package / Pinout	Temp Range
EFR32FG25B222F1920IM56-B	OFDMFSKO-QPSK	16 dBm	1920	512	High	36	QFN56 / Clock Out	-40 to 125 °C
EFR32FG25B221F1920IM56-B	OFDMFSKO-QPSK	16 dBm	1920	512	High	37	QFN56 / Standard	-40 to 125 °C
EFR32FG25B212F1920IM56-B	FSKO-QPSK	16 dBm	1920	512	High	36	QFN56 / Clock Out	-40 to 125 °C
EFR32FG25B211F1920IM56-B	FSKO-QPSK	16 dBm	1920	512	High	37	QFN56 / Standard	-40 to 125 °C
EFR32FG25B121F1152IM56-B	OFDMFSKO-QPSK	16 dBm	1152	256	High	37	QFN56 / Standard	-40 to 125 °C
EFR32FG25B111F1152IM56-B	FSKO-QPSK	16 dBm	1152	256	High	37	QFN56 / Standard	-40 to 125 °C
EFR32FG25A221F1920IM56-B	OFDMFSKO-QPSK	16 dBm	1920	512	Mid	37	QFN56 / Standard	-40 to 125 °C
EFR32FG25A211F1920IM56-B	FSKO-QPSK	16 dBm	1920	512	Mid	37	QFN56 / Standard	-40 to 125 °C
EFR32FG25A121F1152IM56-B	OFDMFSKO-QPSK	16 dBm	1152	256	Mid	37	QFN56 / Standard	-40 to 125 °C
EFR32FG25A111F1152IM56-B	FSKO-QPSK	16 dBm	1152	256	Mid	37	QFN56 / Standard	-40 to 125 °C

Table 2.1. Ordering Information



Field	Options
Product Family	EFR32FG25: Wireless Gecko 25 Family
Security	 A: Secure Vault Mid B: Secure Vault High
Features [f1][f2][f3]	 f1 1: 256 kB RAM 2: 512 kB RAM f2 1: FSK / O-QPSK 2: FSK / O-QPSK / OFDM f3 1: No feature enabled 2: High Quality HFCLKOUT Pin Available
Memory	• F: Flash
Size	Memory Size in kBytes
Temperature Grade	• I: -40 to +125 °C
Package	• M : QFN
Pins	Number of Package Pins
Revision	• B: Revision B
Tape & Reel	• R : Tape & Reel (optional)

Figure 2.1. Ordering Code Key

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3. System Overview

3.1 Introduction

The EFR32 product family combines an energy-friendly MCU with a high performance radio transceiver. The devices are well suited for secure connected IoT multi-protocol devices requiring high performance and low energy consumption. This section gives a short introduction to the full radio and MCU system. The detailed functional description can be found in the EFR32xG25 Reference Manual.

A block diagram of the EFR32FG25 family is shown in Figure 3.1 Detailed EFR32FG25 Block Diagram on page 8. The diagram shows a superset of features available on the family, which vary by part number. For more information about specific device features, consult Ordering Information.



Figure 3.1. Detailed EFR32FG25 Block Diagram

3.2 Radio

The Gecko family features two radio transceivers. A hardware modem and high efficiency PA supports proprietary wireless protocols, proprietary FSK, SUN FSK, and proprietary O-QPSK. A highly configurable software defined modem and high linearity PA supports SUN O-QPSK, and SUN OFDM.

3.2.1 Antenna Interface

The Sub-GHz antenna is attached to an RF matching network which interfaces to a single-ended input pin (SUBG_I) that interface directly to the internal LNA input, and two differential output pins (SUBG_ON and SUBG_OP). The SUBG_ON and SUBG_OP pins interface internally to both +16 dBm differential PAs (the constant envelop high efficiency PA, and the high linearity OFDM PA). The matching networks change based on the operating frequency band.

The external components, RF matching network, and power supply connections for the typical applications are shown in later sections.

3.2.2 Fractional-N Frequency Synthesizer

The EFR32FG25 contains a high performance, low phase noise, fully integrated fractional-N frequency synthesizer. The synthesizer is used in receive mode to generate the LO frequency for the down-conversion mixer. It is also used in transmit either as a direct modulation source for constant-envelope modulation or to provide an LO for up-conversion for other modulation schemes.

The fractional-N architecture provides excellent phase noise performance, frequency resolution better than 100 Hz, and low energy consumption. The synthesizer's fast frequency settling allows for very short receiver and transmitter wake up times to reduce system energy consumption.

3.2.3 Receiver Architecture

The EFR32FG25 uses a low-IF receiver architecture, consisting of a Low-Noise Amplifier (LNA) followed by an I/Q down-conversion mixer, employing a crystal reference. The I/Q signals are further filtered and amplified before being sampled by the IF analog-to-digital converter (IFADC).

The IF frequency is configurable from 150 kHz to 1371 kHz. The IF can further be configured for high-side or low-side injection, providing flexibility with respect to known interferers at the image frequency. In some circumstances the receiver will configure with a zero IF for OFDM.

The Automatic Gain Control (AGC) module adjusts the receiver gain to optimize performance and avoid saturation for excellent selectivity and blocking performance. The sub-GHz radio can be calibrated on-demand by the user for the desired frequency band.

Demodulation is performed in the digital domain. The demodulator performs configurable decimation and channel filtering to allow receive bandwidths ranging from 0.1 to 2530 kHz. High carrier frequency and baud rate offsets are tolerated by active estimation and compensation. Advanced features supporting high quality communication under adverse conditions include forward error correction by block and convolutional coding as well as Direct Sequence Spread Spectrum (DSSS).

A Received Signal Strength Indicator (RSSI) is available for signal quality metrics, for level-based proximity detection, and for RF channel access by Collision Avoidance (CA) or Listen Before Talk (LBT) algorithms. An RSSI capture value is associated with each received frame and the dynamic RSSI measurement can be monitored throughout reception.

The EFR32FG25 features two demodulators, one using integrated hardware for efficient FSK reception, and other using I and Q downconverter and firmware configurable demodulator for OFDM reception. Concurrent listening for FSK and OFDM signals is supported for selected PHYs. Once a signal is detected, only one can be demodulated.

3.2.4 Transmitter Architecture

The EFR32FG25 uses a direct-conversion transmitter architecture with two line ups. The first is for constant envelope modulation formats, the modulator controls phase and frequency modulation in the frequency synthesizer. Transmit symbols or chips are optionally shaped by a digital shaping filter. The shaping filter is fully configurable, including the BT product, and can be used to implement Gaussian or Raised Cosine shaping. The second is for complex modulations such as OFDM. This uses an I and Q up converter mixer, and a separate highly linear PA. The linear PA and the constant envelope PA are output on the same external pin, and can be used only one at a time.

Carrier Sense Multiple Access - Collision Avoidance (CSMA-CA) or Listen Before Talk (LBT) algorithms can be automatically timed by the EFR32FG25. These algorithms are typically defined by regulatory standards to improve inter-operability in a given bandwidth between devices that otherwise lack synchronized RF channel access.

3.2.5 Packet and State Trace

The EFR32FG25 Frame Controller has a packet and state trace unit that provides valuable information during the development phase. It features:

- · Non-intrusive trace of transmit data, receive data and state information
- Data observability on a single-pin UART data output, or on a two-pin SPI data output
- Configurable data output bitrate / baudrate
- · Multiplexed transmitted data, received data and state / meta information in a single serial data stream

3.2.6 Data Buffering

The EFR32FG25 features an advanced Radio Buffer Controller (BUFC) capable of handling up to 4 buffers of adjustable size from 64 bytes to 4096 bytes. Each buffer can be used for RX, TX or both. The buffer data is located in RAM, enabling zero-copy operations.

3.2.7 Radio Controller (RAC)

The Radio Controller controls the top level state of the radio subsystem in the EFR32FG25. It performs the following tasks:

- Precisely-timed control of enabling and disabling of the receiver and transmitter circuitry
- · Run-time calibration of receiver, transmitter and frequency synthesizer
- · Detailed frame transmission timing, including optional LBT or CSMA-CA

3.3 General Purpose Input/Output (GPIO)

EFR32FG25 has up to 37 General Purpose Input/Output pins. Each GPIO pin can be individually configured as either an output or input. More advanced configurations including open-drain, open-source, and glitch-filtering can be configured for each individual GPIO pin. The GPIO pins can be overridden by peripheral connections, like SPI communication. Each peripheral connection can be routed to several GPIO pins on the device. The input value of a GPIO pin can be routed through the Peripheral Reflex System to other peripherals. The GPIO subsystem supports asynchronous external pin interrupts.

All of the pins on ports A and port B are EM2 capable. These pins may be used by Low-Energy peripherals in EM2/3 and may also be used as EM2/3 pin wake-ups. Pins on ports C and D are latched/retained in their current state when entering EM2 until EM2 exit upon which internal peripherals could once again drive those pads.

A few GPIOs also have EM4 wake functionality. These pins are listed in the Alternate Function Table.

3.4 Clocking

3.4.1 Clock Management Unit (CMU)

The Clock Management Unit controls oscillators and clocks in the EFR32FG25. Individual enabling and disabling of clocks to all peripheral modules is performed by the CMU. The CMU also controls enabling and configuration of the oscillators. A high degree of flexibility allows software to optimize energy consumption in any specific application by minimizing power dissipation in unused peripherals and oscillators.

3.4.2 Internal and External Oscillators

The EFR32FG25 supports two crystal oscillators and fully integrates four RC oscillators, listed below.

- A high frequency crystal oscillator (HFXO) with integrated load capacitors, tunable in small steps, provides a precise timing reference for the MCU. The HFXO provides excellent RF clocking performance using a 39.0 MHz crystal. An integrated Thermistor Sense can accurately measure the temperature of this crystal. Internal adjustments to clock frequency can be implemented to compensate for crystal frequency shift over temperature. The HFXO can also support an external clock source such as a TCXO for applications that require an extremely accurate clock frequency over temperature. Typical TCXO current drain and start up time are higher than the temperature compensated crystal oscillator option.
- A 32.768 kHz crystal oscillator (LFXO) provides an accurate timing reference for low energy modes.
- An integrated high frequency RC oscillator (HFRCO) is available for the MCU system, when crystal accuracy is not required. The HFRCO employs fast start-up at minimal energy consumption combined with a wide frequency range, from 1 MHz to 80 MHz.
- An integrated fast start-up RC oscillator (FSRCO) that runs at a fixed 20 MHz
- An integrated low frequency 32.768 kHz RC oscillator (LFRCO) for low power operation where high accuracy is not required.
- An integrated ultra-low frequency 1 kHz RC oscillator (ULFRCO) is available to provide a timing reference at the lowest energy consumption in low energy modes.

3.5 Counters/Timers and PWM

3.5.1 Timer/Counter (TIMER)

TIMER peripherals keep track of timing, count events, generate PWM outputs and trigger timed actions in other peripherals through the Peripheral Reflex System (PRS). The core of each TIMER is a 16-bit or 32-bit counter with up to 3 compare/capture channels. Each channel is configurable in one of three modes. In capture mode, the counter state is stored in a buffer at a selected input event. In compare mode, the channel output reflects the comparison of the counter to a programmed threshold value. In PWM mode, the TIMER supports generation of pulse-width modulation (PWM) outputs of arbitrary waveforms defined by the sequence of values written to the compare registers. In addition some timers offer dead-time insertion.

See 3.13 Configuration Summary for information on the feature set of each timer.

3.5.2 Low Energy Timer (LETIMER)

The unique LETIMER is a 24-bit timer that is available in energy mode EM0 Active, EM1 Sleep, EM2 Deep Sleep, and EM3 Stop. This allows it to be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. The LETIMER is connected to the Peripheral Reflex System (PRS), and can be configured to start counting on compare matches from other peripherals such as the Real Time Clock.

3.5.3 System Real Time Clock with Capture (SYSRTC)

The System Real Time Clock (SYSRTC) is a 32-bit counter providing timekeeping down to EM3. The SYSRTC can be clocked by any of the on-board low-frequency oscillators, and it is capable of providing system wake-up at user defined intervals.

3.5.4 Back-Up Real Time Counter (BURTC)

The Back-Up Real Time Counter (BURTC) is a 32-bit counter providing timekeeping in all energy modes, including EM4. The BURTC can be clocked by any of the on-board low-frequency oscillators, and it is capable of providing system wake-up at user-defined intervals.

3.5.5 Watchdog Timer (WDOG)

The watchdog timer can act both as an independent watchdog or as a watchdog synchronous with the CPU clock. It has windowed monitoring capabilities, and can generate a reset or different interrupts depending on the failure mode of the system. The watchdog can also monitor autonomous systems driven by the Peripheral Reflex System (PRS).

3.6 Communications and Other Digital Peripherals

3.6.1 Universal Serial Bus (USB)

The optional USB on chip PHY is a full-speed/low-speed device mode USB 2.0 controller. The USB can be used in device only configurations, and uses PLL0 at 48 MHz based on the 39 MHz crystal oscillator used as reference clock for radio and MCU operation. The USB block supports both full speed (12 MBit/s) and low speed (1.5 MBit/s) operation. The USB device includes an internal dedicated Descriptor-Based Scatter/Gather DMA and supports up to 10 endpoints. Of these, 9 are Bulk endpoints which are configurable as IN or OUT or as interrupt IN endpoints, and endpoint 0 is pre-defined as CTRL IN. The on-chip PHY includes internal pull-up and pull-down resistors. Bus powered device is supported and requires external voltage regulator to supply 3.3 V to IOVDD2 whenever the system is powered. VBUS-sense requires external resistor voltage divider and uses a GPIO. USB Suspend mode, with less than 2.4 mA average current, is supported with radio receive mode at a low enough duty cycle. Radio TX is not supported in USB Suspend. Remote wakeup is supported and will use an EM2 timer.

3.6.2 Enhanced Universal Synchronous/Asynchronous Receiver/Transmitter (EUSART)

The Enhanced Universal Synchronous/Asynchronous Receiver/Transmitter supports full duplex asynchronous UART communication with hardware flow control, RS-485, and IrDA support. The EUSART also supports high-speed SPI. In EM0 and EM1 the EUSART provides a high-speed, buffered communication interface.

When routed to GPIO ports A or B, the EUSART0 may also be used in a low-energy mode and operate in EM2. A 32.768 kHz clock source allows full duplex UART communication up to 9600 baud. EUSART0 can also act as a SPI secondary device in EM2 and EM3, and wake the system when data is received from an external bus controller.

3.6.3 Inter-Integrated Circuit Interface (I²C)

The I²C module provides an interface between the MCU and a serial I²C bus. It is capable of acting as a main or secondary interface and supports multi-drop buses. Standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates from 10 kbit/s up to 1 Mbit/s. Bus arbitration and timeouts are also available, allowing implementation of an SMBus-compliant system. The interface provided to software by the I²C module allows precise timing control of the transmission process and highly automated transfers. Automatic recognition of addresses is provided in active and low energy modes. Note that not all instances of I²C are available in all energy modes.

3.6.4 Peripheral Reflex System (PRS)

The Peripheral Reflex System provides a communication network between different peripheral modules without software involvement. Peripheral modules producing Reflex signals are called producers. The PRS routes Reflex signals from producers to consumer peripherals which in turn perform actions in response. Edge triggers and other functionality such as simple logic operations (AND, OR, NOT) can be applied by the PRS to the signals. The PRS allows peripherals to act autonomously without waking the MCU core, saving power.

3.6.5 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface LESENSETM is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators, ADC, and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable finite state machine which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

3.7 Secure Vault Features

A dedicated hardware secure engine containing its own CPU enables the Secure Vault functions. It isolates cryptographic functions and data from the host Cortex-M33 core, and provides several additional security features. The EFR32FG25 family includes devices with Secure Vault High and Secure Vault Mid capabilities, which are summarized in the table below.

Table 3.1. Secure Vault Features

Feature	Secure Vault Mid	Secure Vault High
True Random Number Generator (TRNG)	Yes	Yes
Secure Boot with Root of Trust and Secure Loader (RTSL)	Yes	Yes
Secure Debug with Lock/Unlock	Yes	Yes
DPA Countermeasures	Yes	Yes
Anti-Tamper		Yes
External Tamper Detect (ETAMPDET)	Yes	Yes
Secure Attestation		Yes
Secure Key Management		Yes
Symmetric Encryption	 AES 128 / 192 / 256 bit ECB, CTR, CBC, CFB, CCM, GCM, CBC-MAC, and GMAC 	 AES 128 / 192 / 256 bit ECB, CTR, CBC, CFB, CCM, GCM, CBC-MAC, and GMAC ChaCha20
Public Key Encryption - ECDSA / ECDH / EdDSA	• p192 and p256	 p192, p256, p384 and p521 Curve25519 (ECDH) Ed25519 (EdDSA)
Key Derivation	ECJ-PAKE p192 and p256	 ECJ-PAKE p192, p256, p384, and p521 PBKDF2 HKDF
Hashes	• SHA-1 • SHA-2/256	 SHA-1 SHA-2 256, 384, and 512 Poly1305

3.7.1 Secure Boot with Root of Trust and Secure Loader (RTSL)

The Secure Boot with RTSL authenticates a chain of trusted firmware that begins from an immutable memory (ROM).

It prevents malware injection, prevents rollback, ensures that only authentic firmware is executed, and protects Over The Air updates.

For more information about this feature, see AN1218: Series 2 Secure Boot with RTSL.

3.7.2 Cryptographic Accelerator

The Cryptographic Accelerator is an autonomous hardware accelerator with Differential Power Analysis (DPA) countermeasures to protect keys.

It supports AES encryption and decryption with 128/192/256-bit keys, ChaCha20 encryption, and Elliptic Curve Cryptography (ECC) to support public key operations, and hashes.

Supported block cipher modes of operation for AES include:

- ECB (Electronic Code Book)
- · CTR (Counter Mode)
- CBC (Cipher Block Chaining)
- CFB (Cipher Feedback)
- GCM (Galois Counter Mode)
- CCM (Counter with CBC-MAC)
- CBC-MAC (Cipher Block Chaining Message Authentication Code)
- GMAC (Galois Message Authentication Code)

The Cryptographic Accelerator accelerates Elliptical Curve Cryptography and supports the NIST (National Institute of Standards and Technology) recommended curves including P-192, P-256, P-384, and P-521 for ECDH (Elliptic Curve Diffie-Hellman) key derivation, and ECDSA (Elliptic Curve Digital Signature Algorithm) sign and verify operations. Also supported is the non-NIST Curve25519 for ECDH and Ed25519 for EdDSA (Edwards-curve Digital Signature Algorithm) sign and verify operations.

Secure Vault also supports ECJ-PAKE (Elliptic Curve variant of Password Authenticated Key Exchange by Juggling) and PBKDF2 (Password-Based Key Derivation Function 2).

Supported hashes include SHA-1, SHA-2/256/384/512 and Poly1305.

This implementation provides a fast and energy efficient solution to state of the art cryptographic needs.

3.7.3 True Random Number Generator

The True Random Number Generator module is a non-deterministic random number generator that harvests entropy from a thermal energy source. It includes start-up health tests for the entropy source as required by NIST SP800-90B and AIS-31 as well as online health tests required for NIST SP800-90C.

The TRNG is suitable for periodically generating entropy to seed an approved pseudo random number generator.

3.7.4 Secure Debug with Lock/Unlock

For obvious security reasons, it is critical for a product to have its debug interface locked before being released in the field.

In addition, Secure Vault High also provides a secure debug unlock function that allows authenticated access based on public key cryptography. This functionality is particularly useful for supporting failure analysis while maintaining confidentiality of IP and sensitive enduser data.

For more information about this feature, see AN1190: Series 2 Secure Debug.

3.7.5 DPA Countermeasures

The AES and ECC accelerators have Differential Power Analysis (DPA) countermeasures support. This makes it very expensive from a time and effort standpoint to use DPA to recover secret keys.

3.7.6 Secure Key Management with PUF

Key material in Secure Vault High products is protected by "key wrapping" with a standardized symmetric encryption mechanism. This method has the advantage of protecting a virtually unlimited number of keys, limited only by the storage that is accessible by the Cortex-M33, which includes off-chip storage as well. The symmetric key used for this wrapping and unwrapping must be highly secure because it can expose all other key materials in the system. The Secure Vault Key Management system uses a Physically Unclonable Function (PUF) to generate a persistent device-unique seed key on power up to dynamically generate this critical wrapping/unwrapping key which is only visible to the AES encryption engine and is not retained when the device loses power.

3.7.7 Anti-Tamper

Secure Vault High devices provide internal tamper protection which monitors parameters such as voltage, temperature, and electromagnetic pulses as well as detecting tamper of the security sub-system itself. Additionally, 8 external configurable tamper pins support external tamper sources, such as enclosure tamper switches.

For each tamper event, the user is able to select the severity of the tamper response ranging from an interrupt, to a reset, to destroying the PUF reconstruction data which will make all protected key materials un-recoverable and effectively render the device inoperable. The tamper system also has an internal resettable event counter with programmable trigger threshold and refresh periods to mitigate false positive tamper events.

For more information about this feature, see AN1247: Anti-Tamper Protection Configuration and Use.

3.7.8 External Tamper Detection

The External Tamper Detect (ETAMPDET) module enables detection of external tampering, such as unauthorized enclosure opening. ETAMPDET operates in all energy modes down to EM4. Up to two signals can be generated and monitored to identify external tamper events. When a tamper event occurs, an interrupt is generated to allow software to take system-appropriate actions.

ETAMPDET is available on OPNs with Security Vault level at both Mid and High. However, only Vault High OPNs can be configured such that the Tamper block within the SE will respond autonomously to an ETAMPDET event.

3.7.9 Secure Attestation

Secure Vault High products support Secure Attestation, which begins with a secure identity that is created during the Silicon Labs manufacturing process. During device production, each device generates its own public/private keypair and securely stores the wrapped private key into immutable OTP memory and this key never leaves the device. The corresponding public key is extracted from the device and inserted into a binary DER-encoded X.509 device certificate, which is signed into a Silicon Labs CA chain and then programmed back into the chip into an immutable OTP memory.

The secure identity can be used to authenticate the chip at any time in the life of the product. The production certification chain can be requested remotely from the product. This certification chain can be used to verify that the device was authentically produced by Silicon Labs. The device unique public key is also bound to the device certificate in the certification chain. A challenge can be sent to the chip at any point in time to be signed by the device private key. The public key in the device certificate can then be used to verify the challenge response, proving that the device has access to the securely-stored private key, which prevents counterfeit products or impersonation attacks.

For more information about this feature, see AN1268: Authenticating Silicon Labs Devices Using Device Certificates.

3.8 Analog

Three analog buses route analog signals from the four GPIO ports to analog peripherals. These are ABUSA for GPIO Port A, ABUSB for GPIO Port B, and ABUSCD for GPIO Port C and Port D. The analog signals on ABUSA and ABUSB will be voltage limited by the lowest supply voltage on IOVDD1, and AVDD. The analog signals on ABUSCD will be voltage limited by the lowest supply voltage on IOVDD2, and AVDD.

3.8.1 Analog to Digital Converter (IADC)

The IADC is a hybrid architecture combining techniques from both SAR and Delta-Sigma style converters. It has a resolution of 12 bits at 1 Msps and 16 bits at up to 76.9 ksps. Hardware oversampling reduces system-level noise over multiple front-end samples. The IADC includes integrated voltage reference options. Inputs are selectable from a wide range of sources, including pins configurable as either single-ended or differential.

3.8.2 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs are selected from among internal references and external pins. The tradeoff between response time and current consumption is configurable by software. Two 6-bit reference dividers allow for a wide range of internally-programmable reference sources. The ACMP can also be used to monitor the supply voltage. An interrupt can be generated when the supply falls below or rises above the programmable threshold.

3.8.3 Digital to Analog Converter (VDAC)

The Digital to Analog Converter (VDAC) can convert a digital value to an analog output voltage. The VDAC is a fully differential, 500 ksps, 12-bit converter. The VDAC may be used for a number of different applications such as sensor interfaces or sound output. The VDAC can generate high-resolution analog signals while the MCU is operating at low frequencies and with low total power consumption. Using DMA and a timer, the VDAC can be used to generate waveforms without any CPU intervention. The VDAC is available in all energy modes down to and including EM3.

3.9 Power

The EFR32FG25 has an Energy Management Unit (EMU) and efficient integrated regulators to generate internal supply voltages. Only a single external supply voltage is required, from which all internal voltages are created. An optional integrated DC-DC buck regulator can be utilized to further reduce the current consumption. The DC-DC regulator requires one external inductor and one external capacitor.

The EFR32FG25 device family includes support for internal supply voltage scaling, as well as two different power domains groups for peripherals. These enhancements allow for further supply current reductions and lower overall power consumption.

3.9.1 Energy Management Unit (EMU)

The Energy Management Unit manages transitions of energy modes in the device. Each energy mode defines which peripherals and features are available and the amount of current the device consumes. The EMU can also be used to implement system-wide voltage scaling and turn off the power to unused RAM blocks to optimize the energy consumption in the target application. The DC-DC regulator operation is tightly integrated with the EMU.

3.9.2 Voltage Scaling

The EFR32FG25 supports supply voltage scaling for the LDO powering DECOUPLE, with independent selections for EM2 and EM3. Voltage scaling helps to optimize the energy efficiency of the system by operating at lower voltages when possible. The EM0 / EM1 voltage scaling level is VSCALE2, which allows the core to operate in active mode at full speed. The intermediate level, VSCALE1, allows operation in EM2 and EM3. The lowest level, VSCALE0, can be used to conserve power further in EM2 and EM3. The EMU will automatically switch the target voltage scaling level when transitioning between energy modes.

3.9.3 DC-DC Converter

The DC-DC buck converter covers a wide range of load currents, providing high efficiency in energy modes EM0, EM1, EM2 and EM3. RF noise mitigation allows operation of the DC-DC converter without significantly degrading sensitivity of radio components. An on-chip supply-monitor signals when the supply voltage is low to allow bypass of the regulator via programmable software interrupt. It employs soft switching at boot and DCDC regulating-to-bypass transitions to limit the max supply slew-rate and mitigate inrush current.

3.9.4 Power Domains

Peripherals may exist on several independent power domains which are powered down to minimize supply current when not in use. Power domains are managed automatically by the EMU.

The lowest-energy power domain is the "high-voltage" power domain (PDHV), which supports extremely low-energy infrastructure and peripherals. Circuits powered from PDHV are always on and available in all energy modes down to EM4.

The next power domain is the low power domain (PD0), which is further divided to power subsets of peripherals. All PD0 power domains are shut down in EM4. Circuits powered from PD0 power domains may be available in EM0, EM1, EM2, and EM3.

Low power domain A (PD0A) is the base power domain for EM2 and EM3 and will always remain on in EM0-EM3. It powers the most commonly-used EM2 and EM3-capable peripherals and infrastructure required to operate in EM2 and EM3. Auxiliary PD0 power domains (PD0B, PD0C, PD0D, PD0E) power additional EM2 and EM3-capable peripherals on demand. If any peripherals on one of the auxiliary power domains is enabled, that power domain will be active in EM2 and EM3. Otherwise, the auxiliary PD0 power domains will be shut down to reduce current.

Note: Power domain PD0E is also turned on when peripherals on PD0B, PD0C, or PD0D are used.

The active power domain (PD1) powers the rest of the device circuitry, including the CPU core and EM0 / EM1 peripherals. PD1 is always powered on in EM0 and EM1. PD1 is always shut down in EM2, EM3, and EM4.

Table 3.2 Peripheral Power Subdomains on page 18 shows the peripherals on the PDHV and PD0x domains. Any peripheral not listed is on PD1.

Always On in I	EM2/EM3	Selectively On	n in EM2/3			
PDHV ¹	PD0A	PD0B ²	PD0C ²	PD0D ²	PD0E	PDU
LFRCO	SYSRTC	LETIMER0	HFRCOEM23	DEBUG	GPIO	USB
LFXO	FSRCO	IADC0	HFXO	WDOG0	PRS	USBPLL0
BURTC		PCNT0		WDOG1		
BURAM		ACMP0		EUSART0		
ETAMPDET		ACMP1		I2C0		
ULFRCO		LESENSE				
		VDAC0				
-		o available in EM4. DD are enabled, PD(DE will also be autom	atically enabled.		

Table 3.2. Peripheral Power Subdomains

3.10 Reset Management Unit (RMU)

The RMU is responsible for handling reset of the EFR32FG25. A wide range of reset sources are available, including several power supply monitors, pin reset, software controlled reset, core lockup reset, and watchdog reset.

3.11 Core and Memory

3.11.1 Processor Core

The ARM Cortex-M processor includes a 32-bit RISC processor integrating the following features and tasks in the system:

- ARM Cortex-M33 RISC processor achieving 1.50 Dhrystone MIPS/MHz
- ARM TrustZone security technology
- Embedded Trace Macrocell (ETM) for real-time trace and debug
- Up to 1920 kB flash program memory
- Up to 512 kB RAM data memory
- · Configuration and event handling of all modules
- · 2-pin Serial-Wire debug interface

3.11.2 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the microcontroller. The flash memory is readable and writable from both the Cortex-M33 and LDMA. In addition to the main flash array where Program code is normally written the MSC also provides an Information block where additional information such as special user information or flash-lock bits are stored. There is also a readonly page in the information block containing system and device calibration data. Read and write operations are supported in energy modes EM0 Active and EM1 Sleep.

3.11.3 Linked Direct Memory Access Controller (LDMA)

The Linked Direct Memory Access (LDMA) controller allows the system to perform memory operations independently of software. This reduces both energy consumption and software workload. The LDMA allows operations to be linked together and staged, enabling so-phisticated operations to be implemented.

3.12 Memory Map

The EFR32FG25 memory map is shown in the figures below. RAM and flash sizes are for the largest memory configuration.



Figure 3.2. EFR32FG25 Memory Map — Core Peripherals and Code Space

3.13 Configuration Summary

The features of the EFR32FG25 are a subset of the feature set described in the device reference manual. The table below describes device specific implementation of the features. Remaining modules support full configuration.

Table 3.3. Configuration Summary

Module	Lowest Energy Mode	Configuration
I2C0	EM2 ¹	
I2C1	EM1	
IADC0	EM2	
LETIMER0	EM2 ¹	24-bit
TIMER0	EM1	32-bit, 3-channels, +DTI
TIMER1		
TIMER2	EM1	16-bit, 3-channels, +DTI
TIMER3		
TIMER4		
TIMER5		
TIMER6		
EUSART0	EM1 - Full high-speed operation, all modes	
	EM2 ¹ - Low-energy UART operation, 9600 Baud	
	EM2 or EM3 ¹ - Low-energy SPI secondary receiver	
EUSART1	EM1 - Full high-speed operation	
EUSART2		
EUSART3		
EUSART4		
Note:		

Note:

1. EM2 and EM3 operation is only supported for digital peripheral I/O on Port A and Port B. All GPIO ports support digital peripheral operation in EM0 and EM1.

4. Electrical Specifications

4.1 Electrical Characteristics

All electrical parameters in all tables are specified under the following conditions, unless stated otherwise:

- Devices with an output power rating of +16 dBm using the matching network corresponding to the Band of operation.
- Typical values are based on T_A = 25 °C and all supplies at 3.6 V, by production test and/or technology characterization.
- Minimum and maximum values represent the worst conditions across supply voltage, process variation, and operating temperature, unless stated otherwise.

RF electrical parameters are specified under the following additional constraints, unless stated otherwise:

- Typical (Typ) values are measured:
 - in conducted mode, based on Silicon Laboratories band-specific external RF impedance-matching networks according to Section 5.2 RF Matching Networks, and interfacing through a standard coaxial connector at the antenna port to a 50 Ω RF source for receiver tests, and 50 Ω RF Load for transmitter tests.
 - with VREGVDD = AVDD = PAVDD = 3.6 V with 0.20 Ω source resistance, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC,
 - · with all MCU peripherals disabled,
 - with the reference oscillator using a 39 MHz Crystal adjusted to within ±1 ppm,
 - and with operating frequency set to F_{RANGE} Typ for the specific operating band.
- Minimum (Min) and Maximum (Max) values are taken:
 - · over variations in process,
 - with VREGVDD = AVDD = PAVDD adjusted together between their Min and Max voltage given in Table 4.2 General Operating Conditions on page 24
 - on operating temperature Min and Max defined in Table 4.2 General Operating Conditions on page 24 under Operating ambient temperature range,
 - and on the minimum and maximum operating channel frequency between F_{RANGE} Min and F_{RANGE} Max for the specific operating RF Band,
 - while keeping all other conditions at typical unless otherwise noted.

Due to on-chip circuitry (e.g. diodes), some EFR32FG25 power supply pins have a dependent relationship with one or more other power supply pins. These internal relationships between the external voltages applied to the various EFR32FG25 supply pins are defined below. Exceeding the below constraints can result in damage to the device and/or increased current draw.

- VREGVDD \geq DVDD
 - In systems using the DC-DC converter, DVDD (the buck converter output) should not be driven externally and VREGVDD (the buck converter input) must be greater than DVDD (VREGVDD > DVDD)
 - In systems not using the DC-DC converter, DVDD must be shorted to VREGVDD on the PCB (VREGVDD = DVDD)
- AVDD, IOVDD0, IOVDD1, and IOVDD2: No dependency with each other or any other supply pin. Additional leakage may occur if DVDD remains unpowered with power applied to these supplies. See Section 3.8 Analog for details on how voltage supplied to these pins affects some analog operation.
- DVDD ≥ DECOUPLE
- PAVDD ≥ RFVDD

4.2 Absolute Maximum Ratings

Stresses beyond those listed below may cause permanent damage to the device. This is a stress rating only and functional operation of the devices at those or any other conditions beyond those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. For more information on the available quality and reliability data, see the Quality and Reliability Monitor Report at http://www.silabs.com/support/quality/pages/default.aspx.

Table 4.1. Absolute Maximum Ratings

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Storage temperature range	T _{STG}		-50	—	+150	°C
Voltage on any supply pin	V _{DDMAX}		-0.3	_	3.8	V
Junction temperature	T _{JMAX}	-I grade	—	_	+125	°C
Voltage ramp rate on any supply pin	V _{DDRAMPMAX}		_		1.0	V / µs
Voltage on HFXO pins	V _{HFXOPIN}		-0.3	—	1.2	V
DC voltage on any GPIO pin	V _{DIGPIN}		-0.3	_	V _{IOVDD} + 0.3	V
DC voltage on RESETn pin ¹	V _{RESETn}		-0.3	_	3.8	V
Total current into VDD power lines	IVDDMAX	Source	_		200	mA
Total current into VSS ground lines	IVSSMAX	Sink	_		200	mA
Current per I/O pin	I _{IOMAX}	Sink	—	_	50	mA
		Source	—		50	mA
Current for all I/O pins	I _{IOALLMAX}	Sink	_	_	200	mA
		Source	_		200	mA

Note:

1. The RESETn pin has a pull-up device to the DVDD supply. For minimum leakage, RESETn should not exceed the voltage at DVDD.

4.3 General Operating Conditions

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Operating ambient tempera- ture range	T _A	-I temperature grade ¹	-40	_	+125	°C
DVDD supply voltage	V _{DVDD}	EM0/1	1.71	3.6	3.8	V
		EM2/3/4 ²	1.71	3.6	3.8	V
AVDD supply voltage	V _{AVDD}		1.71	3.6	3.8	V
IOVDD0 operating supply voltage	V _{IOVDD0}		1.71	3.6	3.8	V
IOVDD1 operating supply voltage	V _{IOVDD1}		1.71	3.6	3.8	V
IOVDD2 operating supply	V _{IOVDD2}	USB not in use	V _{IOVDD0}	3.6	3.8	V
voltage		USB in use	3.0	3.3	3.6	V
RFVDD operating supply voltage	V _{RFVDD}		1.71	3.6	V _{PAVDD}	V
PAVDD operating supply	V _{PAVDD}	Constant Envelope PA	3.0	3.3	3.8	V
voltage		OFDM 3.6 V PA	3.45	3.6	3.8 3.8 3.8	V
VREGVDD operating supply	V _{VREGVDD}	DCDC in bypass 60 mA load	1.8 3.3 3.4	3.8	V	
voltage		DCDC not in use. DVDD external- ly shorted to VREGVDD	1.71	3.3	3.8	V
		DCDC in regulation	2.2	3.3	3.8	V
DECOUPLE output capaci- tor ³	CDECOUPLE		0.75	1.0	2.75	μF
HCLK and Core frequency	fHCLK	VSCALE2, MODE = WS0	_	_	25	MHz
		VSCALE2, MODE = WS1	—	_	50	MHz
		VSCALE2, MODE = WS2	_	_	3.8 3.8 3.6 V _{PAVDD} 3.8 3.8 3.8 3.8 3.8 3.8 3.8 2.75 25	MHz
		VSCALE2, MODE = WS3	_	_	97.5	MHz
PCLK frequency	f _{PCLK}	VSCALE2	—		48.75	MHz
EM01 Group A clock fre- quency	f _{EM01GRPACLK}	VSCALE2			97.5	MHz
HCLK Radio frequency ⁴	f _{HCLKRADIO}	VSCALE2		39.0	40	MHz
External Clock Input	f _{CLKIN}	VSCALE2, IOVDD0-2 ≥ 2.7 V	_		40	MHz
DPLL Reference Clock	f _{DPLLREFCLK}	VSCALE2	_	_	40	MHz
	1		1		1	1

Table 4.2. General Operating Conditions

	Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
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Note:

- 1. The device may operate continuously at the maximum allowable ambient T_A rating as long as the absolute maximum T_{JMAX} is not exceeded. For an application with significant power dissipation, the allowable T_A may be lower than the maximum T_A rating. $T_A = T_{JMAX} (\Theta_{JA} \times PowerDissipation)$. Refer to the Absolute Maximum Ratings table and the Thermal Characteristics table for T_{JMAX} and Θ_{JA} .
- 2. The DVDD supply is monitored by the DVDD BOD in EM0/1 and the LE DVDD BOD in EM2/3/4.
- 3. The system designer should consult the characteristic specs of the capacitor used on DECOUPLE to ensure its capacitance value stays within the specified bounds across temperature and DC bias.
- 4. The recommended radio crystal frequency for the sub-GHz radio is 39.0 MHz. The minimum and maximum HCLKRADIO frequency in this table represent the design timing limits, which are much wider than the typical crystal tolerance.

4.4 DC-DC Converter

Test conditions: L_{DCDC} = 2.2 µH (Samsung CIG22H2R2MNE), C_{DCDC} = 4.7 µF (TDK CGA5L3X8R1C475K160AB), $V_{VREGVDD}$ = 3.6 V, V_{OUT} = 1.8 V, IPKVAL in EM0/1 modes is set to 150 mA, and in EM2/3 modes is set to 90 mA, unless otherwise indicated.

Table 4.3. DC-DC Converter

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Input voltage range at VREGVDD pin	V _{VREGVDD}	DCDC in regulation, $I_{LOAD} = I_{LOAD}$ MAX ¹ , EM0/EM1 mode	2.2	-	3.8	V
		DCDC in regulation, I _{LOAD} = 5 mA, EM0/EM1 or EM2/EM3 mode	1.8	-	3.8	V
		Bypass Mode, I _{LOAD} ≤ 60 mA	1.8	_	3.8	V
		Bypass Mode, $I_{LOAD} \le 120 \text{ mA}$	1.9	_	3.8	V
Regulated output voltage	V _{OUT}		—	1.8		V
Regulation DC accuracy	ACC _{DC}	$V_{VREGVDD} \ge 2.2 V$, Steady state in EM0/EM1 mode or EM2/EM3 mode	-2.5	_	4.0	%
Regulation total accuracy	ACC _{TOT}	All error sources (including DC errors, overshoot, undershoot)	-5	_	7	%
Steady-state output ripple	V _R	I _{LOAD} = 20 mA in EM0/EM1 mode		9.6		mVpp
DC line regulation	V _{REG}	$I_{LOAD} = I_{LOAD} MAX^{2}$ in EM0/EM1 mode, $V_{VREGVDD} \ge 2.2 V$	—	-2.6		mV/V
Efficiency	EFF	Load current between 100 µA and 60 mA in EM0/EM1 mode	_	91.4	_	%
		Load current between 10 µA and 5 mA in EM2/EM3 mode	—	91.0	—	%
DC load regulation	I _{REG}	Load current between 100 μA and $I_{LOAD}MAX^2$ in EM0/EM1 mode	_	-0.12	_	mV/mA
Output load current	I _{LOAD}	EM0/EM1 mode, DCDC in regula- tion, DCDC_EM01CTRL0.IPKVAL = 9, Pulse-pairing disabled, Radio not transmitting ²	_	_	60	mA
		EM0/EM1 mode, DCDC in regula- tion, Radio in receive mode, with pulse-pairing enabled ²	_	-	36	mA
		EM0/EM1 mode, DCDC in regula- tion, Radio transmitting ¹	_	_	120	mA
		EM2/EM3 mode, DCDC in regula- tion	_	_	5	mA
		Bypass mode, $1.8 \text{ V} \leq \text{V}_{\text{VREGVDD}}$ $\leq 3.8 \text{ V}$	—	- 60	60	mA
		Bypass mode, $1.9 \text{ V} \leq \text{V}_{\text{VREGVDD}} \leq 3.8 \text{ V}$	_	_	120	mA
Nominal output capacitor	C _{DCDC}	4.7 μ F ± 10% X7R capacitor used for performance characterization ³	_	4.7	10	μF
Nominal inductor	L _{DCDC}	± 20% tolerance	_	2.2		μH

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Nominal input capacitor	C _{IN}		C _{DCDC}	_	—	μF
Resistance in bypass mode	R _{BYP}	Bypass switch from VREGVDD to DVDD, V _{VREGVDD} = 1.8 V	_	0.46	0.80	Ω
		Powertrain PFET switch from VREGVDD to VREGSW, V _{VREGVDD} = 1.8 V	_	0.60	0.90	Ω
Supply monitor threshold programming range	V _{CMP_RNG}	Programmable in 0.1 V steps	2	—	2.3	V
Supply monitor threshold ac- curacy	V _{CMP_ACC}	Supply falling edge trip point	-5	_	5	%
Supply monitor threshold hysteresis	V _{CMP_HYST}	Positive hysteresis on the supply rising edge referred to the falling edge trip point	_	4	-	%
Supply monitor response time	t _{CMP_DELAY}	Supply falling edge at -100 mV / µs	—	0.6	-	μs

Note:

1. During radio transmit operations, the RAIL library will place the DCDC into a mode that increases the maximum load current, to support higher TX output power supplied from the DCDC converter.

- 2. Pulse-pairing is an optional feature to improve performance at radio frequencies below 550 MHz, but has limited output current. It is enabled by default when using RAIL with an IPKVAL setting of 3 or less. Pulse pairing may be disabled from application code by setting IPKVAL > 3. This must be done before RAIL software is initialized.
- 3. TDK CGA5L3X8R1C475K160AB used for performance characterization. Actual capacitor values can be significantly de-rated from their specified nominal value by the rated tolerance, as well as the application's AC voltage, DC bias, and temperature. The minimum capacitance counting all error sources should be no less than 3.6 μF.

4.5 Thermal Characteristics

Package	Board	Parameter	Symbol	Test Condition	Value	Unit
56QFN JEDEC - High (7x7mm) Thermal Cond.		Thermal Resistance, Junction to Ambient	Θ _{JA}	Still Air, JESD51-2A	22.6	°C/W
	(2s2p) ¹	Thermal Resistance, Junction to Top Center	Ψ_{JT}	_	0.26	°C/W
		Thermal Resistance, Junction to Board	Ψ_{JB}	_	5.1	°C/W
		Thermal Resistance, Junction to Board	Θ _{JB}	JESD51-8	11.8	°C/W
	No Board	Thermal Resistance, Junction to Case	Θ _{JC}	Temperature controlled heat sink on top of package, all other sides of package insulated to prevent heat flow, per JESD51-14	2.0	°C/W

Table 4.4. Thermal Characteristics

Note:

1. Based on 4 layer PCB with dimension 76 mm x 110 mm, PCB Thickness of 1.6 mm, per JEDEC. PCB Center Land with 25 Via to top internal plane of PCB.

4.6 Current Consumption

4.6.1 MCU current consumption using DC-DC at 3.6 V input

Unless otherwise indicated, typical conditions are: VREGVDD = AVDD = PAVDD = 3.6 V. DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC. Voltage scaling level = VSCALE2. $T_A = 25$ °C. Minimum and maximum values in this table represent the worst conditions across process variation at $T_A = 25$ °C.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Current consumption in EM0 mode with all peripherals dis- abled	I _{ACTIVE}	97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running Prime from flash	_	31	_	µA/MHz
	97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running while loop from flash	_	30		µA/MHz	
		97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running CoreMark loop from flash	_	43		µA/MHz
		39.0 MHz crystal, CPU running Prime from flash	—	35	_	µA/MHz
		39.0 MHz crystal, CPU running while loop from flash	—	35	_	µA/MHz
		39.0 MHz crystal, CPU running CoreMark loop from flash	—	49	_	µA/MHz
		38 MHz HFRCO, CPU running while loop from flash	_	30	_	µA/MHz
		26 MHz HFRCO, CPU running while loop from flash	—	34	_	µA/MHz
		16 MHz HFRCO, CPU running while loop from flash	_	43	_	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	_	395	_	µA/MHz
Current consumption in EM1 mode with all peripherals dis-	I _{EM1}	97.5 MHz RFFPLL referenced to 39.0 MHz crystal	—	22	_	µA/MHz
abled		39.0 MHz crystal	_	26	_	µA/MHz
		38 MHz HFRCO	_	21	_	µA/MHz
		26 MHz HFRCO	—	25	—	µA/MHz
		16 MHz HFRCO	—	34	_	µA/MHz
		1 MHz HFRCO	_	386	_	µA/MHz

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Current consumption in EM2 mode, VSCALE0	I _{EM2_VS}	Full RAM retention and RTC run- ning from LFXO		4.6	_	μA
		Full RAM retention and RTC run- ning from LFRCO	_	4.6	_	μA
		Full RAM retention and RTC run- ning from LFRCO with USB con- nected and in Suspend mode with IOVDD2 = 3.3 V		7.0	_	μΑ
		32 kB RAM retention and RTC running from LFXO	_	2.6		μA
		32 kB RAM retention and RTC running from LFRCO	_	2.6		μA
		32 kB RAM retention and RTC running from LFXO, Sequencer RAM and CPU cache not retained	_	2.3	_	μΑ
		32 kB RAM retention and RTC running from LFXO, Sequencer RAM, CPU cache, and EM0/1 pe- ripheral states not retained	_	2.3	_	μΑ
		32 kB RAM retention and RTC running from LFXO, Sequencer RAM, FRC RAM, CPU cache, and EM0/1 peripheral states not re- tained	_	2.3	_	μA
Current consumption in EM3 mode, VSCALE0	I _{EM3_VS}	32 kB RAM retention and RTC running from ULFRCO	_	2.4	_	μA
Current consumption for re- tained RAM bank in EM2 or EM3	I _{RAM}	Per 32 kB RAM bank	_	0.13	_	μΑ
Additional current in EM2 or EM3 when any peripheral in PD0B is enabled ¹	IPDOB_VS		_	0.37	_	μA
Additional current in EM2 or EM3 when any peripheral in PD0C is enabled ¹	IPDOC_VS		_	0.06	_	μΑ
Additional current in EM2 or EM3 when any peripheral in PD0D is enabled ¹	IPD0D_VS		_	0.58	_	μΑ
Additional current in EM2 or EM3 when any peripheral in PD0E is enabled ¹	IPD0E_VS		_	0.07	_	μΑ
Additional current in EM2 or EM3 when any peripheral in PDU is enabled ¹	I _{PDU_VS}		_	1.42	_	μΑ

Note:

1. Extra current consumed by power domain. Does not include current associated with the enabled peripherals. See 3.9.4 Power Domains for a list of the peripherals in each power domain. Note that if the PD0B, PD0C, or PD0D domains are enabled, PD0E will also automatically be enabled.

4.6.2 MCU current consumption at 3.6 V

Unless otherwise indicated, typical conditions are: AVDD = DVDD = RFVDD = PAVDD = VREGVDD = IOVDD0-2 = 3.6 V. DC-DC not used. Voltage scaling level = VSCALE2. T_A = 25 °C. Minimum and maximum values in this table represent the worst conditions across process variation at T_A = 25 °C.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Current consumption in EM0 mode with all peripherals dis- abled	IACTIVE	97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running Prime from flash		53		µA/MHz
		97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running while loop from flash		53	_	µA/MHz
		97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running CoreMark loop from flash	_	75	_	µA/MHz
		39.0 MHz crystal, CPU running Prime from flash	—	61	_	µA/MHz
		39.0 MHz crystal, CPU running while loop from flash		60		µA/MHz
		39.0 MHz crystal, CPU running CoreMark loop from flash	_	86	_	µA/MHz
		38 MHz HFRCO, CPU running while loop from flash	—	52	97	µA/MHz
		26 MHz HFRCO, CPU running while loop from flash	_	60	_	µA/MHz
		16 MHz HFRCO, CPU running while loop from flash	_	76	_	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	_	685	2300	µA/MHz
Current consumption in EM1 mode with all peripherals dis-	I _{EM1}	97.5 MHz RFFPLL referenced to 39.0 MHz crystal	_	38		µA/MHz
abled		39.0 MHz crystal	—	45	_	µA/MHz
		38 MHz HFRCO	_	36	80	µA/MHz
		26 MHz HFRCO	_	44		µA/MHz
		16 MHz HFRCO	—	60	_	µA/MHz
		1 MHz HFRCO		669	2200	µA/MHz

Table 4.6. MCU current consumption at 3.6 V

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Current consumption in EM2 mode, VSCALE0	I _{EM2_VS}	Full RAM retention and RTC run- ning from LFXO	_	7.9	_	μΑ
		Full RAM retention and RTC run- ning from LFRCO	—	8.0	20	μA
		Full RAM retention and RTC run- ning from LFRCO with USB con- nected and in Suspend mode with IOVDD2 = 3.3 V	_	10.4	_	μΑ
		32 kB RAM retention and RTC running from LFRCO	—	4.4	_	μA
		32 kB RAM retention and RTC running from LFXO	—	4.4	_	μA
		32kB RAM retention and RTC running from LFXO, Sequencer RAM and CPU cache not retained	—	3.9	_	μA
		32 kB RAM retention and RTC running from LFXO, Sequencer RAM, CPU cache, and EM0/1 pe- ripheral states not retained	_	3.9	_	μΑ
		32 kB RAM retention and RTC running from LFXO, Sequencer RAM, FRC RAM, CPU cache, and EM0/1 peripheral states not re- tained		3.8	_	μA
Current consumption in EM3 mode, VSCALE0	I _{EM3_VS}	Full RAM retention and RTC run- ning from ULFRCO	—	7.6	_	μA
		32 kB RAM retention and RTC running from ULFRCO	—	4.0	9.0	μA
Current consumption for re- tained RAM bank in EM2 or EM3	I _{RAM}	Per 32 kB RAM bank	_	0.24	_	μA
Current consumption in EM4	I _{EM4}	No BURTC, no LF oscillator	_	0.74	1.50	μA
mode		BURTC with LFXO	—	1.14	_	μA
		ETAMPDET active ¹	—	0.87	_	μA
Current consumption during reset	I _{RST}	Hard pin reset held	_	482		μA
Additional current in EM2 or EM3 when any peripheral in PD0B is enabled ²	I _{PD0B_VS}		_	0.61	_	μA
Additional current in EM2 or EM3 when any peripheral in PD0C is enabled ²	I _{PD0C_VS}		_	0.08	_	μA
Additional current in EM2 or EM3 when any peripheral in PD0D is enabled ²	IPDOD_VS		_	0.97	_	μA
Additional current in EM2 or EM3 when any peripheral in PD0E is enabled ²	I _{PD0E_VS}		_	0.09	_	μA

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Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Additional current in EM2 or EM3 when any peripheral in PDU is enabled ²	I _{PDU_VS}		_	2.5	_	μA

Note:

1. ETAMPDET operating from ULFRCO divided down to 100 Hz, with 1 nF load capacitance to ground.

2. Extra current consumed by power domain. Does not include current associated with the enabled peripherals. See 3.9.4 Power Domains for a list of the peripherals in each power domain. Note that if the PD0B, PD0C, or PD0D domains are enabled, PD0E will also automatically be enabled.

4.6.3 MCU current consumption at 3.3 V

Unless otherwise indicated, typical conditions are: AVDD = DVDD = RFVDD = PAVDD = VREGVDD = IOVDD0-2 = 3.3 V. DC-DC not used. Voltage scaling level = VSCALE2. T_A = 25 °C. Minimum and maximum values in this table represent the worst conditions across process variation at T_A = 25 °C.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Current consumption in EM0 mode with all peripherals dis- abled	IACTIVE	97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running Prime from flash		53		µA/MHz
		97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running while loop from flash	_	53	_	µA/MHz
		97.5 MHz RFFPLL referenced to 39.0 MHz crystal, CPU running CoreMark loop from flash	_	75	_	µA/MHz
		39.0 MHz crystal, CPU running Prime from flash	—	61	_	µA/MHz
		39.0 MHz crystal, CPU running while loop from flash	_	60	_	µA/MHz
		39.0 MHz crystal, CPU running CoreMark loop from flash	_	86	_	µA/MHz
		38 MHz HFRCO, CPU running while loop from flash	—	52	_	µA/MHz
		26 MHz HFRCO, CPU running while loop from flash	_	59	_	µA/MHz
		16 MHz HFRCO, CPU running while loop from flash	_	75	_	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	_	684	_	µA/MHz
Current consumption in EM1 mode with all peripherals dis-	I _{EM1}	97.5 MHz RFFPLL referenced to 39.0 MHz crystal	_	39		µA/MHz
abled		39.0 MHz crystal	—	45	_	µA/MHz
		38 MHz HFRCO	_	36		µA/MHz
		26 MHz HFRCO	_	44		µA/MHz
		16 MHz HFRCO	—	60	_	µA/MHz
		1 MHz HFRCO	—	668	_	µA/MHz

Table 4.7. MCU current consumption at 3.3 V

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Current consumption in EM2 mode, VSCALE0	I _{EM2_VS}	Full RAM retention and RTC run- ning from LFXO	_	7.6	_	μΑ
		Full RAM retention and RTC run- ning from LFRCO	—	7.6	—	μA
		Full RAM retention and RTC run- ning from LFRCO with USB con- nected and in Suspend mode with IOVDD2 = 3.3 V	_	10	_	μΑ
		32 kB RAM retention and RTC running from LFRCO	—	4.1	_	μA
		32 kB RAM retention and RTC running from LFXO	—	4.0	_	μA
		32kB RAM retention and RTC running from LFXO, Sequencer RAM and CPU cache not retained	—	3.6	_	μA
		32 kB RAM retention and RTC running from LFXO, Sequencer RAM, CPU cache, and EM0/1 pe- ripheral states not retained	_	3.6		μA
		32 kB RAM retention and RTC running from LFXO, Sequencer RAM, FRC RAM, CPU cache, and EM0/1 peripheral states not re- tained	_	3.5		μΑ
Current consumption in EM3 mode, VSCALE0	I _{EM3_VS}	Full RAM retention and RTC run- ning from ULFRCO	_	7.2	_	μA
		32 kB RAM retention and RTC running from ULFRCO	—	3.7	—	μA
Current consumption for re- tained RAM bank in EM2 or EM3	I _{RAM}	Per 32 kB RAM bank	_	0.23	_	μA
Current consumption in EM4	I _{EM4}	No BURTC, no LF oscillator	_	0.40		μA
mode		BURTC with LFXO	_	0.81		μA
		ETAMPDET active ¹		0.54	_	μA
Current consumption during reset	I _{RST}	Hard pin reset held	_	468		μA
Additional current in EM2 or EM3 when any peripheral in PD0B is enabled ²	I _{PD0B_VS}		_	0.62	_	μA
Additional current in EM2 or EM3 when any peripheral in PD0C is enabled ²	I _{PD0C_VS}		_	0.10	_	μA
Additional current in EM2 or EM3 when any peripheral in PD0D is enabled ²	I _{PD0D_VS}		_	0.98	_	μA
Additional current in EM2 or EM3 when any peripheral in PD0E is enabled ²	I _{PD0E_VS}		_	0.11	_	μA

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Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Additional current in EM2 or EM3 when any peripheral in PDU is enabled ²	I _{PDU_VS}		_	2.5	_	μA

Note:

1. ETAMPDET operating from ULFRCO divided down to 100 Hz, with 1 nF load capacitance to ground.

2. Extra current consumed by power domain. Does not include current associated with the enabled peripherals. See 3.9.4 Power Domains for a list of the peripherals in each power domain. Note that if the PD0B, PD0C, or PD0D domains are enabled, PD0E will also automatically be enabled.

4.6.4 Radio current consumption with DC-DC at 3.3 V input

RF current consumption measured with MCU in EM1, HCLK = 39.0 MHz, and all MCU peripherals disabled. Unless otherwise indicated, typical conditions are: VREGVDD = AVDD = PAVDD = 3.3 V. DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC. T_A = 25 °C. Minimum and maximum values in this table represent the worst conditions across process variation at T_A = 25 °C.

Table 4.8.	Radio current	consumption	with DC-DC	at 3.3 V input
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Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Current consumption in re- ceive mode, active packet reception, VSCALE2, EM1P ¹	IRX_ACTIVE	f = 915 MHz, O-QPSK, 4.8 kbps	—	5.8	_	mA
		f = 924 MHz, 4-GFSK, 400 kbps	—	6.3	_	mA
		f = 868 MHz, 2-GFSK, 38.4 kbps	_	5.7	_	mA
		f = 868 MHz, GMSK, 500 kbps		6.3		mA
		f = 868 MHz, O-QPSK, 100 kbps	_	6.3	_	mA
		f = 915 MHz, O-QPSK, 250 kbps		8.8	_	mA
Current consumption in re- ceive mode, listening for packet, VSCALE2, EM1P ¹	IRX_LISTEN	f = 915 MHz, O-QPSK, 4.8 kbps		5.7		mA
		f = 924 MHz, 4-GFSK, 400 kbps		6.4		mA
		f = 868 MHz, 2-GFSK, 38.4 kbps		5.7		mA
		f = 868 MHz, GMSK, 500 kbps		6.3		mA
		f = 868 MHz, O-QPSK, 100 kbps		6.4		mA
		f = 915 MHz, O-QPSK, 250 kbps		9.1		mA
Current consumption in transmit mode, VSCALE2, EM1	I _{TX}	f = 915 MHz, CW, PAVDD ² = 3.3 V, 0 dBm output power ³		24.9	_	mA
		f = 915 MHz, CW, PAVDD ² = 3.6 V, 0 dBm output power ³		24.7		mA
		f = 915 MHz, CW, PAVDD ² = 3.3 V, 12 dBm output power ³		54.5	_	mA
		f = 915 MHz, CW, PAVDD ² = 3.6 V, 12 dBm output power ³		54.3	_	mA
		f = 915 MHz, CW, PAVDD ² = 3.3 V, POUT _{MAX} ⁴ output power ³		76.8		mA
		f = 915 MHz, CW, PAVDD ² = 3.6 V, POUT _{MAX} ⁴ output power ³		76.6	_	mA
		f = 924 MHz, CW, PAVDD ² = 3.3 V, 13 dBm output power ³		58.8	_	mA
		f = 924 MHz, CW, PAVDD ² = 3.6 V, 13 dBm output power ³		58.6	_	mA
		f = 868 MHz, CW, PAVDD ² = 3.3 V, 14 dBm output power ³	_	52.0	—	mA
		f = 470 MHz, CW, PAVDD ² = 3.3 V, 16 dBm output power ⁵	_	72.8		mA
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
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Note:			I			
1. EM1P operation i	s 0.22 mA lower than	EM1 operation				
2. VREGVDD and A	VDD tied to PAVDD					
3. Using the 868/91	5/920 MHz matching n	etwork as shown in the typical	connections section.			
4. Same POUT _{MAX} 45	setting as in Table 4.1	4 915 MHz Band +16 dBm RF	Constant Envelope Tra	ansmitter Cha	aracteristics or	n page
5. Using the 470 MI	Iz matching network a	s shown in the typical connecti	ons section.			

4.6.5 SUN O-QPSK radio current consumption with DC-DC at 3.3 V input

SUN O-QPSK DSSS Modulations are defined by IEEE 802.15.4-2020 section 21, and Table 21-4 using the following abbreviations: f = operating frequency (MHz), Rc = baud or Chip rate (kchip/s), RM = Rate mode (index), Rd = Data bit rate (kbps), and PL = PSDU Length (octets). Unless otherwise indicated, typical conditions are: VREGVDD = AVDD = PAVDD = 3.3 V. DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC. T_A = 25 °C. Minimum and maximum values in this table represent the worst conditions across process variation at T_A = 25 °C.

Table 4.9	SUN O-QPSK radio	current consum	ntion with DC-DO	at 3.3 V input
		current consum		

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Current consumption in SUN O-QPSK Receive mode, ac-	I _{RX_ACTIVE}	f = 914, Rc = 100, RM = 0, Rd = 6.25, PL = 20	—	6.6	_	mA
tive packet reception, VSCALE2, EM1P		f = 914, Rc = 100, RM = 2, Rd = 25, PL = 20	—	6.6	_	mA
		f = 914, Rc = 100, RM = 3, Rd = 50, PL = 250	_	6.7		mA
		f = 914, Rc = 1000, RM = 0, Rd = 31.25, PL = 20	_	8.2	_	mA
		f = 914, Rc = 1000, RM = 3, Rd = 500, PL = 250	_	8.6	_	mA
Current consumption in SUN O-QPSK Receive mode, lis-	I _{RX_LISTEN}	f = 914, Rc = 100, RM = 0, Rd = 6.25, PL = 20	—	6.8	—	mA
tening for indicated modula- tion with no input signal, VSCALE2, EM1P		f = 914, Rc = 100, RM = 2, Rd = 25, PL = 20	-	6.8	_	mA
		f = 914, Rc = 100, RM = 3, Rd = 50, PL = 250	-	6.8	_	mA
		f = 914, Rc = 1000, RM = 0, Rd = 31.25, PL = 20	_	8.9		mA
		f = 914, Rc = 1000, RM = 3, Rd = 500, PL = 250	_	8.9		mA
Current consumption in SUN O-QPSK transmit mode at POUT _{MAX} ¹ output power	Itxpout_max	f = 914, Rc = 100, RM = 2, Rd = 25, PL = 20		71.6	_	mA

Note:

1. Same POUT_{MAX} setting as in Table 4.14 915 MHz Band +16 dBm RF Constant Envelope Transmitter Characteristics on page 45

4.6.6 SUN OFDM radio current consumption with DC-DC at 3.6 V input

These radio current consumption measurements for Min and Max use the same transceiver settings as the Typ. Measurements use packet length of 250 octets when data rate is 50 kbps or higher, and 20 octets packet length when lower then 50 kbps. OFDM Modulation is defined in 802.15.4-2020 section 20.3 . In this table, f = operating frequency in MHz, and the indication "OptX, MCSy" means X as the Option number 1 through 4, and y is the MCS index 0 through 6, and PL = PSDU Length (octets). Unless otherwise indicated, conditions are: VREGVDD = AVDD = PAVDD = 3.6 V. DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC. T_A = 25 °C.

Table 4.10. SUN OFDM radio current consumption with DC-DC at 3.6 V input

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Current consumption in SUN OFDM Receive mode, active packet reception, VSCALE2,	I _{RX_ACTIVE}	f = 914, Opt1, MCS2	_	8.6	_	mA
		f = 914, Opt1, MCS6, T _A = 25 °C ¹	_	8.6	9.0	mA
EM1P		f = 914, Opt2, MCS3	_	7.7		mA
		f = 914, Opt2, MCS6	_	7.8	_	mA
		f = 923.7, Opt3, MCS4, T _A = 25 °C ¹	_	8.9	9.4	mA
		f = 923.7, Opt3, MCS5	_	8.8		mA
		f = 923.7, Opt3, MCS6	_	8.8	_	mA
		f = 866.5, Opt4, MCS4	_	8.7		mA
		f = 866.5, Opt4, MCS6	_	8.6	_	mA
Current consumption in SUN	I _{RX_LISTEN}	f = 914, Opt1, MCS2		8.2		mA
OFDM Receive mode, listen- ing for indicated modulation		f = 914, Opt1, MCS6, T _A = 25 °C ¹		8.2	8.6	mA
with no input signal, VSCALE2, EM1P		f = 914, Opt2, MCS3	_	7.4		mA
		f = 914, Opt2, MCS6	_	7.4	_	mA
		f = 923.7, Opt3, MCS4, T _A = 25 °C ¹	_	7.2	7.7	mA
		f = 923.7, Opt3, MCS5	_	7.2	_	mA
		f = 923.7, Opt3, MCS6	_	7.2	_	mA
		f = 866.5, Opt4, MCS4	_	7.2		mA
		f = 866.5, Opt4, MCS6	_	7.2	_	mA
Current consumption in SUN	I _{TX16}	f = 914, Opt1, MCS2, T _A = 25 °C ¹	_	187	194	mA
OFDM transmit mode with average TX output power set		f = 914, Opt1, MCS3	_	187		mA
to 16 dBm		f = 914, Opt1, MCS6	_	186		mA
		f = 914, Opt2, MCS3		186		mA
		f = 914, Opt2, MCS6	_	186	_	mA
		f = 490, Opt4, MCS6	_	189	_	mA
Current consumption in SUN	I _{TX14}	f = 866.5, Opt4, MCS4	_	184	_	mA
OFDM transmit mode with average TX output power set to 14 dBm		f = 866.5, Opt4, MCS6	_	184		mA

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Current consumption in SUN OFDM transmit mode with average TX output power set	I _{TX13}	f = 923.7, Opt3, MCS4, T _A = 25 °C ¹	_	184	191	mA
to 13 dBm		f = 923.7, Opt3, MCS5		184		mA
		f = 923.7, Opt3, MCS6, T _A = 25 °C ¹	_	184	191	mA
Current consumption in SUN	I _{TX12}	f = 914, Opt1, MCS2		184		mA
OFDM transmit mode at 12 dBm average		f = 914, Opt1, MCS6	_	184	_	mA
		f = 914, Opt2, MCS3		184		mA
		f = 914, Opt2, MCS6		184		mA
		f = 923.7, Opt3, MCS4	_	184	_	mA
		f = 923.7, Opt3, MCS5		184		mA
		f = 923.7, Opt3, MCS6		184		mA
		f = 866.5, Opt4, MCS4		183		mA
		f = 866.5, Opt4, MCS6	_	183		mA
Current consumption in SUN	I _{TX0}	f = 914, Opt1, MCS2	_	70.3	_	mA
OFDM transmit mode at 0 dBm average output power		f = 914, Opt1, MCS6		70.1		mA
with VREGVDD = AVDD = PAVDD = 3.3 V		f = 914, Opt2, MCS3	_	70.0	_	mA
		f = 914, Opt2, MCS6	_	69.9	_	mA
		f = 923.7, Opt3, MCS4		69.8	_	mA
		f = 923.7, Opt3, MCS5	_	69.8	_	mA
		f = 923.7, Opt3, MCS6	_	69.7		mA
		f = 866.5, Opt4, MCS4	_	69.9		mA
		f = 866.5, Opt4, MCS6		69.9		mA

1. For a detailed characteristic over temperature see Figure 4.5 Typical Radio Supply Current and Output Power vs. Temperature on page 142

4.7 Energy Mode Wake-up and Entry Time

Unless otherwise specified, these times are measured using the HFRCO at 19 MHz, with the DPLL disabled.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Wake-up Time from EM1	t _{EM1_WU}	Code execution from flash	_	3		HCLKs
		Code execution from RAM	_	1.43		μs
Wake-up Time from EM2	t _{EM2_WU}	Code execution from flash, No Voltage Scaling	_	12.2	_	μs
		Code execution from RAM, No Voltage Scaling	_	5.4	_	μs
		Voltage scaling up one level ¹	-	36.9	—	μs
		Voltage scaling up two levels ²	_	49.2	_	μs
Wake-up Time from EM3	t _{EM3_WU}	Code execution from flash, No Voltage Scaling	_	12.2		μs
		Code execution from RAM, No Voltage Scaling	_	5.4	_	μs
		Voltage scaling up one level ¹	-	36.9	_	μs
		Voltage scaling up two levels ²	_	49.2	_	μs
Wake-up Time from EM4	t _{EM4_WU}	Code execution from flash	_	24.3		ms
Entry time to EM1	t _{EM1_ENT}	Code execution from flash	-	1.13	_	μs
Entry time to EM2	t _{EM2_ENT}	Code execution from flash	_	5.4		μs
Entry time to EM3	t _{EM3_ENT}	Code execution from flash	_	5.4	_	μs
Entry time to EM4	t _{EM4_ENT}	Code execution from flash	_	10.8		μs

Table 4.11. Energy Mode Wake-up and Entry Time

Note:

1. Voltage scaling one level is between VSCALE1 and VSCALE2.

2. Voltage scaling two levels is between VSCALE0 and VSCALE2.

4.8 Flash Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Flash Supply voltage during write or erase	V _{FLASH}		1.71	_	3.8	V
Flash erase cycles before failure ¹	EC _{FLASH}	T _A ≤ 125 °C	10,000		_	cycles
Flash data retention ¹	RET _{FLASH}	T _A ≤ 125 °C	10		_	years
Program Time	t _{PROG}	one word (32-bits)	40.4	44.3	48.1	μs
		average per word over 128 words	10.4	11.4	12.5	μs
Page Erase Time	t _{PERASE}		11.8	13.3	14.6	ms
Mass Erase Time	t _{MERASE}	1920 kB	177	189	219	ms
		1152 kB	106	113	132	ms
Program Current	I _{PROG}		_	_	2.9	mA
Page Erase Current	IPERASE	Page Erase	_		1.8	mA
Mass Erase Current	I _{MERASE}	Mass Erase	_		1.9	mA
Mass Erase Current	I _{MERASE}	Mass Erase	_		1.9	

Table 4.12. Flash Characteristics

Note:

1. Flash data retention information is published in the Quarterly Quality and Reliability Report.

4.9 Sub-GHz RF Transceiver Characteristics

4.9.1 RF Constant Envelope Transmitter Characteristics

4.9.1.1 920 MHz Band +13 dBm RF Constant Envelope Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 868/915/920 MHz matching network as shown in the typical connections section. Band is 922.3 to 928.1 MHz. Emissions are measured at 13 dBm and 0 dBm. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, crystal frequency = 39.0 MHz, supply filtering as shown in the typical connections section, and RF center frequency 924 MHz.

Table 4.13.	920 MHz Band +	13 dBm RF	Constant Envelo	pe Transmitte	r Characteristics
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Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		922.3	924	928.1	MHz
Maximum TX Power	POUT _{MAX}	16 dBm devices, matching net- work as shown in the typical con- nections section ^{1 2 3}	11.4	13.4	16.1	dBm
Minimum active TX Power	POUT _{MIN}		—	-39.4	-38.9	dBm
Output power variation vs supply	POUT _{VAR_V}	3.0 V < VREGVDD = AVDD = PAVDD < 3.8 V, T = 25 °C at 13 dBm nominal settings	_	0.02	0.1	dB
		3.0 V < VREGVDD = AVDD = PAVDD < 3.8 V, T = 25 °C at 0 dBm nominal settings	_	0.02	0.1	dB
Output power variation vs temperature, peak to peak	POUT _{VAR_T}	T_A = -40 to +85 °C, VREGVDD = AVDD = PAVDD = 3.3 V, and 13 dBm nominal settings.	_	0.7	1.5	dB
		T_A = -40 to +125 °C. VREGVDD = AVDD = PAVDD = 3.3 V, and 13 dBm nominal settings.	_	0.9	2.1	dB
Output power variation vs RF frequency	POUT _{VAR_F}	VREGVDD = AVDD = PAVDD = $3.3 \text{ V}, \text{ T}_{A} = 25 \text{ °C}$	_	0.02	0.13	dB
Adjacent Channel Power 50 kbps 2FSK ^{3 4}	P _{CH_ADJ_50}	P _{OUT} = 0 dBm (1 mW), 924 MHz, 200 kHz channel spacing	_	-29.0	-26.0	dBm
		P _{OUT} = 13 dBm (20 mW), 924 MHz, 200 kHz channel spacing ⁵	_	-15.7	-15.0	dBm
Adjacent Channel Power 100 kbps 2FSK ^{3 6}	P _{CH_ADJ_100}	P _{OUT} = 0 dBm (1 mW), 924 MHz, 400 kHz channel spacing	_	-30.4	-26.0	dBm
		P _{OUT} = 13 dBm (20 mW), 924 MHz, 400 kHz channel spacing	_	-17.1	-15.0	dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Max spurious emissions,	SPUR _{TX_ARIB_0}	f ≤ 710 MHz, RBW = 100 kHz	_	-77.1	-36.0	dBm
$P_{OUT} = 0 \text{ dBm} (1 \text{ mW})^{3 4}$ with VREGVDD = PAVDD = AVDD = 3.0 V		710 MHz < f ≤ 900 MHz, RBW = 1 MHz	—	-69.4	-55.0	dBm
		900 MHz < f ≤ 915 MHz, RBW = 100 kHz	—	-78.3	-55.0	dBm
		915 MHz < f ≤ 930 MHz, RBW = 100 kHz, (except for f-fc ≤ (200+100*n) kHz)	_	-48.8	-36.0	dBm
		930 MHz < f ≤ 1000 MHz, RBW = 100 kHz	—	-75.2	-55.0	dBm
		1000 MHz < f ≤ 1215 MHz, RBW = 1 MHz	_	-67.4	-45.0	dBm
		1215 MHz < f, RBW = 1 MHz	_	-59.2	-30.0	dBm
Max spurious emissions,	SPUR _{TX_ARIB_13}	f ≤ 710 MHz, RBW = 100 kHz	_	-66.8	-36.0	dBm
P _{OUT} = 13 dBm (20 mW) ^{3 4}		710 MHz < f ≤ 900 MHz, RBW = 1 MHz	—	-56.5	-55.0	dBm
		900 MHz < f ≤ 915 MHz, RBW = 100 kHz	_	-65.3	-55.0	dBm
		915 MHz < f ≤ 930 MHz, RBW = 100 kHz, (except for f-fc ≤ (200+100*n) kHz) ⁷	_	-40.9	-36.0	dBm
		930 MHz < f ≤ 1000 MHz, RBW = 100 kHz	_	-62.9	-55.0	dBm
		1000 MHz < f ≤ 1215 MHz, RBW = 1 MHz	_	-56.1	-45.0	dBm
		1215 MHz < f, RBW = 1 MHz	_	-48.0	-30.0	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit

- 1. Supported transmit power levels are determined by the ordering part number (OPN). Transmit power ratings for all devices covered in this datasheet can be found in the Max TX Power column of the Ordering Information Table.
- 2. The transmit power for the 922.3 to 928.1 Band MHz is normally limited by regulatory agency to +13 dBm (20 mW). The 16 dBm devices are recommended with the matching network as shown in the typical connections section.
- 3. The matching network shown in the typical connections section is optimized for best efficiency at 16 dBm. The maximum output power can be above the maximum rating in certain conditions. Emissions for this band are tested at T_A = 25 °C with the output power set to 13 dBm (20 mW) and 0 dBm (1mW).
- 4. Measured per ARIB T108, Part 2 Section $3.2, f_c = 924$ MHz, 922.3 to 928.1 frequency band, 50 kbps, 2FSK, BT = 2, $\Delta f = \pm 25$ kHz, PN9 sequence, 200 kHz channel spacing, n = 1.
- 5. The margin to the regulatory limit (-15 dBm) can be increased by selecting lower BT product values. Example settings and resulting margins can be seen in the following table:

BT product	P _{CH_ADJ_50} [dBm]	Margin [dB]
2	-15.7	0.7
1.3	-20	5
1.0	-25	10
0.5	-30	15

- 6. Measured per ARIB T108, Part 2 Section 3.2, f_c = 924 MHz, 922.3 to 928.1 frequency band, 100 kbps, 2FSK, BT = 2, Δf = ± 25 kHz, PN9 sequence, 400 kHz channel spacing, n = 2.
- The spurious emission is calculated according to TELEC-T245 5th Ed. Spurious Emissions Measurement Procedure Section 4 (6) to (16)

4.9.1.2 915 MHz Band +16 dBm RF Constant Envelope Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 868/915/920 MHz matching network as shown in the typical connections section. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, crystal frequency = 39.0 MHz, supply filtering as shown in the typical connections section, and RF center frequency 915 MHz.

Table 4.14.	915 MHz Band +16 dBm RF	Constant Envelope Transmitter Characteristics
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Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
RF test frequency range	F _{RANGE}		902	915	928	MHz
Maximum TX Power	POUT _{MAX}	16 dBm devices, matching net- work as shown in the typical con- nections section ^{1 2}	14.2	15.9	18.4	dBm
Minimum active TX Power	POUT _{MIN}		—	-39.5	-38.3	dBm
Output power variation vs supply at POUT _{MAX}	POUT _{VAR_V}	3.0 V < VREGVDD = AVDD = PAVDD < 3.8 V, T = 25 °C, and at 16 dBm nominal settings		0.03	_	dB
Output power variation vs temperature, peak to peak	POUT _{VAR_T}	T_A = -40 to +85 °C with VREGVDD = AVDD = PAVDD = 3.3 V, and 16 dBm nominal set- tings.	_	0.8	_	dB
		T_A = -40 to +125 °C with VREGVDD = AVDD = PAVDD = 3.3 V, and 16 dBm nominal set- tings.	_	1.0	_	dB
Output power variation vs RF frequency	POUT _{VAR_F}	VREGVDD = AVDD = PAVDD = 3.3 V , 16 dBm nominal settings, and $T_A = 25 \text{ °C}$		0.05	_	dB
Spurious emissions of har- monics, Conducted meas-	SPUR _{HARM_FCC}	In non-restricted bands, per FCC 47 CFR §15.247 ³	_	-62.2	-20.0	dBc
urement, Test Frequency = 915 MHz ²		In restricted bands, per FCC 47 CFR §15.205 & §15.209 ^{4 5}	_	-47.2	-41.2	dBm
Unwanted signal emissions over frequency domain, Con- ducted measurement, Test Frequency = 915 MHz ²	SPUR _{OOB_FCC}	In non-restricted bands, per FCC 47 CFR §15.247 ³	_	-55.0	-20.0	dBc
		In restricted bands (30-88 MHz),per FCC 47 CFR §15.205 & §15.209 ^{4 5}	_	-64.0	-55.2	dBm
		In restricted bands (88-216 MHz), per FCC 47 CFR §15.205 & §15.209 ^{4 5}	_	-65.7	-51.7	dBm
		In restricted bands (216-960 MHz), per FCC 47 CFR §15.205 & §15.209 ^{4 5}		-63.0	-49.2	dBm
		In restricted bands (>960 MHz), per FCC 47 CFR §15.205 & §15.209 ^{4 5}		-48.2	-41.2	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Note:						
		ermined by the ordering part number (C e Max TX Power column of the Orderin			s for all devic	es cov-
		al connections section is optimized for in certain conditions. Emissions are te				
	CD Dort 15 Continue 15 24	7 Operation within the hand 000 000 M	H7			
3. FCC Title 47 Cl	FR Part 15 Section 15.24	7 Operation within the band 902-928 M	112.			
		5 Restricted bands of operation.	Π IZ.			

4.9.1.2.1 915 MHz Band 0 dBm RF Constant Envelope Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 868/915/920 MHz matching network as shown in the typical connections section. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, and DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, crystal frequency = 39.0 MHz, supply filtering as shown in the typical connections section, and RF center frequency 915 MHz.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
RF test frequency range	F _{RANGE}		902	915	928	MHz
Establish nominal settings for POUT = 0dBm	POUT _{0dBm}		—	0.8	_	dBm
Max Step Size for TX Power setting for POUT between 0 dBm to +12 dBm	POUT _{STEP}	VREGVDD = AVDD = PAVDD = 3.3 V, T = 25 °C	_	0.1	_	dB
Output power variation vs supply at POUT _{MAX}	POUT _{VAR_V}	3.0 V < VREGVDD = AVDD = PAVDD < 3.8 V, T = 25 °C, and 0 dBm nominal settings	_	0.03	0.08	dB
Output power variation vs temperature, peak to peak	POUT _{VAR_T}	T _A = -40 to +85 °C with VREGVDD = AVDD = PAVDD = 3.3 V, and 0 dBm nominal settings	_	0.7	1.8	dB
		T_A = -40 to +125 °C with VREGVDD = AVDD = PAVDD = 3.3 V, and 0 dBm nominal settings	_	0.9	2.7	dB
Output power variation vs RF frequency	POUT _{VAR_F}	VREGVDD = AVDD = PAVDD = 3.3 V, and 0 dBm nominal set- tings, T = 25 °C	—	0.08	0.2	dB
Spurious emissions of har- monics, Conducted meas- urement, Test Frequency = 915 MHz ¹	SPUR _{HARM_FCC}	In restricted bands, per FCC 47 CFR §15.205 & §15.209 ^{2 3} , and 0 dBm nominal settings		-63.3	-41.2	dBm
Unwanted signal emissions over frequency domain, Con- ducted measurement, Test Frequency = 915 MHz ¹	SPUR _{OOB_FCC}	In restricted bands (30-88 MHz),per FCC 47 CFR §15.205 & §15.209 ^{2 3} , and 0 dBm nominal settings		-64.0	-55.2	dBm
		In restricted bands (88-216 MHz), per FCC 47 CFR §15.205 & §15.209 ^{2 3} , and 0 dBm nominal settings		-65.7	-51.7	dBm
		In restricted bands (216-960 MHz), per FCC 47 CFR §15.205 & §15.209 ^{2 3} , and 0 dBm nominal settings	_	-63.0	-49.2	dBm
		In restricted bands (>960 MHz), per FCC 47 CFR §15.205 & §15.209 ^{2 3} , and 0 dBm nominal settings	_	-63.1	-41.2	dBm

Note:

1. Emissions are tested at T_A = 25 °C.

2. FCC Title 47 CFR Part 15 Section 15.205 Restricted bands of operation.

3. FCC Title 47 CFR Part 15 Section 15.209 Radiated emission limits; general requirements.

4.9.1.3 868 MHz Band +14 dBm RF Constant Envelope Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 868/915/920 MHz matching network as shown in the typical connections section. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, crystal frequency = 39.0 MHz, supply filtering as shown in the typical connections section, and RF center frequency 868.3 MHz.

Table 4.16.	868 MHz Band +14 dBm RF	Constant Envelope	Transmitter Characteristics
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Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		863	—	870	MHz
Maximum TX Power	POUT _{MAX}	VREGVDD = AVDD = PAVDD = 3.3 V, 16 dBm devices, matching network as shown in the typical connections section ¹²³	13.2	14.6	15.9	dBm
Minimum active TX Power	POUT _{MIN}		_	-38.4	_	dBm
Output power variation vs supply at POUT _{MAX}	POUT _{VAR_V}	3.0 V < REGVDD = AVDD = PAVDD < 3.8 V, T = 25 °C, and at 14 dBm nominal settings	—	0.03	_	dB
Output power variation vs temperature, peak to peak	POUT _{VAR_T}	$T_A = -40$ to +85 °C, with REGVDD = AVDD = PAVDD = 3.3 V, and 14 dBm nominal settings	_	0.8	1.3	dB
		T_A = -40 to +125 °C, with REGVDD = AVDD = PAVDD = 3.3 V, and 14 dBm nominal set- tings	_	1.0	1.6	dB
Output power variation vs RF frequency	POUT _{VAR_F}	REGVDD = AVDD = PAVDD = 3.3 V, and 14 dBm nominal set- tings, T = 25 °C	_	0.03	0.1	dB
Spurious emissions of har- monics, P _{OUT} = +14 dBm, 868.3 MHz ³	SPUR _{HARM_ETSI}	(frequencies above 1 GHz) ⁴	_	-48.2	-30.0	dBm
Unwanted emissions in spu- rious domain, Per ETSI EN $300-220-1^{3}$ ⁵ , P _{OUT} = +14	SPUR _{OOB_ETSI}	(47-74 MHz, 87.5-118 MHz, 174-230 MHz, and 470-862 MHz) ⁴	_	-68.0	-54.0	dBm
dBm, 868.3 MHz		(other frequencies below 1 GHz) ⁴	_	-60.5	-36.0	dBm
		(frequencies above 1 GHz) ⁴	_	-47.4	-30.0	dBm
Error Vector Magnitude, per IEEE 802.15.4-2020	EVM	Signal is 100 kbps DSSS O- QPSK reference packet. Modula- ted according to IEEE 802.15.4-2020 in the 868MHz band, with pseudo-random packet data content. P _{OUT} = +14 dBm.	_	6.8	35	%

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Note:						
		ermined by the ordering part number (e Max TX Power column of the Orderi			gs for all devid	ces cov-
		and MHz is normally limited to +14 dB ork as shown in the typical connectior		ie 16 dBm dev	vices are reco	ommen-
		re the maximum rating in certain cond 25 mW) and 0 dBm (1mW).	itions. Emissio	ns for this bar	nd are tested	at T _A = 25
4. Spurious emission	n limits per EN 300-220	-1 v3.1.1 5.9.2				
5. Conducted measu	urement per EN 300-22	0-1 v3.1.1 5.9.3.3.1				

4.9.1.4 470 MHz Band +16 dBm RF Constant Envelope Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 470 MHz Band matching network as shown in the typical connections section. Band is 470 to 510 MHz. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, crystal frequency = 39.0 MHz, supply filtering as shown in the typical connections section, and RF center frequency 490 MHz.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
RF test frequency range	F _{RANGE}		470	_	510	MHz
Maximum TX Power	POUT _{MAX}	PAVDD = 3.3 V, 16 dBm devices	14.9	16.2	17.6	dBm
Minimum active TX Power	POUT _{MIN}		_	-41.0		dBm
Output power variation vs supply, peak to peak	POUT _{VAR_V}	3.0 V < REGVDD = AVDD = PAVDD < 3.8 V, T = 25 °C, and at 16 dBm nominal settings		0.04	_	dB
Output power variation vs temperature, peak to peak	POUT _{VAR_T}	-40 to +85 °C at 16 dBm nominal settings	—	0.6	1.1	dB
		-40 to +125 °C at 16 dBm nominal settings	_	0.7	1.5	dB
Output power variation vs RF frequency	POUT _{VAR_F}	T = 25 °C at 16 dBm nominal set- tings	—	0.3	0.7	dB
Harmonic emissions, P _{OUT} = +16 dBm, 490 MHz ¹	SPUR _{HARM_CN}	Per China SRW Requirement, Section 2.1, frequencies below 1GHz	_	-66.2	-36.0	dBm
		Per China SRW Requirement, Section 2.1, frequencies above 1GHz	_	-62.0	-30.0	dBm
Spurious emissions, P _{OUT} = +16 dBm, 490 MHz ¹	SPUR _{OOB_CN}	Per China SRW Requirement, Section 3 (48.5-72.5MHz, 76-108MHz, 167-223MHz, 470-556MHz, and 606-798MHz)	_	-58.0	-54.0	dBm
		Per China SRW Requirement, Section 2.1 (other frequencies be- low 1GHz)		-58.4	-36.0	dBm
		Per China SRW Requirement, Section 2.1 (frequencies above 1GHz)	_	-61.4	-30.0	dBm

4.9.2 RF SUN OFDM Transmitter Characteristics

OFDM Modulation is defined in IEEE 802.15.4-2020 section 20.3. In these tables the indication "OptX, MCSy" means X as the Option number 1 through 4, and y is the MCS index 0 through 6, and PL is the Packet PPDU Length in octets. Measurements use packet length of 250 octets when data rate is 50 kbps or higher, and 20 octets packet length when lower than 50 kbps.

4.9.2.1 923 MHz Band RF SUN OFDM Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 920 MHz Band matching network as shown in the typical connections section. $POUT_{13dBm}^{1}$ is marking the nominal TX setting which is targeting POUT = +13 dBm at typical conditions.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range ²	F _{RANGE}		922.3	923.x	928.1	MHz
Active TX Power for +13 dBm TX output power set- ting ¹	POUT _{13dBm}	923.5 MHz, Opt2, MCS3	_	13.0	_	dBm
		923.5 MHz, Opt2, MCS4	_	13.0	_	dBm
		923.5 MHz, Opt2, MCS5	—	13.1	—	dBm
		923.5 MHz, Opt2, MCS6	—	13.1	—	dBm
		923.7 MHz, Opt3, MCS4 ³	11.5	13.1	14.6	dBm
		923.7 MHz ⁴ , Opt3, MCS4	10.3	13.1	15.4	dBm
		923.7 MHz, Opt3, MCS5	—	13.0	_	dBm
		923.7 MHz, Opt3, MCS6 ³	11.6	13.1	14.6	dBm
		923.7 MHz ⁴ , Opt3, MCS6	9.1	13.1	16.1	dBm
		923.6 MHz, Opt4, MCS4	_	13.0	_	dBm
		923.6 MHz, Opt4, MCS5	_	13.1	_	dBm
		923.6 MHz, Opt4, MCS6	_	13.0	_	dBm
Error Vector Magnitude over	EVM _{13dBm}	923.5 MHz, Opt2, MCS3	—	-32.2	—	dB
process variation with TX setting for POUT _{13dBm} ¹		923.5 MHz, Opt2, MCS4	_	-33.1	_	dB
6 Todahi		923.5 MHz, Opt2, MCS5	—	-32.8	—	dB
		923.5 MHz, Opt2, MCS6	—	-32.5	_	dB
		923.7 MHz, Opt3, MCS4 ³	_	-32.8	-31.0	dB
		923.7 MHz ⁴ , Opt3, MCS4	—	-32.8	-27.9	dB
		923.7 MHz, Opt3, MCS5	_	-32.4	_	dB
		923.7 MHz, Opt3, MCS6 ³	_	-32.8	-31.0	dB
		923.7 MHz ⁴ , Opt3, MCS6	_	-32.8	-28.2	dB
		923.6 MHz, Opt4, MCS4	_	-31.5	_	dB
		923.6 MHz, Opt4, MCS5	_	-31.0	_	dB
		923.6 MHz, Opt4, MCS6	—	-32.2	-	dB

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Error Vector Magnitude in to 2:1 VSWR Load over proc-	EVM _{VSWR2_13}	923.5 MHz, Opt2, MCS3, 2:1 VSWR, T _A = 25 °C	_	-27.9	—	dB
ess variation ⁵ , measured at worst case mis-match phase angle, with TX setting for		923.5 MHz, Opt2, MCS4, 2:1 VSWR, T _A = 25 °C	-	-28.5	_	dB
POUT _{13dBm} ¹		923.5 MHz, Opt2, MCS5, 2:1 VSWR, T _A = 25 °C	-	-28.2	_	dB
		923.5 MHz, Opt2, MCS6, 2:1 VSWR, T _A = 25 °C	-	-28.1	_	dB
		923.7 MHz, Opt3, MCS4, 2:1 VSWR, T _A = 25 °C ³	-	-28.5	-27.0	dB
		923.7 MHz, Opt3, MCS5, 2:1 VSWR, T _A = 25 °C	_	-28.4	_	dB
		923.7 MHz, Opt3, MCS6, 2:1 VSWR, T _A = 25 °C ³	-	-29.0	-27.5	dB
		923.6 MHz, Opt4, MCS4, 2:1 VSWR, T _A = 25 °C	_	-29.0	—	dB
		923.6 MHz, Opt4, MCS5, 2:1 VSWR, T _A = 25 °C	_	-28.9	_	dB
		923.6 MHz, Opt4, MCS6, 2:1 VSWR, T _A = 25 °C	-	-28.7	_	dB
Minimum active TX Power ¹	POUT _{MIN}	923.5 MHz, Opt2, MCS3	_	-29.2	_	dBm
		923.5 MHz, Opt2, MCS6		-29.1		dBm
		923.7 MHz, Opt3, MCS4 ³	_	-29.0	-27.3	dBm
		923.7 MHz, Opt3, MCS5		-29.0		dBm
		923.7 MHz, Opt3, MCS6 ³	_	-28.9	-27.3	dBm
		923.6 MHz, Opt4, MCS4		-29.0		dBm
		923.6 MHz, Opt4, MCS5	_	-28.9	_	dBm
		923.6 MHz, Opt4, MCS6	_	-28.9	_	dBm
Output power variation vs	PVAR _{V_13}	923.5 MHz, Opt2, MCS3	_	0.1	—	dB
PAVDD supply voltage from 3.45 V to 3.8 V with TX set-		923.5 MHz, Opt2, MCS6	_	0.1	—	dB
ting for POUT _{13dBm}		923.7 MHz, Opt3, MCS4 ³	_	0.1	0.24	dB
		923.7 MHz, Opt3, MCS5	_	0.1	_	dB
		923.7 MHz, Opt3, MCS6 ³	_	0.1	0.20	dB
		923.6 MHz, Opt4, MCS4		0.1		dB
		923.6 MHz, Opt4, MCS5	_	0.1		dB
		923.6 MHz, Opt4, MCS6	—	0.1		dB
Active TX Power for +13	POUT _{1340C}	923.7 MHz, Opt3, MCS4	_	13.2	—	dB
dBm TX output power setting at T _A = -40 °C		923.7 MHz, Opt3, MCS6	_	12.8		dB
Active TX Power for +13	POUT _{13_85C}	923.7 MHz, Opt3, MCS4		12.4		dB
dBm TX output power setting at $T_A = 85 \degree C$	_	923.7 MHz, Opt3, MCS6		12.1		dB

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Active TX Power for +13	POUT _{13_105C}	923.7 MHz, Opt3, MCS4	—	12.4		dB
dBm TX output power setting at T _A = 105 °C		923.7 MHz, Opt3, MCS6	—	11.9		dB
Output power variation vs	PVAR _{F_13}	Opt2, MCS3	_	0.1		dB
frequency with TX setting for POUT _{13dBm} . Frequency test		Opt2, MCS6	_	0.1		dB
is at MIN, TYP, and MAX of F _{RANGE}		Opt3, MCS4 ³	_	0.1	0.18	dB
' RANGE		Opt3, MCS5	_	0.1		dB
		Opt3, MCS6 ³	—	0.1	0.18	dB
		Opt4, MCS4	_	0.1		dB
		Opt4, MCS5	—	0.1		dB
		Opt4, MCS6	—	0.1	_	dB
Spurious emission at f _{SPUR}	SPUR _{ARIBL}	923.5 MHz, Opt2, MCS3		-59.8	-36	dBm
below 710 MHz, while on channel desired signal is at		923.5 MHz, Opt2, MCS6	_	-60.4	-36	dBm
POUT = +13 dBm, conduc- ted measurement with 100		923.7 MHz, Opt3, MCS4	—	-59.7	-36	dBm
kHz RBW ^{6 7}		923.7 MHz, Opt3, MCS5	—	-60.2	-36	dBm
		923.7 MHz, Opt3, MCS6	_	-60.3	-36	dBm
		923.6 MHz, Opt4, MCS4	—	-60.4	-36	dBm
		923.6 MHz, Opt4, MCS5	—	-60.4	-36	dBm
		923.6 MHz, Opt4, MCS6	—	-60.5	-36	dBm
Spurious emission at 710	SPUR _{ARIB710}	923.5 MHz, Opt2, MCS3 ⁸	—	-60.7	-55	dB
$\label{eq:mhz} \begin{array}{l} \text{MHz} < \text{f}_{\text{SPUR}} \leq 900 \text{ MHz}, \\ \text{while on channel desired sig-} \end{array}$		923.5 MHz, Opt2, MCS6 ⁸	_	-61.5	-55	dB
nal is at POUT = +13 dBm, conducted measurement		923.7 MHz, Opt3, MCS4 ⁸	_	-61.1	-55	dB
with 1 MHz RBW ^{6 7}		923.7 MHz, Opt3, MCS5 ⁸	—	-61.6	-55	dB
		923.7 MHz, Opt3, MCS6 ⁸	_	-61.2	-55	dB
		923.6 MHz, Opt4, MCS4 ⁸	_	-61.0	-55	dB
		923.6 MHz, Opt4, MCS5 ⁸	_	-60.8	-55	dB
		923.6 MHz, Opt4, MCS6 ⁸	_	-60.7	-55	dB
Spurious emission at 900	SPUR _{ARIB900}	923.5 MHz, Opt2, MCS3 ⁸		-68.4	-55	dBm
$MHz < f_{SPUR} \le 915 MHz,$ while on channel desired sig-		923.5 MHz, Opt2, MCS6 ⁸	_	-69.5	-55	dBm
nal is at POUT = +13 dBm, conducted measurement		923.7 MHz, Opt3, MCS4 ⁸	_	-68.9	-55	dBm
with 100 kHz RBW ^{6 7}		923.7 MHz, Opt3, MCS5 ⁸	—	-70.0	-55	dBm
		923.7 MHz, Opt3, MCS6 ⁸	—	-68.8	-55	dBm
		923.6 MHz, Opt4, MCS4 ⁸	—	-69.8	-55	dBm
		923.6 MHz, Opt4, MCS5 ⁸	—	-68.9	-55	dBm
		923.6 MHz, Opt4, MCS6 ⁸	_	-69.0	-55	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Spurious emission at 915	SPUR _{ARIB915}	923.5 MHz, Opt2, MCS3 ⁹	—	-37.3	-36	dB
$MHz < f_{SPUR} \le 930 MHz ex-$ cept within 200 kHz of occu-		923.5 MHz, Opt2, MCS6 ⁹	_	-38.2	-36	dB
pied channel which is an in- teger number of 200 kHz		923.7 MHz, Opt3, MCS4 ⁹		-47.3	-36	dB
wide radio channel units, while on channel desired sig-		923.7 MHz, Opt3, MCS5 ⁹	_	-46.8	-36	dB
nal is at POUT = +13 dBm, conducted measurement		923.7 MHz, Opt3, MCS6 ⁹	_	-46.6	-36	dB
with 100 kHz RBW, and ARIB STD-T108 part 2, sec- tion 3.2.8 and sections 3.2.7 (3) and $(4)^7$		923.6 MHz, Opt4, MCS4 ⁹	_	-44.6	-36	dB
		923.6 MHz, Opt4, MCS5 ⁹	_	-44.9	-36	dB
		923.6 MHz, Opt4, MCS6 ⁹		-45.3	-36	dB
Spurious emission at 930	SPUR _{ARIB930}	923.5 MHz, Opt2, MCS3 ⁸	_	-67.5	-55	dBm
$MHz < f_{SPUR} \le 1000 MHz$, while on channel desired sig-		923.5 MHz, Opt2, MCS6 ⁸		-67.7	-55	dBm
nal is at POUT = +13 dBm, conducted measurement		923.7 MHz, Opt3, MCS4 ⁸	_	-67.5	-55	dBm
with 100 kHz RBW ^{6 7}		923.7 MHz, Opt3, MCS5 ⁸	_	-68.6	-55	dBm
		923.7 MHz, Opt3, MCS6 ⁸	_	-67.3	-55	dBm
		927.9 MHz, Opt3, MCS4 ⁸	_	-58.0	-55	dBm
		927.9 MHz, Opt3, MCS5 ⁸	_	-63.3	-55	dBm
		927.9 MHz, Opt3, MCS6 ⁸		-60.0	-55	dBm
		923.6 MHz, Opt4, MCS4 ⁸	_	-67.0	-55	dBm
		923.6 MHz, Opt4, MCS5 ⁸	_	-67.5	-55	dBm
		923.6 MHz, Opt4, MCS6 ⁸	_	-67.5	-55	dBm
Spurious emission at 1000	SPUR _{ARIB1000}	923.5 MHz, Opt2, MCS3		-49.1	-45	dB
$MHz < f_{SPUR} \le 1215 MHz$, while on channel desired sig-		923.5 MHz, Opt2, MCS6	_	-48.6	-45	dB
nal is at POUT = +13 dBm, conducted measurement		923.7 MHz, Opt3, MCS4		-48.9	-45	dB
with 1 MHz RBW ^{6 7}		923.7 MHz, Opt3, MCS5	_	-48.6	-45	dB
		923.7 MHz, Opt3, MCS6	_	-48.9	-45	dB
		923.6 MHz, Opt4, MCS4		-48.9	-45	dB
		923.6 MHz, Opt4, MCS5	_	-48.5	-45	dB
		923.6 MHz, Opt4, MCS6	_	-48.7	-45	dB
Spurious emission at 1215 MHz < f _{SPUR} , while on chan-	SPUR _{ARIB1215}	923.5 MHz, Opt2, MCS3	_	-46.7	-30	dBm
nel desired signal is at POUT		923.5 MHz, Opt2, MCS6	—	-46.6	-30	dBm
= +13 dBm, conducted measurement with 1 MHz		923.7 MHz, Opt3, MCS4	—	-51.4	-30	dBm
RBW ^{6 7}		923.7 MHz, Opt3, MCS5	—	-49.7	-30	dBm
		923.7 MHz, Opt3, MCS6	—	-48.9	-30	dBm
		923.6 MHz, Opt4, MCS4		-47.4	-30	dBm
		923.6 MHz, Opt4, MCS5	—	-49.4	-30	dBm
		923.6 MHz, Opt4, MCS6		-49.0	-30	dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Adjacent Channel Leakage	ACLP _{ARIB_13dBm}	923.5 MHz, Opt2, MCS3		-20.9	-15	dBm
Power while on channel de- sired signal is at POUT =		923.5 MHz, Opt2, MCS4		-20.6	-15	dBm
+13 dBm, conducted meas- urement integrating power		923.5 MHz, Opt2, MCS5		-20.6	-15	dBm
from the channel edge out-		923.5 MHz, Opt2, MCS6		-21.4	-15	dBm
ward 200 kHz, and ARIB STD-T108 part 2, section		923.7 MHz, Opt3, MCS4		-19.8	-15	dBm
3.2.7 (4) ⁷		923.7 MHz, Opt3, MCS5		-19.8	-15	dBm
		923.7 MHz, Opt3, MCS6		-19.8	-15	dBm
		923.6 MHz, Opt4, MCS4		-17.9	-15	dBm
		923.6 MHz, Opt4, MCS5		-18.2	-15	dBm
		923.6 MHz, Opt4, MCS6		-18.2	-15	dBm
Adjacent Channel Leakage	ACLP _{ARIB_0dBm}	923.5 MHz, Opt2, MCS3		-45.6	-26	dBm
Power while on channel de- sired signal is at POUT = 0		923.5 MHz, Opt2, MCS4		-45.5	-26	dBm
dBm, conducted measure- ment integrating power from		923.5 MHz, Opt2, MCS5		-45.4	-26	dBm
the channel edge outward		923.5 MHz, Opt2, MCS6		-45.5	-26	dBm
200 kHz, and ARIB STD- T108 part 2, section 3.2.7		923.7 MHz, Opt3, MCS4	_	-42.9	-26	dBm
(3) ⁷		923.7 MHz, Opt3, MCS5		-42.9	-26	dBm
		923.7 MHz, Opt3, MCS6		-42.8	-26	dBm
		923.6 MHz, Opt4, MCS4		-40.5	-26	dBm
		923.6 MHz, Opt4, MCS5	_	-40.6	-26	dBm
		923.6 MHz, Opt4, MCS6	_	-40.6	-26	dBm
Adjacent Channel Power Ra-	ACPRWISUN	923.5 MHz, Opt2, MCS3	20	31.9	_	dBc
tio while on channel desired signal is at POUT = +13 dBm		923.5 MHz, Opt2, MCS4	20	32.2	_	dBc
per Wi-SUN Alliance ^{7 10}		923.5 MHz, Opt2, MCS5	20	32.1	_	dBc
		923.5 MHz, Opt2, MCS6	20	32.4	_	dBc
		923.7 MHz, Opt3, MCS4	20	31.8	_	dBc
		923.7 MHz, Opt3, MCS5	20	31.7	—	dBc
		923.7 MHz, Opt3, MCS6	20	31.6	—	dBc
		923.6 MHz, Opt4, MCS4	20	30.5	—	dBc
		923.6 MHz, Opt4, MCS5	20	30.6	_	dBc
		923.6 MHz, Opt4, MCS6	20	30.7	_	dBc

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Alternate Adjacent Channel Power Ratio while on chan- nel desired signal is at POUT = +13 dBm per Wi-SUN Alli- ance ^{7 10}	A2CPR _{WISUN}	923.5 MHz, Opt2, MCS3	40	48.5	_	dBc
		923.5 MHz, Opt2, MCS4	40	48.4	_	dBc
		923.5 MHz, Opt2, MCS5	40	48.5	_	dBc
		923.5 MHz, Opt2, MCS6	40	48.4	_	dBc
		923.7 MHz, Opt3, MCS4	40	48.8	_	dBc
		923.7 MHz, Opt3, MCS5	40	48.8	_	dBc
		923.7 MHz, Opt3, MCS6	40	48.8	_	dBc
		923.6 MHz, Opt4, MCS4	40	46.4	_	dBc
		923.6 MHz, Opt4, MCS5	40	46.3	_	dBc
		923.6 MHz, Opt4, MCS6	40	46.4	_	dBc

1. With compliance to ARIB STD-T108 part 2, Wi-SUN Alliance PHY Working Group Technical Specification Revision 1VA9, and IEEE 802.15.4-2020 Section 20 except for max power limit

- 2. Typical frequency is defined in the Test Condition column, and varies on selected Option.
- 3. Min/Max numbers are measured at typical voltage, at typical F_{RANGE} frequency, and at T_A = 25 °C.
- 4. Frequency value used for typical measurements
- 5. Other operating conditions are kept at Typical values.
- 6. Per ARIB STD-T108 part 2, section 3.2.8
- 7. Emissions are measured at T_A = 25 $^{\circ}$ C
- 8. The spurious emission is calculated according to TELEC-T245 5th Ed. Spurious Emissions Measurement Procedure Section 4 (1) to (4).
- 9. The spurious emission is calculated according to TELEC-T245 5th Ed. Spurious Emissions Measurement Procedure Section 4 (6) to (16).
- 10. All Operating Conditions are Typical / Nominal only in accordance to Wi-SUN Alliance PHY Working Group Technical Specification Revision 1VA9 section 8.2.7.

4.9.2.2 914 MHz Band RF SUN OFDM Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 915 MHz Band matching network as shown in the typical connections section. POUT_{16dBm}¹ is marking the nominal TX setting which is targeting +16 dBm output power at typical conditions. $POUT_{12dBm}^{1}$ is marking the nominal TX setting which is targeting +12 dBm output power at typical conditions.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		902	914	928	MHz
Active TX Power for +16	POUT _{16dBm}	Opt1, MCS2 ²	14.8	16.1	17.3	dBm
dBm TX output power set- ting ¹		Opt1, MCS2	14.1	16.1	18.2	dBm
		Opt1, MCS3	_	16.1	_	dBm
		Opt1, MCS4	_	16.0	—	dBm
		Opt1, MCS5	_	16.0	_	dBm
		Opt1, MCS6 ²	14.7	16.0	17.3	dBm
		Opt1, MCS6	14.1	16.0	17.4	dBm
		Opt2, MCS3 ²	14.8	16.1	17.3	dBm
		Opt2, MCS3	14.2	16.1	17.5	dBm
		Opt2, MCS4	_	16.0	_	dBm
		Opt2, MCS5	_	16.1	_	dBm
		Opt2, MCS6 ²	14.8	16.0	17.2	dBm
		Opt2, MCS6	12.6	16.0	19.2	dBm
		Opt3, MCS4	_	16.0	—	dBm
		Opt3, MCS6	_	16.1	—	dBm
Error Vector Magnitude over	EVM _{16dBm}	Opt1, MCS2	_	-25.4	_	dB
process variation with TX setting for POUT _{16dBm} ¹		Opt1, MCS3	_	-26.1	_	dB
		Opt1, MCS4	_	-25.9	_	dB
		Opt1, MCS5	_	-26.5	_	dB
		Opt1, MCS6	_	-26.4	_	dB
		Opt2, MCS3	_	-25.5	_	dB
		Opt2, MCS4	_	-26.3	_	dB
		Opt2, MCS5	—	-26.4	—	dB
		Opt2, MCS6		-25.7	_	dB
		Opt3, MCS4	_	-26.0	_	dB
	1		1	1	1	1

Opt3, MCS6

Table 4.19. 914 MHz Band RF SUN OFDM Transmitter Characteristics

dB

-26.5

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Error Vector Magnitude in to 2:1 VSWR Load over process variation ³ , measured at	EVM _{VSWR2_16}	Opt1, MCS2, 2:1 VSWR, T _A = 25 °C ²	_	-20.7	-19.2	dB
worst case mis-match phase angle, with TX settings for		Opt1, MCS3, 2:1 VSWR, T _A = 25 °C	_	-21.0	_	dB
POUT _{16dBm} ¹		Opt1, MCS4, 2:1 VSWR, T _A = 25 °C	—	-21.1	—	dB
		Opt1, MCS5, 2:1 VSWR, T _A = 25 °C	—	-21.2	_	dB
		Opt1, MCS6, 2:1 VSWR, T _A = 25 °C ²	_	-21.3	-19.5	dB
		Opt2, MCS3, 2:1 VSWR, T _A = 25 °C ²	—	-21.4	-19.5	dB
		Opt2, MCS4, 2:1 VSWR, T _A = 25 °C	_	-21.6	—	dB
		Opt2, MCS5, 2:1 VSWR, T _A = 25 °C	_	-21.7	_	dB
		Opt2, MCS6, 2:1 VSWR, T _A = 25 °C ²	—	-21.6	-20.0	dB
		Opt3, MCS4, 2:1 VSWR, T _A = 25 °C	—	-21.9	_	dB
		Opt3, MCS6, 2:1 VSWR, T _A = 25 °C	—	-22.0	—	dB
Output power variation vs	PVAR _{V_16}	Opt1, MCS2 ²	_	0.1	0.25	dB
PAVDD supply voltage from 3.45 V to 3.8 V with TX set-		Opt1, MCS3	_	0.1	_	dB
ting for POUT _{16dBm}		Opt1, MCS4	_	0.1	_	dB
		Opt1, MCS5	_	0.1	_	dB
		Opt1, MCS6 ²	—	0.1	0.45	dB
		Opt2, MCS3 ²	_	0.1	0.27	dB
		Opt2, MCS4	_	0.1	_	dB
		Opt2, MCS5	_	0.1	_	dB
		Opt2, MCS6 ²		0.1	0.26	dB
		Opt3, MCS4	_	0.1	_	dB
		Opt3, MCS6	_	0.1		dB
Active TX Power for +16	POUT _{1640C}	Opt1, MCS2 ⁴		16.1	_	dBm
dBm TX output power setting at $T_A = -40 \ ^{\circ}C$		Opt1, MCS6 ⁴	_	16.2	_	dBm
		Opt2, MCS3 ⁴	_	16.2		dBm
		Opt2, MCS6 ⁴	_	16.0	_	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Active TX Power for +16	POUT _{16_85C}	Opt1, MCS2 ⁴	—	15.6	_	dBm
dBm TX output power setting at $T_A = 85 \degree C$		Opt1, MCS6 ⁴	—	15.7	_	dBm
		Opt2, MCS3 ⁴	—	15.7	_	dBm
		Opt2, MCS6 ⁴	_	15.5		dBm
Active TX Power for +16	POUT _{16_105C}	Opt1, MCS2 ⁴	_	15.5	_	dBm
dBm TX output power setting at T _A = 105 °C		Opt1, MCS6 ⁴	_	15.5		dBm
		Opt2, MCS3 ⁴		15.6		dBm
		Opt2, MCS6 ⁴	_	15.4		dBm
Output power variation vs	PVAR _{F 16}	Opt1, MCS2 ²		0.15	0.39	dB
frequency with TX setting for POUT _{16dBm} . Frequency test		Opt1, MCS3		0.15		dB
FOUT 16dBm. Frequency test is at MIN, TYP, and MAX of F _{RANGE}		Opt1, MCS4		0.15		dB
		Opt1, MCS5	_	0.15		dB
		Opt1, MCS6 ²	_	0.15	0.43	dB
		Opt2, MCS3 ²		0.15	0.38	dB
		Opt2, MCS4		0.15		dB
		Opt2, MCS5	_	0.15		dB
		Opt2, MCS6 ²	_	0.15	0.38	dB
		Opt3, MCS4	_	0.15		dB
		Opt3, MCS6	_	0.15	_	dB
Active TX Power for +12	POUT _{12dBm}	Opt1, MCS2 ²	10.7	12.1	13.3	dBm
dBm TX output power set- ting ¹		Opt1, MCS2	9.1	12.1	14.5	dBm
		Opt1, MCS3	_	12.1	_	dBm
		Opt1, MCS4	—	12.1	_	dBm
		Opt1, MCS5	—	12.1	_	dBm
		Opt1, MCS6 ²	10.6	12.1	13.3	dBm
		Opt1, MCS6	7.3	12.1	16.3	dBm
		Opt2, MCS3 ²	10.6	12.0	13.2	dBm
		Opt2, MCS3	9.5	12.0	14.3	dBm
		Opt2, MCS4		12.1	_	dBm
		Opt2, MCS5	—	12.1		dBm
		Opt2, MCS6 ²	10.6	12.1	13.2	dBm
		Opt2, MCS6	7.5	12.1	15.2	dBm
		Opt3, MCS4		12.1		dBm
		Opt3, MCS6	—	12.1		dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Error Vector Magnitude over	EVM _{12dBm}	Opt1, MCS2	_	-34.2		dB
process variation with TX setting for POUT _{12dBm} ¹		Opt1, MCS3	_	-34.7	—	dB
		Opt1, MCS4	—	-34.1	_	dB
		Opt1, MCS5	—	-34.3	—	dB
		Opt1, MCS6	—	-34.6	_	dB
		Opt2, MCS3	_	-34.3	_	dB
		Opt2, MCS4	—	-34.6	—	dB
		Opt2, MCS5	_	-34.6	_	dB
		Opt2, MCS6	—	-34.1	—	dB
		Opt3, MCS4	_	-34.0	—	dB
		Opt3, MCS6	_	-34.4	_	dB
Error Vector Magnitude in to 2:1 VSWR Load over proc- ess variation ³ , measured at worst case mis-match phase angle, with TX settings for	EVM _{VSWR2_12}	Opt1, MCS2, 2:1 VSWR, T _A = 25 °C ²	—	-31.1	-28.0	dB
		Opt1, MCS3, 2:1 VSWR, T _A = 25 °C	_	-30.6	_	dB
POUT _{12dBm} ¹		Opt1, MCS4, 2:1 VSWR, T _A = 25 °C	—	-30.1	—	dB
		Opt1, MCS5, 2:1 VSWR, T _A = 25 °C	_	-30.5	—	dB
		Opt1, MCS6, 2:1 VSWR, T _A = 25 °C ²	—	-30.6	-28.3	dB
		Opt2, MCS3, 2:1 VSWR, T _A = 25 °C ²	_	-30.2	-28.7	dB
		Opt2, MCS4, 2:1 VSWR, T _A = 25 °C	_	-29.8	—	dB
		Opt2, MCS5, 2:1 VSWR, T _A = 25 °C	_	-30.7	_	dB
		Opt2, MCS6, 2:1 VSWR, T _A = 25 °C ²	_	-29.7	-28.6	dB
		Opt3, MCS4, 2:1 VSWR, T _A = 25 °C	_	-30.2	_	dB
		Opt3, MCS6, 2:1 VSWR, T _A = 25 °C	_	-29.5	_	dB

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Output power variation vs	PVAR _{V_12}	Opt1, MCS2 ²		0.1	0.17	dB
PAVDD supply voltage from 3.45 V to 3.8 V with TX set-		Opt1, MCS3	_	0.1	_	dB
ting for POUT _{12dBm}		Opt1, MCS4	_	0.1	_	dB
		Opt1, MCS5	_	0.1	_	dB
		Opt1, MCS6 ²	—	0.1	0.23	dB
		Opt2, MCS3 ²	_	0.1	0.17	dB
		Opt2, MCS4	_	0.1	_	dB
		Opt2, MCS5	_	0.1		dB
		Opt2, MCS6 ²	—	0.1	0.14	dB
		Opt3, MCS4	_	0.1		dB
		Opt3, MCS6		0.1		dB
Active TX Power for +12 dBm TX output power setting	POUT _{1240C}	Opt1, MCS2 ⁴	—	12.0		dBm
at $T_A = -40 \ ^{\circ}C$		Opt1, MCS6 ⁴	—	12.1	—	dBm
		Opt2, MCS3 ⁴	—	12.1	_	dBm
		Opt2, MCS6 ⁴	_	12.0	_	dBm
Active TX Power for +12	POUT _{12_85C}	Opt1, MCS2 ⁴	_	11.4	_	dBm
dBm TX output power setting at $T_A = 85 \degree C$		Opt1, MCS6 ⁴	_	11.7	_	dBm
		Opt2, MCS3 ⁴	_	11.5	_	dBm
		Opt2, MCS6 ⁴	_	11.2	_	dBm
Active TX Power for +12	POUT _{12_105C}	Opt1, MCS2 ⁴	_	11.2		dBm
dBm TX output power setting at $T_A = 105 \degree C$		Opt1, MCS6 ⁴		11.4		dBm
		Opt2, MCS3 ⁴		11.3		dBm
		Opt2, MCS6 ⁴		11.0		dBm
Output power variation vs	PVAR _{F_12}	Opt1, MCS2 ²		0.1	0.32	dB
frequency with TX setting for POUT _{12dBm} . Frequency test		Opt1, MCS3		0.1		dB
is at MIN, TYP, and MAX of		Opt1, MCS4		0.1		dB
F _{RANGE}		Opt1, MCS5		0.1	_	dB
		Opt1, MCS6 ²	_	0.1	0.50	dB
		Opt2, MCS3 ²		0.1	0.31	dB
		Opt2, MCS4		0.1		dB
		Opt2, MCS5		0.1	_	dB
		Opt2, MCS6 ²	_	0.1	0.34	dB
		Opt3, MCS4		0.1		dB
		Opt3, MCS6		0.1	_	dB

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Minimum active TX Power,	POUT _{MIN}	Opt1, MCS2 ²	_	-29.1	-27.6	dBm
PAVDD is Minimum of 3.45 V, and Typical of 3.6 V, and		Opt1, MCS3	_	-28.9		dBm
max of 3.8 V ¹		Opt1, MCS4		-28.9		dBm
		Opt1, MCS5		-28.8		dBm
		Opt1, MCS6 ²	_	-28.7	-27.2	dBm
		Opt2, MCS3 ²		-29.3	-27.7	dBm
		Opt2, MCS4	_	-29.2	_	dBm
		Opt2, MCS5		-29.2	_	dBm
		Opt2, MCS6 ²	_	-29.2	-27.7	dBm
		Opt3, MCS4	_	-29.0	_	dBm
		Opt3, MCS6	_	-29.1	_	dBm
Max Step Size for TX Power setting for POUT between 0 dBm to +12 dBm	POUT _{STEP}	VREGVDD = AVDD = PAVDD = 3.6 V, T = 25 °C	_	0.1	_	dB
Spurious emissions of har- monics in non-restricted bands using average power detector, per FCC 47 CFR Part 15.247 with TX setting	HARM _{FCCNR}	Opt1, MCS2		-68.7	-20	dBc
		Opt1, MCS3		-67.7	-20	dBc
		Opt1, MCS4	_	-68.4	-20	dBc
for POUT _{16dBm} ^{5 6}		Opt1, MCS5	_	-69.0	-20	dBc
		Opt1, MCS6	_	-67.9	-20	dBc
		Opt2, MCS3	—	-65.5	-20	dBc
		Opt2, MCS4		-64.8	-20	dBc
		Opt2, MCS5	—	-66.4	-20	dBc
		Opt2, MCS6		-66.2	-20	dBc
		Opt3, MCS4	—	-63.3	-20	dBc
		Opt3, MCS6		-63.2	-20	dBc
Spurious emissions of har-	HARM _{FCCRS}	Opt1, MCS2	—	-59.0	-41.2	dBm
monics in restricted bands using average power detec-		Opt1, MCS3	_	-59.2	-41.2	dBm
tor, per FCC 47 CFR Part 15.247, Part 15.205, and		Opt1, MCS4	—	-58.8	-41.2	dBm
Part 15.209 with TX setting		Opt1, MCS5	—	-59.0	-41.2	dBm
for POUT _{16dBm} ^{5 6}		Opt1, MCS6	—	-59.7	-41.2	dBm
		Opt2, MCS3	—	-57.6	-41.2	dBm
		Opt2, MCS4		-57.0	-41.2	dBm
		Opt2, MCS5		-57.5	-41.2	dBm
		Opt2, MCS6		-57.5	-41.2	dBm
		Opt3, MCS4	_	-56.5	-41.2	dBm
		Opt3, MCS6	_	-55.0	-41.2	dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Spurious emissions out-of-		Opt1, MCS2	_	-41.0	-20	dBc
band, in non-restricted bands per FCC 47 CFR Part 15.247		Opt1, MCS3	_	-34.9	-20	dBc
with TX setting for POUT _{16dBm} ⁶		Opt1, MCS4	_	-34.5	-20	dBc
FOUT _{16dBm}		Opt1, MCS5		-38.0	-20	dBc
		Opt1, MCS6		-39.4	-20	dBc
		Opt2, MCS3		-38.9	-20	dBc
		Opt2, MCS4		-31.9	-20	dBc
		Opt2, MCS5		-31.6	-20	dBc
		Opt2, MCS6		-43.3	-20	dBc
		Opt3, MCS4		-53.7	-20	dBc
		Opt3, MCS6	_	-57.1	-20	dBc
Spurious emissions out-of-	OOB _{FCC30}	Opt1, MCS2	_	-59.7	-41.2	dBm
band, in restricted bands (30-88 MHz) per FCC 47		Opt1, MCS3	_	-59.9	-41.2	dBm
CFR Part 15.247, Part 15.205, and Part 15.209 with		Opt1, MCS4	_	-59.9	-41.2	dBm
TX setting for $POUT_{16dBm}^{6}$		Opt1, MCS5		-60.0	-41.2	dBm
		Opt1, MCS6		-60.0	-41.2	dBm
		Opt2, MCS3		-60.0	-41.2	dBm
		Opt2, MCS4		-59.7	-41.2	dBm
		Opt2, MCS5	_	-59.9	-41.2	dBm
		Opt2, MCS6	_	-59.9	-41.2	dBm
		Opt3, MCS4		-59.9	-41.2	dBm
		Opt3, MCS6	_	-59.9	-41.2	dBm
Spurious emissions out-of-	OOB _{FCC88}	Opt1, MCS2	_	-61.1	-41.2	dBm
band, in restricted bands (88-216 MHz) per FCC 47		Opt1, MCS3		-61.1	-41.2	dBm
CFR Part 15.247, Part 15.205, and Part 15.209 with		Opt1, MCS4	_	-61.0	-41.2	dBm
TX setting for $POUT_{16dBm}^{6}$		Opt1, MCS5	_	-61.2	-41.2	dBm
		Opt1, MCS6		-61.5	-41.2	dBm
		Opt2, MCS3	_	-61.2	-41.2	dBm
		Opt2, MCS4		-61.5	-41.2	dBm
		Opt2, MCS5	_	-61.4	-41.2	dBm
		Opt2, MCS6		-61.4	-41.2	dBm
		Opt3, MCS4	_	-61.4	-41.2	dBm
		Opt3, MCS6	_	-61.3	-41.2	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Spurious emissions out-of-	OOB _{FCC216}	Opt1, MCS2		-61.6	-41.2	dBm
band, in restricted bands (216-960 MHz) per FCC 47		Opt1, MCS3	_	-60.6	-41.2	dBm
CFR Part 15.247, Part 15.205, and Part 15.209 with		Opt1, MCS4	_	-60.6	-41.2	dBm
TX setting for POUT _{16dBm} ⁶		Opt1, MCS5		-60.7	-41.2	dBm
		Opt1, MCS6		-60.6	-41.2	dBm
		Opt2, MCS3	_	-60.8	-41.2	dBm
		Opt2, MCS4	_	-60.8	-41.2	dBm
		Opt2, MCS5		-60.7	-41.2	dBm
		Opt2, MCS6		-60.8	-41.2	dBm
		Opt3, MCS4	_	-60.8	-41.2	dBm
		Opt3, MCS6		-60.8	-41.2	dBm
Spurious emissions out-of-	OOB _{FCC960}	Opt1, MCS2		-57.5	-41.2	dBm
band, in restricted bands (>960 MHz) per FCC 47		Opt1, MCS3		-57.3	-41.2	dBm
CFR Part 15.247, Part 15.205, and Part 15.209 with		Opt1, MCS4		-57.0	-41.2	dBm
TX setting for $POUT_{16dBm}^{6}$		Opt1, MCS5		-57.4	-41.2	dBm
		Opt1, MCS6		-58.0	-41.2	dBm
		Opt2, MCS3		-57.1	-41.2	dBm
		Opt2, MCS4		-57.6	-41.2	dBm
		Opt2, MCS5		-57.6	-41.2	dBm
		Opt2, MCS6		-57.5	-41.2	dBm
		Opt3, MCS4		-57.3	-41.2	dBm
		Opt3, MCS6	—	-57.4	-41.2	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Power Spectral Density (Average method per ANSI	PSD _{3kHz_16}	Opt1, MCS2	_	-3.9	_	dBm/ 3kHz
C63. 10-2020 11.10.3 AVGPSD-1) at frequency of highest level for a 3 kHz win-		Opt1, MCS3	_	-3.1	_	dBm/ 3kHz
dow with TX setting for POUT _{16dBm} ^{1 6}		Opt1, MCS4	_	-2.7	_	dBm/ 3kHz
		Opt1, MCS5	_	-2.6	_	dBm/ 3kHz
		Opt1, MCS6	_	-2.5	—	dBm/ 3kHz
		Opt2, MCS3	_	-2.7	_	dBm/ 3kHz
		Opt2, MCS4	_	-2.5	_	dBm/ 3kHz
		Opt2, MCS5	—	-2.1	_	dBm/ 3kHz
		Opt2, MCS6	_	-2.0		dBm/ 3kHz
		Opt3, MCS4	_	0.3	_	dBm/ 3kHz
		Opt3, MCS6	_	1.0	_	dBm/ 3kHz
Power Spectral Density (Average method per ANSI	PSD _{3kHz_12}	Opt1, MCS2	_	-7.9		dBm/ 3kHz
C63. 10-2020 11.10.3 AVGPSD-1) at frequency of highest level for a 3 kHz win-		Opt1, MCS3	_	-7.0	_	dBm/ 3kHz
dow with TX setting for POUT _{12dBm} ^{1 6}		Opt1, MCS4	_	-6.8		dBm/ 3kHz
		Opt1, MCS5	_	-6.6	_	dBm/ 3kHz
		Opt1, MCS6	_	-6.4	_	dBm/ 3kHz
		Opt2, MCS3	_	-6.8	_	dBm/ 3kHz
		Opt2, MCS4	_	-6.5		dBm/ 3kHz
		Opt2, MCS5	_	-6.1		dBm/ 3kHz
		Opt2, MCS6	_	-6.1	_	dBm/ 3kHz
		Opt3, MCS4	_	-3.7		dBm/ 3kHz
		Opt3, MCS6	_	-3.1		dBm/ 3kHz

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Adjacent Channel Power Ra-	ACPRWISUN	Opt1, MCS2	20	22.3	_	dBc
tio with TX setting for POUT _{16dBm} per Wi-SUN Alli-		Opt1, MCS3	20	22.7	_	dBc
ance ⁶⁷		Opt1, MCS4	20	22.8	_	dBc
		Opt1, MCS5	20	22.9	_	dBc
		Opt1, MCS6	20	23.0	_	dBc
		Opt2, MCS3	20	25.3	_	dBc
		Opt2, MCS4	20	25.6	—	dBc
		Opt2, MCS5	20	25.6	_	dBc
		Opt2, MCS6	20	25.8	—	dBc
		Opt3, MCS4	20	25.3	_	dBc
		Opt3, MCS6	20	25.4	—	dBc
Alternate Adjacent Channel	A2CPR _{WISUN}	Opt1, MCS2	40	49.6	_	dBc
Power Ratio with TX setting for POUT _{16dBm} per Wi-SUN		Opt1, MCS3	40	49.7	_	dBc
Alliance ^{6 7}		Opt1, MCS4	40	49.7	—	dBc
		Opt1, MCS5	40	49.7	—	dBc
		Opt1, MCS6	40	49.6	—	dBc
		Opt2, MCS3	40	49.4	—	dBc
		Opt2, MCS4	40	49.5	_	dBc
		Opt2, MCS5	40	49.4	-	dBc
		Opt2, MCS6	40	48.4	_	dBc
		Opt3, MCS4	40	48.5	_	dBc
		Opt3, MCS6	40	48.5	—	dBc

1. With compliance to FCC Title 47 CFR Part 15.247, Wi-SUN Alliance PHY Working Group Technical Specification Revision 1VA9, and IEEE 802.15.4-2020 Section 20

- 2. Min/Max numbers are measured at typical voltage, at typical F_{RANGE} frequency, and at T_A = 25 °C.
- 3. Other operating conditions are kept at Typical values.
- 4. Measured at typical voltage and at typical $\mathsf{F}_{\mathsf{RANGE}}$ frequency
- 5. For 902 MHz $\leq f_0 \leq$ 928 MHz the harmonics at 2*f₀, 7*f₀ and part of 6*f₀ will end up in the non-restricted bands. The other harmonics are in the restricted bands.
- 6. Emissions are measured at T_A = 25 °C
- All Operating Conditions are Typical / Nominal only in accordance to Wi-SUN Alliance PHY Working Group Technical Specification Revision 1VA9 section 8.2.7.

4.9.2.3 866 MHz Band RF SUN OFDM Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 868 MHz Band matching network as shown in the typical connections section. $POUT_{14dBm}^{1}$ is marking the nominal TX setting which is targeting POUT = +14 dBm at typical conditions.

Table 4.20. 866 MHz Band RF SUN OFDM Transmitter Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
RF test frequency range	F _{RANGE}		863.1	866.5	876	MHz
Active TX Power for +14	POUT _{14dBm}	Opt4, MCS2		14.1	_	dBm
dBm TX output power set- ting ¹		Opt4, MCS4		14.1	_	dBm
		Opt4, MCS5		14.2	_	dBm
		Opt4, MCS6		14.1		dBm
Error Vector Magnitude over	EVM _{14dBm}	Opt4, MCS2		-30.1	_	dB
process variation with TX setting for POUT _{14dBm} ¹		Opt4, MCS4		-28.0	_	dB
o radin		Opt4, MCS5		-28.6	_	dB
		Opt4, MCS6		-28.7	_	dB
Error Vector Magnitude in to 2:1 VSWR Load over proc-	EVM _{VSWR2_14}	Opt4, MCS2, 2:1 VSWR, T _A = 25 °C	_	-26.3	_	dB
ess variation, measured at worst case mis-match phase angle, with TX setting for		Opt4, MCS4, 2:1 VSWR, T _A = 25 °C	_	-24.9	_	dB
POUT _{14dBm} ¹		Opt4, MCS5, 2:1 VSWR, T _A = 25 °C	_	-25.1	_	dB
		Opt4, MCS6, 2:1 VSWR, T _A = 25 °C		-25.0		dB
Minimum active TX Power ¹	POUT _{MIN}	Opt4, MCS2		-27.1	_	dBm
		Opt4, MCS4		-27.1	_	dBm
		Opt4, MCS5		-27.0	_	dBm
		Opt4, MCS6	_	-27.0	_	dBm
Max Step Size for TX Power setting for POUT between 0 dBm to +12 dBm	POUT _{STEP}	VREGVDD = AVDD = PAVDD = 3.6 V, T = 25 °C	—	0.1	_	dB
Output power variation vs	PVAR _{V_14}	Opt4, MCS2		0.1	_	dB
PAVDD supply voltage from 3.45 V to 3.8 V, with TX set-		Opt4, MCS4		0.1	_	dB
ting for POUT _{14dBm}		Opt4, MCS5		0.1	_	dB
		Opt4, MCS6		0.1		dB
Peak to peak output power	PVAR _{T85_14}	Opt4, MCS2		1.04		dB
variation vs ambient Temper- ature -40 °C to +85 °C with		Opt4, MCS4		0.96		dB
TX setting for POUT _{14dBm}		Opt4, MCS5		1.07		dB
		Opt4, MCS6	_	1.10	_	dB

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Peak to peak output power	PVAR _{T105_14}	Opt4, MCS2	_	0.23		dB
variation vs ambient Temper- ature +85 °C to +105 °C with		Opt4, MCS4	—	0.23	_	dB
TX setting for POUT _{14dBm}		Opt4, MCS5	_	0.23	_	dB
		Opt4, MCS6	_	0.20	_	dB
Output power variation vs	PVAR _{F_14}	Opt4, MCS2	_	0.18	_	dB
frequency with TX setting for POUT _{14dBm} .Frequency test		Opt4, MCS4	_	0.16	_	dB
is at MIN, TYP, and MAX of F _{RANGE}		Opt4, MCS5	—	0.14	_	dB
' RANGE		Opt4, MCS6	_	0.17	_	dB
Spurious emissions at spur	SPUR _{ETSI_54}	Opt4, MCS2	_	-59.9	-54	dBm
frequencies inside the bands in which the -54 dBm max		Opt4, MCS4	_	-60.4	-54	dBm
limit applies, while the on channel desired signal is at		Opt4, MCS5	—	-60.9	-54	dBm
POUT = +14 dBm tested at the highest and lowest oper- ating channel frequency, conducted measurement with 100 kHz RBW ^{2 3 4}		Opt4, MCS6	_	-59.6	-54	dBm
Spurious emissions at spur	SPUR _{ETSI_36}	Opt4, MCS2	_	-44.3	-36	dBm
frequencies below 1 GHz where the -36 dBm max limit		Opt4, MCS4	_	-44.2	-36	dBm
applies, while on channel de- sired signal is at POUT =		Opt4, MCS5	_	-44.8	-36	dBm
+14 dBm tested at the high- est and lowest operating channel frequency, conduc- ted measurement with 100 kHz RBW ^{2 3 5}		Opt4, MCS6	_	-45.6	-36	dBm
Spurious emissions at spur	SPUR _{ETSI_1G6}	Opt4, MCS2	_	-54.0	-30	dBm
frequency above 1 GHz (in- cluding harmonics), and be-		Opt4, MCS4	—	-55.4	-30	dBm
low 6 GHz, while on channel desired signal is at POUT =		Opt4, MCS5	_	-51.4	-30	dBm
+14 dBm for highest and lowest operating channel fre- quency, conducted measure- ment with 1 MHz RBW ^{2 3}		Opt4, MCS6	_	-54.0	-30	dBm
Adjacent Channel Power Ra-	ACPRWISUN	Opt4, MCS2	20	26.0	_	dBc
tio while on channel desired signal is at POUT = +14 dBm		Opt4, MCS4	20	26.2		dBc
per Wi-SUN Alliance ^{3 6}		Opt4, MCS5	20	26.1	_	dBc
		Opt4, MCS6	20	26.5	—	dBc
Alternate Adjacent Channel	A2CPR _{WISUN}	Opt4, MCS2	40	47.1		dBc
Power Ratio while on chan- nel desired signal is at POUT		Opt4, MCS4	40	47.0	_	dBc
= +14 dBm per Wi-SUN Alli- ance ^{3 6}		Opt4, MCS5	40	47.0	—	dBc
		Opt4, MCS6	40	47.0	_	dBc

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Note:						
	e to ETSI EN 300 220-1 v3 2020 Section 20 except for	3.1.1, Wi-SUN Alliance PHY Working G r max power limit	Group Technic	cal Specificati	on Revision 1	VA9, and
2. Per ETSI EN 30	0 220-1 v3.1.1 section 5.9	0.2 and 5.9.3, Table 19				
3. Emissions are n	neasured at T _A = 25 °C					
4. Spurious emissi MHz; and 470 to	•	frequency bands are limited to -54 dBr	m: 47 to 74 M	IHz; 87.5 to 1	18 MHz; 174	to 230
· ·	ons which are below 1 GF o 790 MHz) are limited to -	Iz and outside of the four frequency ba 36 dBm	ands (47 to 74	4 MHz; 87.5 to	o 118 MHz; 17	74 to 230
	onditions are Typical / Non /A9 section 8.2.7.	ninal only in accordance to Wi-SUN All	liance PHY W	/orking Group	Technical Sp	pecifica-

4.9.2.4 490 MHz Band RF SUN OFDM Transmitter Characteristics

This table is for devices with an output power rating of +16 dBm using the 470 MHz Band matching network as shown in the typical connections section. $POUT_{16dBm}$ is marking the nominal TX setting which is targeting POUT = +16 dBm at typical conditions.

Table 4.21. 490 MHz Band RF SUN OFDM Transmitter Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		470	490	510	MHz
Active TX Power for +16 dBm TX output power setting	POUT _{16dBm}	Opt4, MCS2	_	16.0	_	dBm
		Opt4, MCS4	_	16.0	_	dBm
		Opt4, MCS5	_	16.1		dBm
		Opt4, MCS6	_	16.0		dBm
Error Vector Magnitude over	EVM _{16dBm}	Opt4, MCS2	_	-30.2		dB
process variation with TX setting for POUT _{16dBm}		Opt4, MCS4		-27.4		dB
-		Opt4, MCS5		-27.7		dB
		Opt4, MCS6		-27.8		dB
Error Vector Magnitude in to 2:1 VSWR Load over proc-	EVM _{VSWR2_16}	Opt4, MCS2, 2:1 VSWR, T _A = 25 °C	_	-24.5	_	dB
ess variation measured at worst case mis-match phase angle, with TX setting for		Opt4, MCS4, 2:1 VSWR, T _A = 25 °C	_	-23.3	_	dB
POUT _{16dBm}		Opt4, MCS5, 2:1 VSWR, T _A = 25 °C	—	-23.4	_	dB
		Opt4, MCS6, 2:1 VSWR, T _A = 25 °C	_	-23.1		dB
Minimum active TX Power	POUT _{MIN}	Opt4, MCS2	_	-28.0		dBm
		Opt4, MCS4		-27.9		dBm
		Opt4, MCS5	_	-27.8		dBm
		Opt4, MCS6		-27.7		dBm
Output power variation vs	PVAR _{V_16}	Opt4, MCS2	_	0.1		dB
PAVDD supply voltage from 3.45 V to 3.8 V, with TX set-		Opt4, MCS4	—	0.1	_	dB
ting for POUT _{16dBm}		Opt4, MCS5	_	0.1		dB
		Opt4, MCS6	_	0.1		dB
Peak to peak output power	PVAR _{T85_16}	Opt4, MCS2	_	0.49		dB
variation vs ambient Temper- ature -40 °C to +85 °C, with		Opt4, MCS4		0.57		dB
TX setting for $POUT_{16dBm}$		Opt4, MCS5	_	0.55		dB
		Opt4, MCS6	_	0.49	_	dB
Peak to peak output power	PVAR _{T105_16}	Opt4, MCS2	—	0.1	_	dB
variation vs ambient Temper- ature +85 °C to +105 °C,		Opt4, MCS4	_	0.1		dB
with TX setting for POUT _{16dBm}		Opt4, MCS5	_	0.1		dB
iodom.		Opt4, MCS6		0.1		dB

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Output power variation vs	PVAR _{F_16}	Opt4, MCS2	_	1.2	_	dB
frequency with TX setting for POUT _{16dBm} . Frequency test		Opt4, MCS4	_	1.2		dB
is at MIN, TYP, and MAX of		Opt4, MCS5	_	1.2	_	dB
F _{RANGE}		Opt4, MCS6	_	1.2	_	dB
Harmonic emissions per Chi-	SPUR _{HARM1_CN}	Opt4, MCS2	_	-62.1	_	dBm
na SRW Requirement, Sec- tion 2.1 (frequencies below		Opt4, MCS4	_	-62.8	_	dBm
1GHz). P _{OUT} = +16 dBm, 490 MHz ¹		Opt4, MCS5	_	-62.3	_	dBm
490 MHZ ⁺		Opt4, MCS6	_	-62.9		dBm
Harmonic emissions per Chi-	SPUR _{HARM2_CN}	Opt4, MCS2	_	-62.6		dBm
na SRW Requirement, Sec- tion 2.1 (frequencies above		Opt4, MCS4	_	-62.6	_	dBm
1GHz). P _{OUT} = +16 dBm, 490 MHz ¹		Opt4, MCS5	_	-62.4		dBm
490 MHZ		Opt4, MCS6	_	-62.5	_	dBm
Spurious emissions per Chi-	SPUR _{OOB1_CN}	Opt4, MCS2	_	-57.6	_	dBm
na SRW Requirement, Sec- tion 3 (48.5-72.5MHz,		Opt4, MCS4	_	-57.7		dBm
76-108MHz, 167-223MHz, and 606-798MHz). P _{OUT} =		Opt4, MCS5	_	-57.6	_	dBm
+16 dBm, 490 MHz ¹		Opt4, MCS6	_	-57.9	_	dBm
Spurious emissions per Chi-	SPUR _{OOB2_CN}	Opt4, MCS2	_	-53.4		dBm
na SRW Requirement, Sec- tion 2.1 (other frequencies		Opt4, MCS4	_	-52.5		dBm
below 1GHz). P _{OUT} = +16 dBm, 490 MHz ¹		Opt4, MCS5	_	-53.7		dBm
		Opt4, MCS6	_	-53.1		dBm
Spurious emissions per Chi-	SPUR _{OOB3_CN}	Opt4, MCS2	_	-63.0		dBm
na SRW Requirement, Sec- tion 2.1 (frequencies above		Opt4, MCS4	_	-63.0		dBm
1GHz). P _{OUT} = +16 dBm, 490 MHz ¹		Opt4, MCS5	_	-62.8		dBm
490 MHZ		Opt4, MCS6	_	-63.1	_	dBm
Adjacent Channel Power Ra-	ACPRWISUN	Opt4, MCS2	_	24.2		dBc
tio while on channel desired signal is at POUT = +16 dBm		Opt4, MCS4	_	24.0	_	dBc
per Wi-SUN Alliance ¹²		Opt4, MCS5	_	24.2	_	dBc
		Opt4, MCS6	_	24.3	_	dBc
Alternate Adjacent Channel	A2CPR _{WISUN}	Opt4, MCS2	_	47.6	_	dBc
Power Ratio while on chan- nel desired signal is at POUT		Opt4, MCS4	_	47.7	_	dBc
= +16 dBm per Wi-SUN Alli- ance ^{1 2}		Opt4, MCS5	_	47.7	_	dBc
		Opt4, MCS6	_	47.8		dBc

1. Emissions are tested at T_A = 25 °C.

2. All Operating Conditions are Typical / Nominal only in accordance to Wi-SUN Alliance PHY Working Group Technical Specification Revision 1VA9 section 8.2.7.

4.9.3 RF Proprietary Receiver Characteristics

4.9.3.1 920 MHz Band RF Receiver Characteristics

Band is 922.3 to 928.1 MHz. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, external PA Supply, supply filtering as shown in the typical connections section, crystal frequency = 39.0 MHz ± 1 ppm, and RF center frequency 924.0 MHz.

Table 4.22. 920 MHz Band RF Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
RF test frequency range	F _{RANGE}		922.3	924	928.1	MHz
Rx Max Strong Signal Input Level for PER 10%	RX _{SAT}	Desired is reference 400 kbps 4FSK signal ¹	_	-	10	dBm
Sensitivity	SENS	Desired is reference 50 kbps 2FSK signal, $\Delta f = \pm 25$ kHz, PER<10% ^{2 3}	_	-109.9	-108.6	dBm
		Desired is reference 50 kbps 2FSK signal, $\Delta f = \pm 25$ kHz, PER<10% ²	_	-109.9	-106.4	dBm
		Desired is reference 100 kbps 2FSK signal, $\Delta f = \pm 50$ kHz, PER<10% ^{4 3}	_	-107.0	-105.9	dBm
		Desired is reference 100 kbps 2FSK signal, $\Delta f = \pm 50$ kHz, PER<10% ⁴	_	-107.0	-103.2	dBm
		Desired is reference 400 kbps 4FSK signal, $\Delta f_o = \pm 100$ kHz, Δf_i = ± 33.3 kHz, PER<10% ¹	_	-99.1	_	dBm
Adjacent channel rejection, Interferer is CW at ± 1 × channel spacing	ACR1	Desired is reference 50 kbps 2FSK signal ² at 3dB above sensi- tivity level	_	45.4	_	dB
		Desired is reference 100 kbps 2FSK signal ⁴ at 3dB above sensi- tivity level	_	46.9	_	dB
		Desired is reference 400 kbps 4FSK signal ¹ at 3dB above sensi- tivity level	_	42.1	_	dB
Alternate channel rejection, Interferer is CW at ± 2 × channel spacing	ACR2	Desired is reference 50 kbps 2FSK signal ² at 3dB above sensi- tivity level	_	50.8	_	dB
		Desired is reference 100 kbps 2FSK signal ⁴ at 3dB above sensi- tivity level	_	55.4	_	dB
		Desired is reference 400 kbps 4FSK signal ¹ at 3dB above sensi- tivity level	_	47.1	_	dB
Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
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Image rejection, Interferer is CW at image frequency	IR	Desired is reference 50 kbps 2FSK signal ² at 3dB above sensi- tivity level	_	46.6	_	dB
		Desired is reference 100 kbps 2FSK signal ⁴ at 3dB above sensi- tivity level	_	47.2	_	dB
		Desired is reference 400 kbps 4FSK signal ¹ at 3dB above sensi- tivity level	_	42.1	_	
Blocking selectivity, 10%	BLOCK	Interferer CW at Desired ± 1 MHz	_	55.2	—	dB
PER. Desired is 100 kbps 2FSK signal at 3dB above		Interferer CW at Desired ± 2 MHz	_	62.9	_	dB
sensitivity level		Interferer CW at Desired ± 10 MHz	_	78.6		dB
Intermod selectivity,10% PER. CW interferers at 400 kHz and 800 kHz offsets	IM	Desired is reference 100 kbps 2FSK signal ⁴ at 3dB above sensi- tivity level	_	43.7		dB
Upper limit of input power range over which RSSI _{RES} and RSSI _{ABSERR} are main- tained	RSSI _{MAX}				-30	dBm
Lower limit of input power range over which RSSI _{RES} and RSSI _{ABSERR} are main- tained	RSSI _{MIN}		-100	_	_	dBm
RSSI resolution	RSSI _{RES}	Over RSSI _{MIN} to RSSI _{MAX} range	_	0.25	_	dB
RSSI maximum absolute er- ror over typical conditions with offset correction	RSSI _{ABSERR}	Over RSSI _{MIN} to RSSI _{MAX} range	_	1.6	_	dB
Max spurious emissions dur-	SPUR _{RX_ARIB}	Below 710 MHz, RBW=100kHz	_	-84.5	-54	dBm
ing active receive mode, per ARIB STD-T108 Part 2, Sec-		710-900 MHz, RBW=1MHz	—	-92.1	-55	dBm
tion 3.3		900-915 MHz, RBW=100kHz	_	-102.6	-55	dBm
		915-930 MHz, RBW=100kHz	_	-104.3	-54	dBm
		930-1000 MHz, RBW=100kHz	_	-100.5	-55	dBm
		Above 1000 MHz, RBW=1MHz		-78.6	-47	dBm

- 1. Definition of reference signal is 400 kbps 4FSK, BT = 2, mi = 0.33, PER<10%, Channel Spacing = 600 kHz, Data Whitening, no FEC, Per IEEE 802.15.4g 920 MHz band, mode 4.
- 2. Definition of reference signal is 50 kbps 2FSK, BT = 2, mi = 1.0, PER<10%, Channel Spacing = 200 kHz, Data Whitening, no FEC.
- 3. Min/Max numbers are measured at typical voltage, at typical F_{RANGE} frequency, and at T_A = 25 °C.
- 4. Definition of reference signal is 100 kbps 2FSK, BT = 2, mi = 1.0, PER<10%, Channel Spacing = 400 kHz, Data Whitening, no FEC.

4.9.3.2 915 MHz Band RF Receiver Characteristics

Band is 902 to 928 MHz. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, crystal frequency = 39.0 MHz ± 1 ppm, supply filtering as shown in the typical connections section, and RF center frequency 915 MHz.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		902	_	928	MHz
Rx Max Strong Signal Input Level for 0.1% BER	RX _{SAT}	Desired is reference 2 Mbps 2GFSK signal ¹	_	-	10	dBm
Sensitivity	SENS	Desired is reference 10 kbps 2GFSK signal, $\Delta f = \pm 5$ kHz, PER<1% ²	_	-117.0	_	dBm
		Desired is reference 50 kbps 2FSK signal, $\Delta f = \pm 25$ kHz, PER<10% ³	_	-109.9	—	dBm
		Desired is reference 50 kbps 2FSK signal, $\Delta f = \pm 25$ kHz, PER<10% with FEC ⁴	_	-114.6	—	dBm
		Desired is reference 150 kbps 2FSK signal, $\Delta f = \pm 37.5$ kHz, PER<10% ⁵	_	-106.8	—	dBm
		Desired is reference 2 Mbps 2GFSK signal, $\Delta f = \pm 500 \text{ kHz}$, BER<0.1% ¹	_	-96.9	—	dBm
		Desired is reference 4.8 kbps O- QPSK signal, spreading factor=8, PER<1% ⁶	_	-125.8	—	dBm
		Desired is reference 250 kbps O- QPSK DSSS signal, PER<1% ⁷	_	-103.3	_	dBm
Adjacent channel rejection, Interferer is CW at ± 1 × channel spacing	ACR1	Desired is reference 50 kbps 2FSK signal ³ at 3dB above sensi- tivity level	_	45.2	—	dB
		Desired is reference 150 kbps 2FSK signal ⁵ at 3dB above sensi- tivity level	_	45.5	—	dB
		Desired is reference 250 kbps O- QPSK DSSS signal ⁷ at 3dB above sensitivity level	_	41.5	—	dB
Alternate channel rejection, Interferer is CW at ± 2 × channel spacing	ACR2	Desired is reference 50 kbps 2FSK signal ³ at 3dB above sensi- tivity level	_	50.8	_	dB
		Desired is reference 150 kbps 2FSK signal ⁵ at 3dB above sensi- tivity level		56.1	_	dB
		Desired is reference 250 kbps O- QPSK DSSS signal ⁷ at 3dB above sensitivity level	_	45.5	_	dB

Table 4.23. 915 MHz Band RF Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Image rejection, Interferer is CW at image frequency	IR	Desired is reference 50 kbps 2FSK signal ³ at 3dB above sensi- tivity level		45.2	_	dB
		Desired is reference 150 kbps 2FSK signal ⁵ at 3dB above sensi- tivity level	_	45.5	_	dB
		Desired is reference 250 kbps O- QPSK DSSS signal ⁷ at 3dB above sensitivity level		43.3	_	dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal at 3 dB above required sen- sitivity. Undesired signal is CW at ± 1 MHz frequency offset.	BLOCK _{1M}	50 kbps 2FSK ³		63.5		dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal at 3 dB above required sen- sitivity. Undesired signal is CW at ± 2 MHz frequency offset.	BLOCK _{2M}	50 kbps 2FSK ³		71.4		dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal at 3 dB above required sen- sitivity. Undesired signal is CW at ± 10 MHz frequency offset.	BLOCK _{10M}	50 kbps 2FSK ³	_	82.0	_	dB
Intermod selectivity, PER < 10%. CW interferers at 400 kHz and 800 kHz offsets	IM	Desired is reference 50 kbps 2GFSK signal ³ at 3dB above sen- sitivity level	_	45.8	_	dB
Upper limit of input power range over which RSSI _{RES} and RSSI _{ABSERR} are main- tained	RSSI _{MAX}		_	_	-30	dBm
Lower limit of input power range over which RSSI _{RES} and RSSI _{ABSERR} are main- tained	RSSI _{MIN}		-100	_	_	dBm
RSSI resolution	RSSI _{RES}	Over RSSI _{MIN} to RSSI _{MAX} range		0.25	_	dB
RSSI maximum absolute er- ror over typical conditions with offset correction	RSSI _{ABSERR}	Over RSSI _{MIN} to RSSI _{MAX} range	_	1.2	_	dB
Max spurious emissions dur- ing active receive mode, per	SPUR _{RX_FCC}	216-960 MHz	—	-84.7	-49.2	dBm
FCC Part 15.109(a)		Above 960 MHz		-76.5	-41.2	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Note:						
1. Crystal tolerance	= 0 ppm.					
2. Definition of reference octets.	rence signal is 10 kbps	2GFSK, BT = 2, mi = 1.0, PER<1%, RX	channel BW	= 40 kHz, pa	yload length =	: 20
3. Definition of refer FEC.	rence signal is 50 kbps	2FSK, BT = 2, mi = 1.0, PER<10%, Cha	annel Spacing) = 200 kHz, [Data Whitenin	g, no
4. Definition of refer FEC.	rence signal is 50 kbps	2FSK, BT = 2, mi = 1.0, PER<10%, Cha	annel Spacing) = 200 kHz, [Data Whitenin	g, with
5. Definition of refer FEC.	rence signal is 150 kbps	s 2FSK, BT = 2, mi = 0.5, PER<10%, Cl	hannel Spacin	ig = 400 kHz,	Data Whiteni	ng, no
6. Definition of reference Crystal tolerance		O-QPSK DSSS long-range PHY, 38.4	kcps chip rate	, chipping co	de length 32,	PER<1%
	•	DSSS, Data rate = 250 kbps, 32-chip F . Crystal tolerance = 0 ppm.	PN sequence	mapping, <1%	% PER, Chan	nel Spac-

4.9.3.3 868 MHz Band RF Receiver Characteristics

Band is 868 to 870 MHz. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, crystal frequency = 39.0 MHz ± 1 ppm, supply filtering as shown in the typical connections section, and RF center frequency 868.3 MHz.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		863	—	870	MHz
Rx Max Strong Signal Input Level for 0.1% BER	RX _{SAT}	Desired is reference 500 kbps 2GMSK signal ¹	_	_	10	dBm
Sensitivity	SENS	Desired is reference 10 kbps 2GFSK signal, Δf = ± 5 kHz, PER<10% ²	—	-119.3	—	dBm
		Desired is reference 38.4 kbps 2GFSK signal, $\Delta f = \pm$ 20 kHz, BER<0.1% ³	—	-113.2	—	dBm
		Desired is reference 50 kbps 2FSK signal, $\Delta f = \pm 12.5$ kHz, PER<10% ⁴	—	-110.8	—	dBm
		Desired is reference 100 kbps 2FSK signal, $\Delta f = \pm 25$ kHz, PER<10% ⁵	—	-108.0	—	dBm
		Desired is reference 500 kbps 2GMSK signal, $\Delta f = \pm 125 \text{ kHz}^1$, BER<0.1% ⁶	—	-103.0	—	dBm
		Desired is reference 100 kbps O- QPSK DSSS signal, PER<1% ⁷	_	-109.8	_	dBm
Adjacent channel rejection, Interferer is CW at ± 1 × channel spacing	ACR1	Desired is reference 10 kbps 2GFSK signal ² at 3dB above sen- sitivity level	—	53.3	—	dB
		Desired is reference 38.4 kbps 2GFSK signal ³ at 3dB above sen- sitivity level	—	44.8	—	dB
		Desired is reference 50 kbps 2FSK signal ⁴ at 3dB above sensi- tivity level	_	45.7	_	dB
		Desired is reference 100 kbps 2FSK signal ⁵ at 3dB above sensi- tivity level	_	44.8	_	dB
		Desired is reference 100 kbps O- QPSK DSSS signal ⁷ at 3dB above sensitivity level	_	56.3	_	dB

Table 4.24. 868 MHz Band RF Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Alternate channel rejection, Interferer is CW at ± 2 × channel spacing	ACR2	Desired is reference 10 kbps 2GFSK signal ² at 3dB above sen- sitivity level	—	53.7	—	dB
		Desired is reference 38.4 kbps 2GFSK signal ³ at 3dB above sen- sitivity level	_	41.9	_	dB
		Desired is reference 50 kbps 2FSK signal ⁴ at 3dB above sensi- tivity level	—	45.1	_	dB
		Desired is reference 100 kbps 2FSK signal ⁵ at 3dB above sensi- tivity level	_	50.5	_	dB
		Desired is reference 100 kbps O- QPSK DSSS signal ⁷ at 3dB above sensitivity level	_	67.1	_	dB
Image rejection, Interferer is CW at image frequency	IR	Desired is reference 10 kbps 2GFSK signal ² at 3dB above sen- sitivity level	_	44.5	_	dB
		Desired is reference 38.4 kbps 2GFSK signal ³ at 3dB above sen- sitivity level	_	42.0	_	dB
		Desired is reference 50 kbps 2FSK signal ⁴ at 3dB above sensi- tivity level	_	46.8	_	dB
		Desired is reference 100 kbps 2FSK signal ⁵ at 3dB above sensi- tivity level	_	46.2	_	dB
		Desired is reference 100 kbps O- QPSK DSSS signal ⁷ at 3dB above sensitivity level	_	44.1	_	dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal at 3 dB above required sen- sitivity. Undesired signal is CW at ± 1 MHz frequency offset.	BLOCK _{1M}	50 kbps 2FSK signal ⁴	_	64.4	_	dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal at 3 dB above required sen- sitivity. Undesired signal is CW at ± 2 MHz frequency offset.	BLOCK _{2M}	50 kbps 2FSK signal ⁴	_	73.5	_	dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal at 3 dB above required sen- sitivity. Undesired signal is CW at ± 10 MHz frequency offset.	BLOCK _{10M}	50 kbps 2FSK signal ⁴	_	84.1		dB
Upper limit of input power range over which RSSI _{RES} and RSSI _{ABSERR} are main- tained	RSSI _{MAX}		_	_	-40	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Lower limit of input power range over which RSSI _{RES} and RSSI _{ABSERR} are main- tained	RSSI _{MIN}		-100	_	_	dBm
RSSI resolution	RSSI _{RES}	Over RSSI _{MIN} to RSSI _{MAX} range	—	0.25	—	dB
RSSI maximum absolute er- ror over typical conditions with offset correction	RSSI _{ABSERR}	Over RSSI _{MIN} to RSSI _{MAX} range	_	1.8	_	dB
Max spurious emissions dur-	SPUR _{RX}	30 MHz to 1 GHz	—	-84.8	-57	dBm
ing active receive mode		1 GHz to 12 GHz	_	-76.1	-47	dBm

- 1. Definition of reference signal is 500 kbps 2GMSK, BT = 0.5, mi = 0.5, BER<0.1%, RX channel BW = 753.320 kHz. Crystal tolerance = 0 ppm.
- 2. Definition of reference signal is 10 kbps 2GFSK, BT = 0.5, mi = 1.0, PER<10%, Data Whitening, no FEC. Crystal tolerance = 0 ppm. Per IEEE 802.15.4x.
- 3. Definition of reference signal is 38.4 kbps 2GFSK, BT = 0.5, mi = 1.04, BER<0.1%, RX channel BW = 74.809 kHz, channel spacing = 100 kHz. Crystal tolerance = 0 ppm.
- 4. Definition of reference signal is 50 kbps 2FSK, BT = 2, mi = 0.5, PER<10%, Channel Spacing = 100 kHz, Data Whitening, no FEC.
- 5. Definition of reference signal is 100 kbps 2FSK, BT = 2, mi = 0.5, PER<10%, Channel Spacing = 200 kHz, Data Whitening, no FEC.
- 6. The modulation bandwidth may not be suitable for regional regulatory requirements in this band. Crystal tolerance = 0 ppm.
- 7. Definition of reference signal is O-QPSK DSSS per IEEE 802.15.4 section 12.2 and Table 12-2, Data rate = 100 kbps, 4 bit to 16 chip PN sequence mapping, <1% PER, Channel Spacing = 2 MHz, payload length=20 octets.

4.9.3.4 470 MHz Band RF Receiver Characteristics

Band is 470 to 510 MHz. Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, supply filtering as shown in the typical connections section, crystal frequency = 39.0 MHz ± 1 ppm, and RF center frequency 490 MHz.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		470	_	510	MHz
Rx Max Strong Signal Input Level for 10% PER	RX _{SAT}	Desired is reference 100 kbps 2FSK signal ¹	_	_	10	dBm
Sensitivity	SENS	Desired is reference 10 kbps 2GFSK signal, $\Delta f = \pm 25$ kHz, BER<0.1% ²	_	-117.7	_	dBm
		Desired is reference 50 kbps 2FSK signal, $\Delta f = \pm 25$ kHz, PER<10% ³	_	-111.1	—	dBm
		Desired is reference 100 kbps 2FSK signal, $\Delta f = \pm 25$ kHz, PER<10% ¹	_	-110.1	—	dBm
Adjacent channel rejection, Interferer is CW at ± 1 × channel spacing	ACR1	Desired is reference 10 kbps 2GFSK signal ² at 3dB above sen- sitivity level	_	52.2	_	dB
		Desired is reference 50 kbps 2FSK signal ³ at 3dB above sensi- tivity level	_	48.7	_	dB
		Desired is reference 100 kbps 2FSK signal ¹ at 3dB above sensi- tivity level	_	46.4	_	dB
Alternate channel rejection, Interferer is CW at ± 2 × channel spacing	ACR2	Desired is reference 10 kbps 2GFSK signal ² at 3dB above sen- sitivity level	—	40.7	-	dB
		Desired is reference 50 kbps 2FSK signal ³ at 3dB above sensi- tivity level	_	53.9	—	dB
		Desired is reference 100 kbps 2FSK signal ¹ at 3dB above sensi- tivity level	_	55.3	_	dB
Image rejection, Interferer is CW at image frequency	IR	Desired is reference 10 kbps 2GFSK signal ² at 3dB above sen- sitivity level	—	40.5	_	dB
	2F tiv Du 2F	Desired is reference 50 kbps 2FSK signal ³ at 3dB above sensi- tivity level	_	49.1	—	dB
		Desired is reference 100 kbps 2FSK signal ¹ at 3dB above sensi- tivity level	_	48.0	_	dB

Table 4.25. 470 MHz Band RF Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Blocking selectivity, 0.1%	BLOCK ₁₀	Interferer CW at Desired ± 1 MHz	_	72.4	_	dB
BER. Desired is reference 10 kbps 2GFSK signal ² at 3dB		Interferer CW at Desired ± 2 MHz	_	80.1	_	dB
above sensitivity level		Interferer CW at Desired ± 10 MHz	—	86.0	_	dB
Upper limit of input power range over which RSSI _{RES} and RSSI _{ABSERR} are main- tained	RSSI _{MAX}		—	_	-30	dBm
Lower limit of input power range over which RSSI _{RES} and RSSI _{ABSERR} are main- tained	RSSI _{MIN}		-100	_	_	dBm
RSSI resolution	RSSI _{RES}	Over RSSI _{MIN} to RSSI _{MAX} range	_	0.25	_	dB
RSSI maximum absolute er- ror over typical conditions with offset correction	RSSI _{ABSERR}	Over RSSI _{MIN} to RSSI _{MAX} range		2.3	_	dB
Max spurious emissions dur-	SPUR _{RX}	30 MHz to 1 GHz	—	-81.0	-57	dBm
ing active receive mode		1 GHz to 12 GHz	_	-71.8	-47	dBm

1. Definition of reference signal is 100 kbps 2FSK, BT = 2, mi = 0.5, PER<10%, Channel Spacing = 200 kHz.

2. Definition of reference signal is 10 kbps 2GFSK, BT = 0.5, mi = 5.0, BER<0.1%, RX channel BW = 99.2 kHz. Crystal tolerance = 0 ppm.

3. Definition of reference signal is 50 kbps 2FSK, BT = 2, mi = 1.0, PER<10%, Channel Spacing = 200 kHz.

4.9.4 RF SUN O-QPSK Receiver Characteristics

SUN O-QPSK DSSS Modulations are defined by IEEE 802.15.4-2020 section 21, and Table 21-4 using the following abbreviations: Rc = baud or Chip rate (kchip/s), RM = Rate mode (index), Rd = bit data rate (kbps), and PL = PSDU Length (octets). Measurements use packet length of 250 octets when data rate is 50 kbps or higher, and 20 octets packet length when lower then 50 kbps.

4.9.4.1 914 MHz Band RF SUN O-QPSK Receiver Characteristics

Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, external PA Supply, supply filtering as shown in the typical connections section.

Table 4.26. 914 MHz Band RF SUN O-QPSK Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		902	914	928	MHz
Rx Sensitivity for 10% Pack-	SENS	Rc = 100, RM = 0, Rd = 6.25		-123.9		dBm
et Error Rate (PER) with no interferer for SUN O-QPSK		Rc = 100, RM = 1, Rd = 12.5		-121.1		dBm
modulations		Rc = 100, RM = 2, Rd = 25		-120.2		dBm
		Rc = 100, RM = 3, Rd = 50		-118.8		dBm
		Rc = 1000, RM = 0, Rd = 31.25		-116.0		dBm
		Rc = 1000, RM = 1, Rd = 125		-113.1		dBm
		Rc = 1000, RM = 2, Rd = 250		-110.6		dBm
		Rc = 1000, RM = 3, Rd = 500		-109.0		dBm
Rx Max Strong Signal Input	RX _{SAT}	Rc = 100, RM = 0, Rd = 6.25		10		dBm
Level for 10% PER		Rc = 1000, RM = 3, Rd = 500	_	10		dBm
Adjacent Channel Rejection is the U/D ratio in dB (a.k.a. ISR) for 10% PER according	ACR1	Rc = 100, RM = 0, Rd = 6.25	_	61.5		dB
		Rc = 100, RM = 1, Rd = 12.5		58.3		dB
to IEEE 802.15.4-2020 sec- tion 21.5.4 for the lower ∆f		Rc = 100, RM = 2, Rd = 25		57.6		dB
in table 21-23, with Desired		Rc = 100, RM = 3, Rd = 50		56.4		dB
signal at 3 dB above re- quired sensitivity in Table		Rc = 1000, RM = 0, Rd = 31.25		55.3		dB
21-21. ¹		Rc = 1000, RM = 1, Rd = 125	_	52.1		dB
		Rc = 1000, RM = 2, Rd = 250		49.7		dB
		Rc = 1000, RM = 3, Rd = 500	_	48.0		dB
Alternate Adjacent Channel	ACR2	Rc = 100, RM = 0, Rd = 6.25	_	71.1		dB
Rejection (ISR) is the U/D ra- tio in dB for 10% PER ac-		Rc = 100, RM = 1, Rd = 12.5	_	68.0		dB
cording to IEEE 802.15.4-2020 section 21.5.4		Rc = 100, RM = 2, Rd = 25	_	67.3		dB
for the higher $ \Delta f $ in table		Rc = 100, RM = 3, Rd = 50		65.5		dB
21-23, with Desired signal at 3 dB above required sensitiv-		Rc = 1000, RM = 0, Rd = 31.25	—	58.9		dB
ity in Table 21-21. ¹		Rc = 1000, RM = 1, Rd = 125	_	55.8		dB
		Rc = 1000, RM = 2, Rd = 250	—	53.3		dB
		Rc = 1000, RM = 3, Rd = 500	—	51.6	_	dB

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Co-Channel Rejection U/D	CoChR	Rc = 100, RM = 0, Rd = 6.25		3.6		dB
ratio. Set Desired signal to 3 dB above required sensitivity		Rc = 100, RM = 1, Rd = 12.5	_	1.8		dB
level according to IEEE 805.15.4-2020 section		Rc = 100, RM = 2, Rd = 25	_	0.2	_	dB
21.5.3, Table 21-21. Unde-		Rc = 100, RM = 3, Rd = 50		-0.5		dB
sired signal level shall be adjusted to make PER = 10%. ¹		Rc = 1000, RM = 0, Rd = 31.25	_	5.7		dB
		Rc = 1000, RM = 1, Rd = 125		2.1		dB
		Rc = 1000, RM = 2, Rd = 250	_	-0.6	_	dB
		Rc = 1000, RM = 3, Rd = 500	_	-4.3	_	dB
Error for Rx Energy Detec-	AGC _{Pre}	Rc = 100, RM = 0, Rd = 6.25	_	0.7	_	dB
tion, and AGC. Input signal comprising all zero bits ac-		Rc = 100, RM = 3, Rd = 50	_	0.6	_	dB
cording to IEEE 802.15.4-2020 section		Rc = 1000, RM = 0, Rd = 31.25	_	0.5	_	dB
802.15.4-2020 section 21.2.2.2, as a continuous Preamble. Report the signal level delta: Rx measured sig- nal level averaged over two Preambles of 56 bits minus the applied signal level. ²		Rc = 1000, RM = 3, Rd = 500	_	0.5	_	dB
Frequency Error Sensitivity.	SENS _{FE}	Rc = 100, RM = 0, Rd = 6.25	_	-121.0	_	dBm
Receiver signal level for 10% PER with the desired signal's		Rc = 100, RM = 1, Rd = 12.5	—	-117.1	_	dBm
frequency offset by ± 50 ppm.		Rc = 100, RM = 2, Rd = 25	_	-119.9	_	dBm
		Rc = 100, RM = 3, Rd = 50	_	-118.3	_	dBm
		Rc = 1000, RM = 0, Rd = 31.25	_	-116.1	_	dBm
		Rc = 1000, RM = 1, Rd = 125	_	-113.1	_	dBm
		Rc = 1000, RM = 2, Rd = 250	_	-110.6	—	dBm
		Rc = 1000, RM = 3, Rd = 500	_	-108.8	_	dBm
Signal Quality Estimate in- dex [0-255] for SUN O-	SQE	at SENS Rc = 100, RM = 2, Rd = 25	—	42		index
QPSK modulation with the given input signal condition as measured by the receiver		3 dB above SENS Rc = 100, RM = 2, Rd = 25	_	63	_	index
with AGC active.		10 dB above SENS Rc = 100, RM = 2, Rd = 25	—	119	_	index
		at -97 dBm Rc = 100, RM = 2, Rd = 25		217	_	index
		at -97 dBm and ACR1 Rc = 100, RM = 2, Rd = 25	_	40	_	index
		at -40 dBm no interferer Rc = 100, RM = 2, Rd = 25	—	255	_	index
		at -40 dBm with a co-channel in- terferer level adjusted for 10% PER ¹ Rc = 100, RM = 2, Rd = 25		163	_	index
		at SENS _{FE} with 50 ppm Delta Rc = 100, RM = 2, Rd = 25		40	—	index

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Receive Signal Strength Indi- cator in dB for SUN O-QPSK	RSSI	at SENS Rc = 100, RM = 2, Rd = 25	_	-117.4	_	dBm
modulation with the given in- put signal condition as meas- ured by the receiver with		3 dB above SENS Rc = 100, RM = 2, Rd = 25	_	-115.6	—	dBm
AGC active.		10 dB above SENS Rc = 100, RM = 2, Rd = 25	_	-109.4	—	dBm
		at -97 dBm Rc = 100, RM = 2, Rd = 25	_	-96.7	_	dBm
		at -97 dBm and Undesired at ACR1 Rc = 100, RM = 2, Rd = 25	—	-95.3	—	dBm
		at -40 dBm no interferer Rc = 100, RM = 2, Rd = 25	—	-39.9	—	dBm
		at -40 dBm with a co-channel in- terferer level adjusted for 10% $PER^1 Rc = 100$, RM = 2, Rd = 25	_	-40.2	_	dBm
		at SENS _{FE} with 50 ppm Delta Rc = 100, RM = 2, Rd = 25	_	-117.7	_	dBm

1. The undesired signal shall be a compliant SUN O-QPSK PHY PSDU according to IEEE 802.15.4-2020 section 21.5.4 containing a pseudo random bit sequence which is different from the desired signal. The undesired signal omits the SHR and PHR, uses chip-whitening, and the chip rate and spreading mode are the same as the desired signal.

2. The specification is less than ± 6 dB error at all power levels between 10 dB above required sensitivity to 50 dB above required sensitivity.

4.9.5 RF Wi-SUN FSK Receiver Characteristics

Wi-SUN FSK Modulations are defined in Wi-SUN Alliance PHY Working Group (PHYWG TPS) Wi-SUN PHY Technical Specification -Amendment 1VA9 November 2022. The PHY modulations in this table use BT = 2 and are indicated by (T, M, C) where T is the Phy Mode ID Type, and M is the Mode from PHY WG TPS Tables 2, 3, and 4. Also, C is the Channel Plan ID from PHY WG TPS Tables 6 and 7. The PHYWG TPS also references IEEE 802.15.4-2020 section 19 especially. Measurements use packet length of 250 octets when data rate is 50 kbps or higher, and 20 octets packet length when lower than 50 kbps.

The following table gives information about the different Wi-SUN FSK configurations that are supported by this device family. This section is meant to be informative, in case of any contradiction the Wi-SUN PHY TPS takes precedence.

Table 4.27. FSK Modulation for Wi-SUN, BT = 2, 2 level FSK, with Data Whitening

Old FSK # 1V09 PHY Op Mode ¹	Wi-SUN PHY (Type ² , Mode ³ , ChanPlanID ⁴)	PhyModelD decimal ⁵	Data Rate (kbps)	Operating Band (MHz)	Modulation Index ⁶	Channel Bandwidth ⁷ (kHz)	Channel Spacing (kHz)	FEC Enabled ⁹
#1a	(0, 1, 36)	1	50	866	0.5	65	100	No
#1b	(0, 2, 1)	2	50	914	1	100	200	No
#1b	(0, 2, 21)	2	50	923	1	100	200	No
#2a	(0, 3, 37)	3	100	866	0.5	110	200	No
#2a	(0, 3, 1)	3	100	914	0.5	110	200	No
#2b	(0, 4, 22)	4	100	923	1	200	400	No
#3	(0, 5, 37)	5	150	866	0.5	165	200 ⁸	No
#3	(0, 5, 2)	5	150	914	0.5	165	400	No
#3	(0, 5, 22)	5	150	923	0.5	165	400	No
#4a	(0, 6, 2)	6	200	914	0.5	220	400	No
#4b	(0, 7, 23)	7	200	923	1	400	600	No
#5	(0, 8, 3)	8	300	914	0.5	330	600	No
#5	(0, 8, 23)	8	300	923	0.5	330	600	No
#1a	(1, 1, 36)	17	50	866	0.5	65	100	NRNSC
#1b	(1, 2, 1)	18	50	914	1	100	200	NRNSC
#1b	(1, 2, 21)	18	50	923	1	100	200	NRNSC
#2a	(1, 3, 37)	19	100	866	0.5	110	200	NRNSC
#2a	(1, 3, 1)	19	100	914	0.5	110	200	NRNSC
#2b	(1, 4, 22)	20	100	923	1	200	400	NRNSC
#3	(1, 5, 37)	21	150	866	0.5	165	200 ⁸	NRNSC
#3	(1, 5, 2)	21	150	914	0.5	165	400	NRNSC
#3	(1, 5, 22)	21	150	923	0.5	165	400	NRNSC
#4a	(1, 6, 2)	22	200	914	0.5	220	400	NRNSC
#4b	(1, 7, 23)	23	200	923	1	400	600	NRNSC
#5	(1, 8, 3)	24	300	914	0.5	330	600	NRNSC
#5	(1, 8, 23)	24	300	923	0.5	330	600	NRNSC

Old FSK # 1V09 PHY Op Mode ¹	Wi-SUN PHY (Type ² , Mode ³ , ChanPlanID ⁴)	PhyModelD decimal ⁵	Data Rate (kbps)	Operating Band (MHz)	Modulation Index ⁶	Channel Bandwidth ⁷ (kHz)	Channel Spacing (kHz)	FEC Enabled ⁹	
Note:									
1. Wi-SUN FSK Phy Operating Mode # from PHYWG TPS 1V09 November 2022, Table 2.									
2. Wi-SUN PHY Type follows PHYWG TPS 1VA9, Table 3.									
3. Wi-SUN PH	Y Mode follows PH	IYWG TPS 1V	A9, Table 4.						
4. Wi-SUN FS	K Operating Frequ	ency channel p	lan follows Pl	HYWG TPS 1V	A9, Tables 6 ar	nd 7.			
5. Wi-SUN FS column.	K Phy Mode ID is f	rom Wi-SUN St	andard PHY	WG TPS 1VA9,	Tables 2, 3, ar	nd 4. See also T	able 16 first	and second	
6. Viterbi DeM	od is enabled whe	n modulation in	dex (mi) is les	ss than 1.0, and	disabled wher	n mi is 1.0 or hig	gher.		
7. Approximati	on of the modulation	on signal occup	ied channel b	andwidth for in	formation purp	ose.			
8. Europe Reg	ion uses smaller c	hannel spacing							
9. Modulations	use interleaving o	nly with FEC. A	lso, when FE	C is used it mu	st be NRNSC.				

4.9.5.1 923 MHz Band RF Wi-SUN FSK Receiver Characteristics

Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, external PA Supply, supply filtering as shown in the typical connections section, crystal frequency = 39.0 MHz ± 1 ppm.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range ¹	F _{RANGE}		922.3	923.x	928.1	MHz
Rx Max Strong Signal Input Level for 10% PER.	RX _{SAT}	#5 = (1, 8, 23) ² , 300 kbps, mi = 0.5, with FEC ³	_	10	_	dBm
Rx Sensitivity for 10% Pack- et Error Rate (PER) with no interferer	SENS	#2b = (0, 4, 22) ² , 100 kbps, mi = 1.0, no FEC ⁴	_	-107.0	-103.2	dBm
		#1b = (1, 2, 21) ² , 50 kbps, mi = 1.0, with FEC ⁵	—	-114.5	—	dBm
		#2b = (1, 4, 22) ² , 100 kbps, mi = 1.0, with FEC ⁶	_	-111.1	-107.2	dBm
		#3 = (1, 5, 22) ² , 150 kbps, mi = 0.5, with FEC ⁷	_	-109.4	_	dBm
		#4b = (1, 7, 23) ² , 200 kbps, mi = 1.0, with FEC ⁸	_	-108.0		dBm
		#5 = (1, 8, 23) ² , 300 kbps, mi = 0.5, with FEC ³	_	-106.4	-101.2	dBm
Adjacent Channel Rejection U/D ratio for 10% PER ac- cording to IEEE	ACR1	#2b = (0, 4, 22) ² , 100 kbps, mi = 1.0, no FEC ⁴	_	46.9	_	dB
802.15.4-2020 section 19.6.8 with Desired signal at 3 dB above required sensitivity.		#1b = (1, 2, 21) ² , 50 kbps, mi = 1.0, with FEC ⁵	_	49.9	_	dB
Undesired signal is CW at ± 1 × channel spacing. Re-		#2b = (1, 4, 22) ² , 100 kbps, mi = 1.0, with FEC ⁶	_	49.9	_	dB
quires IR Calibration.		#3 = (1, 5, 22) ² , 150 kbps, mi = 0.5, with FEC ⁷	_	48.6	_	dB
		#4b = (1, 7, 23) ² , 200 kbps, mi = 1.0, with FEC ⁸	_	50.9		dB
		#5 = (1, 8, 23) ² , 300 kbps, mi = 0.5, with FEC ³	_	50.0	_	dB

Table 4.28. 923 MHz Band RF Wi-SUN FSK Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Alternate Channel Rejection U/D ratio for 10% PER ac- cording to IEEE	ACR2	#2b = (0, 4, 22) ² , 100 kbps, mi = 1.0, no FEC ⁴	—	53.2	_	dB
802.15.4-2020 section 19.6.8 with Desired signal at 3 dB above required sensitivity.		#1b = (1, 2, 21) ² , 50 kbps, mi = 1.0, with FEC ⁵	_	53.6		dB
Undesired signal is CW at ± 2 × channel spacing. Re- quires IR Calibration.		#2b = (1, 4, 22) ² , 100 kbps, mi = 1.0, with FEC ⁶	—	58.5	_	dB
		#3 = (1, 5, 22) ² , 150 kbps, mi = 0.5, with FEC ⁷	_	57.1	_	dB
		#4b = (1, 7, 23) ² , 200 kbps, mi = 1.0, with FEC ⁸	_	56.3	_	dB
		#5 = (1, 8, 23) ² , 300 kbps, mi = 0.5, with FEC ³	_	57.8	_	dB
Image Rejection U/D ratio for 10% PER. Undesired signal is CW at the RX image fre-	IR	#2b = (0, 4, 22) ² , 100 kbps, mi = 1.0, no FEC ⁴	—	47.2	—	dB
quency. Desired signal is 3dB above required sensitivi-		#1b = (1, 2, 21) ² , 50 kbps, mi = 1.0, with FEC ⁵	_	51.3	—	dB
ty level according to IEEE 802.15.4-2020 section 19.6.7.		#2b = (1, 4, 22) ² , 100 kbps, mi = 1.0, with FEC ⁶	—	50.1	—	dB
		#3 = (1, 5, 22) ² , 150 kbps, mi = 0.5, with FEC ⁷	—	48.3	—	dB
		#4b = (1, 7, 23) ² , 200 kbps, mi = 1.0, with FEC ⁸	_	51.4	—	dB
		#5 = (1, 8, 23) ² , 300 kbps, mi = 0.5, with FEC ³	—	49.3	—	dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal at 3 dB above required sen-	BLOCK _{10M}	#2b = (0, 4, 22) ² , 100 kbps, mi = 1.0, no FEC ⁴	_	78.6	—	dB
sitivity level according to IEEE 802.15.4-2020 section 19.6.7. Undesired signal is CW at \pm 10 MHz frequency offset.		#2b = (1, 4, 22) ² , 100 kbps, mi = 1.0, with FEC ⁶	_	83.9	_	dB
Co-Channel Rejection U/D ratio. Set Desired signal to 3 dB above required sensitivity	CoChR	#2b = (0, 4, 22) ² , 100 kbps, mi = 1.0, no FEC ⁴	—	-2.9	_	dB
level according to IEEE 805.15.4-2020 section		#1b = (1, 2, 21) ² , 50 kbps, mi = 1.0, with FEC ⁵	_	-1.4	_	dB
19.6.7. Undesired signal is CW with level adjusted to make PER = 10%.		#2b = (1, 4, 22) ² , 100 kbps, mi = 1.0, with FEC ⁶		-1.6	—	dB
		#3 = (1, 5, 22) ² , 150 kbps, mi = 0.5, with FEC ⁷		-4.9	—	dB
		#4b = (1, 7, 23) ² , 200 kbps, mi = 1.0, with FEC ⁸	_	-2.2	_	dB
		#5 = (1, 8, 23) ² , 300 kbps, mi = 0.5, with FEC ³	_	-5.3	_	dB

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Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Rx Energy Detection Magni-	AGC _{PreamME}	#1b, 50 kbps, mi = 1.0	_	1.0	_	dB
tude Error, and AGC, aver- aged over 8 repetitions of the		#2b, 100 kbps, mi = 1.0	_	0.9	_	dB
Preamble Field. ⁹		#3, 150 kbps, mi = 0.5	—	1.2	—	dB
		#4b, 200 kbps, mi = 1.0	—	1.1	—	dB
		#5, 300 kbps, mi = 0.5	—	1.2	—	dB
Frequency Error Sensitivity. Receiver signal level for 10% PER with the desired signal's frequency offset by the given F _{Err} .	SENS _{FE}	#2b = (0, 4, 22) ² , 100 kbps, mi = 1.0, no FEC ⁴ . F _{Err} = ± 110 ppm	_	-106.5	_	dBm
		#1b = (1, 2, 21) ² , 50 kbps, mi = 1.0, with FEC ⁵ . F _{Err} = ± 70 ppm	_	-109.7	_	dBm
		#2b = (1, 4, 22) ² , 100 kbps, mi = 1.0, with FEC ⁶ . F _{Err} = ± 110 ppm	—	-107.4	—	dBm
		#3 = (1, 5, 22) ² , 150 kbps, mi = 0.5, with FEC ⁷ . F _{Err} = ± 110 ppm	_	-109.3	—	dBm
		#4b = (1, 7, 23) ² , 200 kbps, mi = 1.0, with FEC ⁸ . F _{Err} = ± 90 ppm	_	-108.0	—	dBm
		#5 = (1, 8, 23) ² , 300 kbps, mi = 0.5, with FEC ³ . F _{Err} = ± 100 ppm	_	-106.1	—	dBm
Receive Signal Strength Indi-	RSSI	at SENS #2b = (1, 4, 22) ²	_	-111.1	_	dBm
cator in dB for the given in- put signal condition as meas- ured by the receiver with		3 dB above SENS #2b = (1, 4, 22) ²	—	-108.3	—	dBm
AGC active.		10 dB above SENS #2b = (1, 4, 22) ²	_	-101.4	—	dBm
		at -91 dBm, #2b = (1, 4, 22) ²	—	-91.8	—	dBm
		at -91 dBm and ACR1 #2b = $(1, 4, 22)^2$	_	-90.4	_	dBm
		at -40 dBm no interferer #2b = (1, 4, 22) ²	_	-40.7	_	dBm
		at -40 dBm with a co-channel CW interferer level adjusted for 10% PER #2b = (1, 4, 22) ²	_	-39.5	—	dBm
		at SENS _{FE} #2b = (1, 4, 22) ² ; F _{Err} = ± 110 ppm		-107.7		dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Note:			l			
1. Test Frequency F for for 22, and F = 923.		es slightly according to the PHY Char	inel Plan ID: F	= 923.6 MHz	for 21, F = 92	3.7 MHz
tested according to	Wi-SUN PHYWG TPS	sis for each Test Conditions descript S amendment 1VA9 with T = Type ID /i-SUN FSK Receiver Characteristics	in Table 3, M =	= Mode ID in 1	Table 4, and C	C = Chan-
•	300 kbps 2FSK, BT = 1.0 standard mode #5	2, mi = 0.5, PER<10%, Channel Spa	acing = 600 kH:	z, Data White	ning, with FE0	C. Per
	100 kbps 2FSK, BT = 1.0 standard mode #2	2, mi =1.0, PER<10%, Channel Spa b	cing = 400 kHz	z, Data Whiter	iing, without F	EC. Per
5. Reference signal is SUN FAN PHY 1.0		2, mi =1.0, PER<10%, Channel Spac	ing = 200 kHz,	Data Whitenii	ng, with FEC.	Per Wi-
6. Reference signal is SUN FAN PHY 1.0		2, mi =1.0, PER<10%, Channel Spa	cing = 400 kHz	z, Data Whiter	iing, with FEC	. Per Wi-
	150 kbps 2FSK, BT = 1.0 standard mode #3	2, mi = 0.5, PER<10%, Channel Spa	acing = 400 kH	z, Data White	ning, with FE0	C. Per
8. Reference signal is SUN FAN PHY 1.0		2, mi =1.0, PER<10%, Channel Spa	cing = 600 kHz	z, Data Whiter	iing, with FEC	. Per Wi-
dB above required s input signal level at The Magnitude Erro	sensitivity to 50 dB about the 50 Ω Antenna por	2.3.1 of IEEE 802.15.4-2020), sweep ove required sensitivity of 802.15.4-2 t along with the signal level measure e of the difference between these two ed).	020 section 19 d by the receive	.6.7 . At each er averaged o	2 dB step, reover 8 Preamb	cord the le Fields.

4.9.5.2 914 MHz Band RF Wi-SUN FSK Receiver Characteristics

Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, external PA Supply, supply filtering as shown in the typical connections section, crystal frequency = 39.0 MHz ± 1 ppm.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
RF test frequency range	F _{RANGE}		902	914	928	MHz
Rx Max Strong Signal Input Level for 10% PER.	RX _{SAT}	#5 = (1, 8, 3) ¹ , 300 kbps, mi = 0.5, with FEC ²	—	10	_	dBm
Rx Sensitivity for 10% Pack- et Error Rate (PER) with no interferer	SENS	#1b = (0, 2, 1) ¹ , 50 kbps, mi = 1.0, no FEC ³	—	-109.9	_	dBm
		#1b = $(1, 2, 1)^1$, 50 kbps, mi = 1.0, with FEC ⁴	—	-114.6	-110.5	dBm
		#2a = (1, 3, 1) ¹ , 100 kbps, mi = 0.5, with FEC ⁵	_	-110.9	_	dBm
		#3 = (1, 5, 2) ¹ , 150 kbps, mi = 0.5, with FEC ⁶	_	-109.4	-104.1	dBm
		#4a = (1, 6, 2) ¹ , 200 kbps, mi = 0.5, with FEC ⁷	_	-108.1	-104.5	dBm
		#5 = (1, 8, 3) ¹ , 300 kbps, mi = 0.5, with FEC ²	_	-106.4	_	dBm
Adjacent Channel Rejection U/D ratio for 10% PER ac- cording to IEEE	ACR1	#1b = (0, 2, 1) ¹ , 50 kbps, mi = 1.0, no FEC ³	_	45.2	_	dB
802.15.4-2020 section 19.6.8 with Desired signal at 3 dB above required sensitivity.		#1b = (1, 2, 1) ¹ , 50 kbps, mi = 1.0, with FEC ⁴	_	49.5	_	dB
Undesired signal is CW at ± 1 × channel spacing. Re-		#2a = (1, 3, 1) ¹ , 100 kbps, mi = 0.5, with FEC ⁵	_	46.3	_	dB
quires IR Calibration.		#3 = (1, 5, 2) ¹ , 150 kbps, mi = 0.5, with FEC ⁶	—	48.2	_	dB
		#4a = (1, 6, 2) ¹ , 200 kbps, mi = 0.5, with FEC ⁷	—	48.1	_	dB
		#5 = (1, 8, 3) ¹ , 300 kbps, mi = 0.5, with FEC ²	—	49.3	_	dB

Table 4.29. 914 MHz Band RF Wi-SUN FSK Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Alternate Channel Rejection U/D ratio for 10% PER ac- cording to IEEE	ACR2	#1b = (0, 2, 1) ¹ , 50 kbps, mi = 1.0, no FEC ³	_	51.0	—	dB
802.15.4-2020 section 19.6.8 with Desired signal at 3 dB above required sensitivity.		#1b = (1, 2, 1) ¹ , 50 kbps, mi = 1.0, with FEC ⁴	_	53.4	—	dB
Undesired signal is CW at ± 2 × channel spacing. Re- quires IR Calibration.		#2a = (1, 3, 1) ¹ , 100 kbps, mi = 0.5, with FEC ⁵	_	50.6	_	dB
		#3 = (1, 5, 2) ¹ , 150 kbps, mi = 0.5, with FEC ⁶	_	57.3	_	dB
		#4a = (1, 6, 2) ¹ , 200 kbps, mi = 0.5, with FEC ⁷	_	55.9	—	dB
		#5 = (1, 8, 3) ¹ , 300 kbps, mi = 0.5, with FEC ²	_	57.2	_	dB
Image Rejection U/D ratio for 10% PER. Undesired signal is CW at the RX image fre-	IR	#1b = (0, 2, 1) ¹ , 50 kbps, mi = 1.0, no FEC ³	_	46.8	—	dB
quency. Desired signal is 3dB above required sensitivi- ty level according to IEEE		#1b = (1, 2, 1) ¹ , 50 kbps, mi = 1.0, with FEC ⁴	_	51.4	_	dB
802.15.4-2020 section 19.6.7.		#2a = (1, 3, 1) ¹ , 100 kbps, mi = 0.5, with FEC ⁵	_	48.7	—	dB
		#3 = (1, 5, 2) ¹ , 150 kbps, mi = 0.5, with FEC ⁶	_	48.1	—	dB
		#4a = (1, 6, 2) ¹ , 200 kbps, mi = 0.5, with FEC ⁷	_	48.3	—	dB
		#5 = (1, 8, 3) ¹ , 300 kbps, mi = 0.5, with FEC ²	—	48.5	_	dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal at 3 dB above required sen-	BLOCK _{10M}	#1b = (0, 2, 1) ¹ , 50 kbps, mi = 1.0, no FEC ³	—	82.0	_	dB
sitivity level according to IEEE $802.15.4-2020$ section 19.6.7. Undesired signal is CW at \pm 10 MHz frequency offset.		#1b = (1, 2, 1) ¹ , 50 kbps, mi = 1.0, with FEC ⁴	—	87.1	_	dB
Co-Channel Rejection U/D ratio. Set Desired signal to 3 dB above required sensitivity	CoChR	#1b = (0, 2, 1) ¹ , 50 kbps, mi = 1.0, no FEC ³	_	-2.6	—	dB
level according to IEEE 805.15.4-2020 section		#1b = (1, 2, 1) ¹ , 50 kbps, mi = 1.0, with FEC ⁴	_	-1.3	_	dB
19.6.7. Undesired signal is CW with level adjusted to make PER = 10%.		#2a = (1, 3, 1) ¹ , 100 kbps, mi = 0.5, with FEC ⁵	—	-5.6		dB
		#3 = $(1, 5, 2)^1$, 150 kbps, mi = 0.5, with FEC ⁶	—	-4.7		dB
		#4a = (1, 6, 2) ¹ , 200 kbps, mi = 0.5, with FEC ⁷	—	-5.1		dB
		#5 = (1, 8, 3) ¹ , 300 kbps, mi = 0.5, with FEC ²	—	-5.4	_	dB

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Rx Energy Detection Magni-	AGC _{PreamME}	#1b, 50 kbps, mi = 1.0	_	1.4	_	dB
tude Error, and AGC, aver- aged over 8 repetitions of the		#2a, 100 kbps, mi = 0.5	_	2.3	_	dB
Preamble Field. ⁸		#3, 150 kbps, mi = 0.5	_	1.8	_	dB
		#4a, 200 kbps, mi = 0.5	—	1.9	_	dB
		#5, 300 kbps, mi = 0.5	_	1.4	_	dB
Frequency Error Sensitivity. Receiver signal level for 10% PER with the desired signal's	SENS _{FE}	#1b = (0, 2, 1) ¹ , 50 kbps, mi = 1.0, no FEC ³ . F _{Err} = ± 60 ppm	_	-109.0		dBm
frequency offset by the given F_{Err} .		#1b = $(1, 2, 1)^1$, 50 kbps, mi = 1.0, with FEC ⁴ . F _{Err} = ± 60 ppm	_	-109.7	—	dBm
		#2a = (1, 3, 1) ¹ , 100 kbps, mi = 0.5, with FEC ⁵ . F _{Err} = ± 60 ppm	_	-108.6	_	dBm
		#3 = $(1, 5, 2)^1$, 150 kbps, mi = 0.5, with FEC ⁶ . F _{Err} = ± 90 ppm	_	-106.8	_	dBm
		#4a = (1, 6, 2) ¹ , 200 kbps, mi = 0.5, with FEC ⁷ . F _{Err} = ± 110 ppm	_	-106.2	_	dBm
		#5 = $(1, 8, 3)^1$, 300 kbps, mi = 0.5, with FEC ² . F _{Err} = ± 110 ppm	_	-106.0	_	dBm
Receive Signal Strength Indi-	RSSI	at SENS #3 = (1, 5, 2) ¹	_	-109.6		dBm
cator in dB for the given in- put signal condition as meas-		3 dB above SENS #3 = (1, 5, 2) ¹	_	-106.2		dBm
ured by the receiver with AGC active.		10 dB above SENS #3 = (1, 5, 2) ¹	_	-99.2		dBm
		at -89 dBm, #3 = (1, 5, 2) ¹	_	-89.6		dBm
		at -89 dBm and ACR1 #3 = (1, 5, 2) ¹	_	-89.4	_	dBm
		at -40 dBm no interferer, #3 = (1, 5, 2) ¹	_	-40.4		dBm
		at -40 dBm with a co-channel CW interferer level adjusted for 10% PER #3 = (1, 5, 2) ¹	_	-40.4	_	dBm
		at SENS _{FE} #3 = (1, 5, 2) ¹ ; F _{Err} = ± 90 ppm	_	-107.0	_	dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Note:	I					
tested according to	WI-SUN PHYWG TPS	sis for each Test Conditions amendment 1VA9 with T = i-SUN FSK Receiver Charac	Type ID in Table 3, M =	Mode ID in T	able 4, and (C = Chan-
	300 kbps 2FSK, BT = .0 standard mode #5	2, mi = 0.5, PER<10%, Cha	nnel Spacing = 600 kH:	z, Data Whiter	ning, with FE	C. Per
	50 kbps 2FSK, BT = 2 .0 standard mode #11	2, mi =1.0, PER<10%, Chanr o	nel Spacing = 200 kHz,	Data Whitenir	ng, without Fl	EC. Per
4. Reference signal is SUN FAN PHY 1.0 s	•	2, mi =1.0, PER<10%, Chanr	nel Spacing = 200 kHz,	Data Whitenir	ng, with FEC.	Per Wi-
5. Reference signal is SUN FAN PHY 1.0 s		2, mi =0.5, PER<10%, Char	nnel Spacing = 200 kHz	, Data Whiten	ing, with FEC	C. Per Wi-
	150 kbps 2FSK, BT = .0 standard mode #3	2, mi = 0.5, PER<10%, Cha	nnel Spacing = 400 kH	z, Data Whiter	ning, with FE	C. Per
	200 kbps 2FSK, BT = .0 standard mode #4a	2, mi = 0.5, PER<10%, Cha a	nnel Spacing = 400 kH	z, Data Whiter	ning, without	FEC. Per
dB above required s input signal level at The Magnitude Erro	ensitivity to 50 dB abo the 50 Ω Antenna por	.3.1 of IEEE 802.15.4-2020) ove required sensitivity of 80 t along with the signal level r of the difference between the ed).	2.15.4-2020 section 19 neasured by the receive	.6.7 . At each a er averaged ov	2 dB step, re ver 8 Pream	cord the ble Fields.

4.9.5.3 866 MHz Band RF Wi-SUN FSK Receiver Characteristics

Unless otherwise indicated, typical conditions are: $T_A = 25$ °C, VREGVDD = PAVDD = AVDD = 3.3 V, DVDD = IOVDD0-2 = RFVDD = 1.8 V from DC-DC regulator output, external PA Supply, supply filtering as shown in the typical connections section, crystal frequency = 39.0 MHz ± 1 ppm.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		863	866.5	876	MHz
Rx Max Strong Signal Input Level for 10% PER.	RX _{SAT}	#3 = (1, 5, 37) ¹ , 150 kbps, mi = 0.5, with FEC ²	_	10	—	dBm
Rx Sensitivity for 10% Pack- et Error Rate (PER) with no interferer	SENS	#1a = (0, 1, 36) ¹ , 50 kbps, mi = 0.5, no FEC ³	_	-110.8	—	dBm
		#2a = (0, 3, 37) ¹ , 100 kbps, mi = 0.5, no FEC ⁴	_	-108.0	—	dBm
		#1a = (1, 1, 36) ¹ , 50 kbps, mi = 0.5, with FEC ⁵	_	-114.1	—	dBm
		#2a = (1, 3, 37) ¹ , 100 kbps, mi = 0.5, with FEC ⁶	_	-110.2	—	dBm
		#3 = (1, 5, 37) ¹ , 150 kbps, mi = 0.5, with FEC ²	_	-108.8	—	dBm
Adjacent Channel Rejection U/D ratio for 10% PER ac- cording to IEEE	ACR1	#1a = (0, 1, 36) ¹ , 50 kbps, mi = 0.5, no FEC ³	—	45.7	—	dB
802.15.4-2020 section 19.6.8 with Desired signal at 3 dB above required sensitivity.		#2a = (0, 3, 37) ¹ , 100 kbps, mi = 0.5, no FEC ⁴	_	44.8	—	dB
Undesired signal is CW at ± 1 × channel spacing. Re- quires IR Calibration.		#1a = (1, 1, 36) ¹ , 50 kbps, mi = 0.5, with FEC ⁵	_	49.3	—	dB
		#2a = (1, 3, 37) ¹ , 100 kbps, mi = 0.5, with FEC ⁶	_	46.9	_	dB
		#3 = (1, 5, 37) ¹ , 150 kbps, mi = 0.5, with FEC ²	—	45.5	—	dB
Alternate Channel Rejection U/D ratio for 10% PER ac- cording to IEEE	ACR2	#1a = (0, 1, 36) ¹ , 50 kbps, mi = 0.5, no FEC ³	—	45.1	—	dB
802.15.4-2020 section 19.6.8 with Desired signal at 3 dB above required sensitivity.		#2a = (0, 3, 37) ¹ , 100 kbps, mi = 0.5, no FEC ⁴	—	50.5	—	dB
Undesired signal is CW at ± 2 × channel spacing. Re- quires IR Calibration.		#1a = (1, 1, 36) ¹ , 50 kbps, mi = 0.5, with FEC ⁵	_	48.1	—	dB
		#2a = (1, 3, 37) ¹ , 100 kbps, mi = 0.5, with FEC ⁶	_	51.5	_	dB
		#3 = (1, 5, 37) ¹ , 150 kbps, mi = 0.5, with FEC ²	_	47.2	_	dB

Table 4.30. 866 MHz Band RF Wi-SUN FSK Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Image Rejection U/D ratio for 10% PER. Undesired signal is CW at the RX image fre-	IR	#1a = (0, 1, 36) ¹ , 50 kbps, mi = 0.5, no FEC ³	—	46.8	—	dB
quency. Desired signal is 3dB above required sensitivi- ty level according to IEEE		#2a = (0, 3, 37) ¹ , 100 kbps, mi = 0.5, no FEC ⁴		46.2		dB
802.15.4-2020 section 19.6.7.		#1a = (1, 1, 36) ¹ , 50 kbps, mi = 0.5, with FEC ⁵		49.8	—	dB
		#2a = (1, 3, 37) ¹ , 100 kbps, mi = 0.5, with FEC ⁶	_	48.6	—	dB
		#3 = (1, 5, 37) ¹ , 150 kbps, mi = 0.5, with FEC ²	_	47.8	_	dB
Blocking Selectivity U/D ratio for 10% PER. Desired signal	BLOCK _{10M}	#1a = (0, 1, 36) ¹ , 50 kbps, mi = 0.5, no FEC ³	_	84.1	_	dB
at 3 dB above required sen- sitivity level according to IEEE 802.15.4-2020 section 19.6.7. Undesired signal is CW at ± 10 MHz frequency offset.		#1a = (1, 1, 36) ¹ , 50 kbps, mi = 0.5, with FEC ⁵	_	87.0	_	dB
Co-Channel Rejection U/D ratio. Set Desired signal to 3 dB above required sensitivity	CoChR	#1a = (0, 1, 36) ¹ , 50 kbps, mi = 0.5, no FEC ³	—	-7.1	—	dB
level according to IEEE 805.15.4-2020 section 19.6.7. Undesired signal is		#2a = (0, 3, 37) ¹ , 100 kbps, mi = 0.5, no FEC ⁴	—	-7.2	—	dB
CW with level adjusted to make PER = 10%.		#1a = (1, 1, 36) ¹ , 50 kbps, mi = 0.5, with FEC ⁵	_	-4.4	—	dB
		#2a = (1, 3, 37) ¹ , 100 kbps, mi = 0.5, with FEC ⁶	—	-5.2	—	dB
		#3 = (1, 5, 37) ¹ , 150 kbps, mi = 0.5, with FEC ²	—	-4.4	—	dB
Rx Energy Detection Magni-	AGC _{PreamME}	#1a, 50 kbps, mi = 0.5	_	1.1	_	dB
tude Error, and AGC, aver- aged over 8 repetitions of the		#2a, 100 kbps, mi = 0.5	_	1.8	_	dB
Preamble Field. ⁷		#3, 150 kbps, mi = 0.5	_	1.4	_	dB
Frequency Error Sensitivity. Receiver signal level for 10% PER with the desired signal's	SENS _{FE}	#1a = (0, 1, 36) ¹ , 50 kbps, mi = 0.5, no FEC ³ . F _{Err} = ± 60 ppm	_	-107.1	—	dBm
frequency offset by the given F_{Err} .		#2a = (0, 3, 37) ¹ , 100 kbps, mi = 0.5, no FEC ⁴ . F _{Err} = ± 60 ppm	_	-105.9	—	dBm
		#1a = $(1, 1, 36)^1$, 50 kbps, mi = 0.5, with FEC ⁵ . F _{Err} = ± 60 ppm	_	-107.3	—	dBm
		#2a = (1, 3, 37) ¹ , 100 kbps, mi = 0.5, with FEC ⁶ . F _{Err} = ± 60 ppm	_	-108.3	_	dBm
		#3 = (1, 5, 37) ¹ , 150 kbps, mi = 0.5, with FEC ² . F _{Err} = ± 90 ppm	_	-106.6	_	dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Receive Signal Strength Indi-	RSSI	at SENS #2a = (1, 3, 37) ¹	—	-110.7	_	dBm
cator in dB for the given in- put signal condition as meas- ured by the receiver with AGC active.		3 dB above SENS #2a = (1, 3, 37) ¹		-107.9		dBm
		10 dB above SENS #2a = (1, 3, 37) ¹	—	-100.8	_	dBm
		at -91 dBm, #2a = (1, 3, 37) ¹	—	-92.2	_	dBm
		at -91 dBm and ACR1 #2a = (1, 3, 37) ¹		-91.7		dBm
		at -40 dBm no interferer #2a = (1, 3, 37) ¹		-41.1		dBm
		at -40 dBm with a co-channel CW interferer level adjusted for 10% PER #2a = (1, 3, 37) ¹	_	-41.0	_	dBm
		at SENS _{FE} #2a = (1, 3, 37) ¹ ; F _{Err} = ± 60 ppm		-109.2	_	dBm

- 1. The indexes provided inside the parenthesis for each Test Conditions description are (T, M, C) and these define the PHY being tested according to Wi-SUN PHYWG TPS amendment 1VA9 with T = Type ID in Table 3, M = Mode ID in Table 4, and C = Channel Plan ID in Tables 6 and 7. 4.9.5 RF Wi-SUN FSK Receiver Characteristics summarizes the options listed in this document.
- 2. Reference signal is 150 kbps 2FSK, BT = 2, mi = 0.5, PER<10%, Channel Spacing = 200 kHz, Data Whitening, with FEC. Per Wi-SUN FAN PHY 1.0 standard mode #3
- 3. Reference signal is 50 kbps 2FSK, BT = 2, mi =0.5, PER<10%, Channel Spacing = 100 kHz, Data Whitening, without FEC. Per Wi-SUN FAN PHY 1.0 standard mode #1a
- 4. Reference signal is 100 kbps 2FSK, BT = 2, mi =0.5, PER<10%, Channel Spacing = 200 kHz, Data Whitening, without FEC. Per Wi-SUN FAN PHY 1.0 standard mode #2a
- 5. Reference signal is 50 kbps 2FSK, BT = 2, mi =0.5, PER<10%, Channel Spacing = 100 kHz, Data Whitening, with FEC. Per Wi-SUN FAN PHY 1.0 standard mode #1a
- 6. Reference signal is 100 kbps 2FSK, BT = 2, mi =0.5, PER<10%, Channel Spacing = 200 kHz, Data Whitening, with FEC. Per Wi-SUN FAN PHY 1.0 standard mode #2a
- 7. Using Preamble Field signal (section 19.2.3.1 of IEEE 802.15.4-2020), sweep Antenna input level in 2 dB steps starting from 10 dB above required sensitivity to 50 dB above required sensitivity of 802.15.4-2020 section 19.6.7. At each 2 dB step, record the input signal level at the 50 Ω Antenna port along with the signal level measured by the receiver averaged over 8 Preamble Fields. The Magnitude Error is the absolute value of the difference between these two at the 2 dB step with the worst Error. AGC_Pre-amME = Max(|Avg(Rx_meas) Rx_applied|).

4.9.6 RF SUN OFDM Receiver Characteristics

OFDM Modulation is defined in Wi-SUN Alliance PHY Working Group (PHYWG TPS) Wi-SUN PHY Technical Specification - Amendment 1VA9 November 2022 which refers to IEEE 802.15.4-2020 especially section 20.3 . In this table the indication "OptX, MCSy" means X as the Option number 1 through 4, and y is the MCS index 0 through 6, and PL is the Packet PPDU Length in octets. Unless otherwise specified, for OFDM Options 1 and 2 header is normally MCS0, for Option 3 header is normally MCS1, and for Option 4 header is normally MCS2. Measurements use packet length of 250 octets when data rate is 50 kbps or higher, and 20 octets packet length when lower than 50 kbps.

4.9.6.1 923 MHz Band RF SUN OFDM Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range ¹	F _{RANGE}		922.3	923.x	928.1	MHz

Table 4.31. 923 MHz Band RF SUN OFDM Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Rx Sensitivity for 10% Pack-	SENS	923.5 MHz, Opt2, MCS0 ²	_	-113.0	-111.3	dBm
et Error Rate (PER) with no interferer		923.5 MHz, Opt2, MCS0		-113.0	-108.3	dBm
		923.5 MHz, Opt2, MCS1		-112.1	_	dBm
		923.5 MHz, Opt2, MCS2		-109.9	_	dBm
		923.5 MHz, Opt2, MCS3 ²	_	-107.3	-106.0	dBm
		923.5 MHz, Opt2, MCS3		-107.3	-103.1	dBm
		923.5 MHz, Opt2, MCS4		-104.8	_	dBm
		923.5 MHz, Opt2, MCS5	_	-102.0	_	dBm
		923.5 MHz, Opt2, MCS6 ²	—	-98.4	-97.3	dBm
		923.5 MHz, Opt2, MCS6		-98.4	-94.3	dBm
		923.7 MHz, Opt3, MCS0, header MCS0, with PL = 20 octets ²	_	-115.0	-113.1	dBm
		923.7 MHz, Opt3, MCS0, header MCS0, with PL = 20 octets	_	-115.0	-110.2	dBm
		923.7 MHz, Opt3, MCS1, header MCS1 ²	_	-114.3	-112.7	dBm
		923.7 MHz, Opt3, MCS1, header MCS1	_	-114.3	-109.3	dBm
		923.7 MHz, Opt3, MCS2 ²		-112.1	-110.6	dBm
		923.7 MHz, Opt3, MCS2		-112.1	-107.4	dBm
		923.7 MHz, Opt3, MCS3 ²		-109.9	-108.1	dBm
		923.7 MHz, Opt3, MCS3		-109.9	-105.4	dBm
		923.7 MHz, Opt3, MCS4 ²		-107.5	-106.2	dBm
		923.7 MHz, Opt3, MCS4		-107.5	-103.2	dBm
		923.7 MHz, Opt3, MCS5 ²		-104.9	-103.2	dBm
		923.7 MHz, Opt3, MCS5		-104.9	-100.1	dBm
		923.7 MHz, Opt3, MCS6 ²		-101.1	-100.0	dBm
		923.7 MHz, Opt3, MCS6		-101.1	-96.5	dBm
		923.6 MHz, Opt4, MCS0, header MCS0, with PL = 20 octets		-115.8	_	dBm
		923.6 MHz, Opt4, MCS2, header MCS2		-113.4	_	dBm
		923.6 MHz, Opt4, MCS4 ²		-110.3	-108.2	dBm
		923.6 MHz, Opt4, MCS4		-110.3	-105.4	dBm
		923.6 MHz, Opt4, MCS5 ²		-107.6	-106.0	dBm
		923.6 MHz, Opt4, MCS5		-107.6	-102.2	dBm
		923.6 MHz, Opt4, MCS6 ²		-104.0	-102.3	dBm
		923.6 MHz, Opt4, MCS6		-104.0	-99.7	dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Rx Max Strong Signal Input	RX _{SAT}	923.5 MHz, Opt2, MCS3	_	10		dBm
Level for 10% PER for pack- et length = 250 octets unless		923.5 MHz, Opt2, MCS6	_	10	_	dBm
otherwise stated.		923.7 MHz, Opt3, MCS4	_	10		dBm
		923.7 MHz, Opt3, MCS6	_	10		dBm
Adjacent Channel Rejection	ACR1	923.5 MHz, Opt2, MCS3	_	33.9	_	dB
U/D ratio for 10% PER ac- cording to IEEE		923.5 MHz, Opt2, MCS6	_	31.8	_	dB
802.15.4-2020 section 20.5.4 with Desired signal at 3 dB		923.7 MHz, Opt3, MCS4	33.7	35.5	_	dB
above required sensitivity in Table 20-21, and Undesired		923.7 MHz, Opt3, MCS6	19.3	31.2	_	dB
signal on an adjacent chan-		923.6 MHz, Opt4, MCS4	_	32.0	_	dB
nel. Requires IR Calibration. ³		923.6 MHz, Opt4, MCS6	_	31.1	_	dB
Alternate Adjacent Channel	ACR2	923.5 MHz, Opt2, MCS3	_	38.9	_	dB
Rejection U/D ratio for 10% PER according to IEEE		923.5 MHz, Opt2, MCS6	_	39.8	_	dB
802.15.4-2020 section 20.5.5 with Desired signal at 3 dB		923.7 MHz, Opt3, MCS4	39.8	42.9	_	dB
above required sensitivity in Table 20-21, and Undesired		923.7 MHz, Opt3, MCS6	35.5	38.9	_	dB
signal at two frequency		923.6 MHz, Opt4, MCS4	_	37.0		dB
channels away. Requires IR Calibration. ³		923.6 MHz, Opt4, MCS6	—	37.3	_	dB
Image Rejection U/D Ratio for 10% PER. Undesired sig-	IR	923.5 MHz, Opt2, MCS3	_	33.9		dB
nal is CW at the RX image		923.5 MHz, Opt2, MCS6		31.8		dB
frequency. Desired signal is 3dB above required sensitivi-		923.7 MHz, Opt3, MCS4	_	35.5		dB
ty level according to IEEE 802.15.4-2020 section		923.7 MHz, Opt3, MCS6	—	31.2	—	dB
20.5.3.		923.6 MHz, Opt4, MCS4		32.0	_	dB
		923.6 MHz, Opt4, MCS6		31.1	_	dB
Blocking Selectivity U/D ratio	BLOCK _{10M}	923.5 MHz, Opt2, MCS3		59.9		dB
for 10% PER. Desired signal at 3 dB above required sen-		923.7 MHz, Opt3, MCS4		61.3		dB
sitivity. Undesired signal is modulated and at ± 10 MHz		923.7 MHz, Opt3, MCS6		57.1		dB
frequency offset. ³		923.6 MHz, Opt4, MCS4	—	63.8		dB
		923.6 MHz, Opt4, MCS6		58.1	_	dB
Co-Channel Rejection U/D	CoChR	923.5 MHz, Opt2, MCS3	—	-4.1		dB
ratio. Set Desired signal to 3 dB above required sensitivity		923.5 MHz, Opt2, MCS6	—	-13.0	_	dB
level according to IEEE 805.15.4-2020 section		923.7 MHz, Opt3, MCS4	-7.4	-6.5	_	dB
20.5.3. Undesired signal lev- el shall be adjusted to make		923.7 MHz, Opt3, MCS6	-14.0	-13.1	_	dB
PER = 10% . ³		923.6 MHz, Opt4, MCS4		-4.9		dB
		923.6 MHz, Opt4, MCS6		-11.3		dB
Rx Energy Detection Magni-	AGC _{STFME}	923.5 MHz, Opt2, STF		0.8		dB
tude Error, and AGC, aver- aged over 8 symbols of		923.7 MHz, Opt3, STF		1.1		dB
Short Training Field. ⁴		923.6 MHz, Opt4, STF	_	0.7		dB

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Frequency Error Sensitivity.	SENS _{FE}	923.5 MHz, Opt2, MCS3	_	-107.5		dBm
Receiver signal level for 10% PER with the desired signal's		923.5 MHz, Opt2, MCS6	_	-98.4	_	dBm
frequency offset by ± 60 ppm.		923.7 MHz, Opt3, MCS4 ²	_	-107.4	-105.8	dBm
		923.7 MHz, Opt3, MCS4	_	-107.4	-103.1	dBm
		923.7 MHz, Opt3, MCS6 ²	_	-101.0	-99.4	dBm
		923.7 MHz, Opt3, MCS6	_	-101.0	-96.5	dBm
		923.6 MHz, Opt4, MCS4	_	-110.1		dBm
		923.6 MHz, Opt4, MCS6	_	-104.1	_	dBm
Signal Quality Estimate in-	SQE	at SENS Opt3, MCS6	_	101	_	index
dex [0-255] for the given in- put signal condition as meas-		3 dB above SENS Opt3, MCS6	—	121	—	index
ured by the receiver with AGC active.		10 dB above SENS Opt3, MCS6	—	176	_	index
		at -88 dBm Opt3, MCS6	—	197		index
		at -88 dBm and Undesired at ACR1 Opt3, MCS6	—	104	_	index
		at -40 dBm no interferer Opt3, MCS6	—	248		index
		at -40 dBm with a co-channel un- desired signal level adjusted for 10% PER ³ Opt3, MCS6	_	103	_	index
		at SENS _{FE} Opt3, MCS6, with 60 ppm	_	99	_	index
Receive Signal Strength Indi-	RSSI	at SENS Opt3, MCS6 ²	_	-101.2	_	dBm
cator in dB for the given in- put signal condition as meas-		3 dB above SENS Opt3, MCS6 ²	-100.0	-98.4	-96.7	dBm
ured by the receiver with AGC active.		10 dB above SENS Opt3, MCS6 ²	-93.1	-91.6	-89.8	dBm
		at -88 dBm Opt3, MCS6 ²	-90.1	-88.4	-86.6	dBm
		at -88 dBm and ACR1 Opt3, MCS6 ²	-89.7	-88.1	-86.8	dBm
		at -40 dBm no interferer Opt3, MCS6 ²	-42.8	-40.8	-38.6	dBm
		at -40 dBm with a co-channel un- desired signal level adjusted for 10% PER ³ Opt3, MCS6 ²	-42.4	-40.8	-39.1	dBm
		at SENS _{FE} Opt3, MCS6, with 60 ppm ²	-103.0	-101.3	-100.0	dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Note:	-					
1. Typical frequency is defir	ned in the Test Con	dition column, and varies on selecte	d Option.			
2. Min/Max numbers are me	easured at typical v	oltage, at typical F _{RANGE} frequency,	and at $T_A = 2$	25 °C.		
		dulation type and settings as the de LTF are excluded from the frame of t			out containing	different
10 dB above required set 20-21. At each 2 dB step receiver averaged over 8	nsitivity to 50 dB ab , record the input si STF symbols. The	20.2.2 of IEEE 802.15.4-2020), sweat pove required sensitivity of the Option ignal level at the 50 Ω Antenna port a Magnitude Error is the absolute value = Max(Avg(Rx_meas) - Rx_applied	n in test with I along with the ue of the diffe	MCS0 in 802. signal level	15.4-2020 Ta measured by t	ble the

4.9.6.2 914 MHz Band RF SUN OFDM Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		902	914	928	MHz
Rx Sensitivity for 10% Pack-	SENS	Opt1, MCS0 ¹	_	-110.8	-109.6	dBm
et Error Rate (PER) with no interferer		Opt1, MCS0	_	-110.8	-106.0	dBm
		Opt1, MCS1	_	-109.7		dBm
		Opt1, MCS2 ¹	_	-107.1	-106.1	dBm
		Opt1, MCS2	_	-107.1	-102.7	dBm
		Opt1, MCS3	_	-104.3	_	dBm
		Opt1, MCS4	_	-101.8	_	dBm
		Opt1, MCS5	_	-99.0	_	dBm
		Opt1, MCS6 ¹	_	-95.3	-94.6	dBm
		Opt1, MCS6	_	-95.3	-91.0	dBm
		Opt2, MCS0	_	-113.0	_	dBm
		Opt2, MCS1	_	-112.2	_	dBm
		Opt2, MCS2	_	-109.9	_	dBm
		Opt2, MCS3 ¹	_	-107.4	-106.1	dBm
		Opt2, MCS3	_	-107.4	-102.4	dBm
		Opt2, MCS4	_	-104.9		dBm
		Opt2, MCS5	_	-102.1		dBm
		Opt2, MCS6 ¹	_	-98.5	-97.3	dBm
		Opt2, MCS6	—	-98.5	-94.3	dBm
		Opt3, MCS1, header MCS1	_	-114.3	_	dBm
		Opt3, MCS4	—	-107.7	_	dBm
		Opt3, MCS6 ¹	—	-101.1	-100.1	dBm
		Opt3, MCS6	_	-101.1	-96.5	dBm
		Opt4, MCS0, header MCS0, with PL = 20 octets	_	-116.0		dBm
		Opt4, MCS6 ¹	_	-104.0	-102.6	dBm
		Opt4, MCS6	_	-104.0	-99.7	dBm
Rx Max Strong Signal Input	RX _{SAT}	Opt1, MCS2	_	10	_	dBm
Level for 10% PER for pack- et length = 250 octets unless		Opt1, MCS6	_	10		dBm
otherwise stated.		Opt2, MCS3	_	10	_	dBm
		Opt2, MCS6	_	10	_	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Adjacent Channel Rejection	ACR1	Opt1, MCS2		30.2		dB
U/D ratio for 10% PER ac- cording to IEEE		Opt1, MCS6		27.8		dB
802.15.4-2020 section 20.5.4 with Desired signal at 3 dB		Opt2, MCS3		33.9		dB
above required sensitivity in Table 20-21, and Undesired signal on an adjacent chan- nel. Requires IR Calibration. ²		Opt2, MCS6		34.7	_	dB
Iternate Adjacent Channel	ACR2	Opt1, MCS2		41.0		dB
Rejection U/D ratio for 10% PER according to IEEE		Opt1, MCS6		36.6	_	dB
802.15.4-2020 section 20.5.5 with Desired signal at 3 dB		Opt2, MCS3	—	38.9	_	dB
above required sensitivity in Table 20-21, and Undesired signal at two frequency channels away. Requires IR Calibration. ²		Opt2, MCS6	_	39.7	_	dB
Image Rejection U/D Ratio	IR	Opt1, MCS2		30.2		dB
for 10% PER. Undesired sig- nal is CW at the RX image		Opt1, MCS6		27.8		dB
frequency. Desired signal is 3dB above required sensitivi-		Opt2, MCS3		33.9		dB
ty level according to IEEE 802.15.4-2020 section 20.5.3.		Opt2, MCS6	_	34.7	_	dB
Blocking Selectivity U/D ratio	BLOCK _{10M}	Opt1, MCS2	—	54.5	—	dB
for 10% PER. Desired signal at 3 dB above required sen-		Opt1, MCS6	—	48.4	—	dB
sitivity. Undesired signal is modulated and at ± 10 MHz		Opt2, MCS3	_	60.2	_	dB
frequency offset. ²		Opt2, MCS6	—	52.2	—	dB
Co-Channel Rejection U/D	CoChR	Opt1, MCS2	—	-2.1	—	dB
ratio. Set Desired signal to 3 dB above required sensitivity		Opt1, MCS6	—	-14.0	—	dB
level according to IEEE 805.15.4-2020 section		Opt2, MCS3	—	-4.0	—	dB
20.5.3. Undesired signal level shall be adjusted to make PER = 10% ²		Opt2, MCS6		-13.0	_	dB
Rx Energy Detection Magni-	AGC _{STFME}	Opt1, STF	_	0.7	_	dB
tude Error, and AGC, aver- aged over 8 symbols of		Opt2, STF		0.6		dB
Short Training Field. ³		Opt3, STF		0.8		dB
		Opt4, STF	—	0.5	—	dB
Frequency Error Sensitivity.	SENS _{FE}	Opt1, MCS2	—	-107.1	_	dBm
Receiver signal level for 10% PER with the desired signal's		Opt1, MCS6	—	-95.3	_	dBm
frequency offset by ± 60 ppm.		Opt2, MCS3	—	-107.6	_	dBm
		Opt2, MCS6	—	-98.4		dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Signal Quality Estimate in-	SQE	at SENS Opt1, MCS6		100		index
dex [0-255] for the given in- put signal condition as meas-		3 dB above SENS Opt1, MCS6	_	120	_	index
ured by the receiver with AGC active.		10 dB above SENS Opt1, MCS6		173		index
		at -82 dBm Opt1, MCS6	_	194		index
		at -82 dBm and Undesired at ACR1 Opt1, MCS6	_	102	_	index
		at -40 dBm no interferer Opt1, MCS6	_	254	_	index
		at -40 dBm with a co-channel un- desired signal level adjusted for 10% PER ² Opt1, MCS6	_	98	—	index
		at SENS _{FE} Opt1, MCS6, with 60 ppm	_	97	_	index
Receive Signal Strength Indi-	RSSI	at SENS Opt1, MCS6	_	-94.1	_	dBm
cator in dB for the given in- put signal condition as meas-		3 dB above SENS Opt1, MCS6	_	-91.1	_	dBm
ured by the receiver with AGC active.		10 dB above SENS Opt1, MCS6	_	-84.2	_	dBm
		at -82 dBm, Opt1, MCS6	_	-81.2	_	dBm
		at -82 dBm and ACR1 Opt1, MCS6	_	-81.0	_	dBm
		at -40 dBm no interferer Opt1, MCS6	_	-39.5	—	dBm
		at -40 dBm with a co-channel un- desired signal level adjusted for 10% PER ² Opt1, MCS6	—	-39.6	—	dBm
		at SENS _{FE} Opt1, MCS6, with 60 ppm		-94.3		dBm

1. Min/Max numbers are measured at typical voltage, at typical F_{RANGE} frequency, and at T_A = 25 °C.

2. The undesired signal shall use the same modulation type and settings as the desired signal being tested, but containing different pseudo random data in its PSDU. STF and LTF are excluded from the frame of the undesired signal.

3. Using a Short Training Field signal (section 20.2.2 of IEEE 802.15.4-2020), sweep Antenna input level in 2 dB steps starting from 10 dB above required sensitivity to 50 dB above required sensitivity of the Option in test with MCS0 in 802.15.4-2020 Table 20-21. At each 2 dB step, record the input signal level at the 50 Ω Antenna port along with the signal level measured by the receiver averaged over 8 STF symbols. The Magnitude Error is the absolute value of the difference between these two at the 2 dB step with the worst Error. AGC_STFME = Max(|Avg(Rx_meas) - Rx_applied|).

4.9.6.3 866 MHz Band RF SUN OFDM Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
RF test frequency range	F _{RANGE}		863.1	866.5	876	MHz
Rx Sensitivity for 10% Pack- et Error Rate (PER) with no	SENS	Opt4, MCS0, header MCS0, with PL = 20 octets	_	-115.6	_	dBm
interferer		Opt4, MCS2, header MCS2 ¹	_	-113.2	-110.4	dBm
		Opt4, MCS2, header MCS2	_	-113.2	-108.9	dBm
		Opt4, MCS4 ¹	_	-110.1	-108.1	dBm
		Opt4, MCS4	_	-110.1	-105.1	dBm
		Opt4, MCS5		-107.4	_	dBm
		Opt4, MCS6 ¹	_	-103.8	-102.1	dBm
		Opt4, MCS6		-103.8	-99.9	dBm
Rx Max Strong Signal Input	RX _{SAT}	Opt4, MCS4	_	10	_	dBm
Level for 10% PER for pack- et length = 250 octets unless otherwise stated.		Opt4, MCS6	_	10	_	dBm
Adjacent Channel Rejection	ACR1	Opt4, MCS4	_	34.8	_	dB
U/D ratio for 10% PER ac- cording to IEEE 802.15.4-2020 section 20.5.4 with Desired signal at 3 dB above required sensitivity in Table 20-21, and Undesired signal on an adjacent chan- nel. Requires IR Calibration. ²		Opt4, MCS6	_	32.5	_	dB
Alternate Adjacent Channel	ACR2	Opt4, MCS4	—	40.2	_	dB
Rejection U/D ratio for 10% PER according to IEEE 802.15.4-2020 section 20.5.5 with Desired signal at 3 dB above required sensitivity in Table 20-21, and Undesired signal at two frequency channels away. Requires IR Calibration. ²		Opt4, MCS6	_	37.7		dB
Image Rejection U/D Ratio	IR	Opt4, MCS4	—	34.8	—	dB
for 10% PER. Undesired sig- nal is CW at the RX image frequency. Desired signal is 3dB above required sensitivi- ty level according to IEEE 802.15.4-2020 section 20.5.3.		Opt4, MCS6	_	32.5		dB
Blocking Selectivity U/D ratio	BLOCK _{10M}	Opt4, MCS4		64.4	_	dB
for 10% PER. Desired signal at 3 dB above required sen- sitivity. Undesired signal is modulated and at \pm 10 MHz frequency offset. ²		Opt4, MCS6	_	58.3	_	dB

Table 4.33. 866 MHz Band RF SUN OFDM Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Co-Channel Rejection U/D	CoChR	Opt4, MCS4	_	-4.9	_	dB
ratio. Set Desired signal to 3 dB above required sensitivity level according to IEEE 805.15.4-2020 section 20.5.3. Undesired signal lev- el shall be adjusted to make PER = 10%. ²		Opt4, MCS6	_	-11.3		dB
Rx Energy Detection Magni- tude Error, and AGC, aver- aged over 8 symbols of Short Training Field. ³	AGC _{STFME}	Opt4, STF	_	3.9	_	dB
Frequency Error Sensitivity. Receiver signal level for 10% PER with the desired signal's frequency offset by \pm 60 ppm.	SENS _{FE}	Opt4, MCS4	—	-109.9	_	dBm
		Opt4, MCS6	_	-102.7	_	dBm
Signal Quality Estimate in-	SQE	at SENS Opt4, MCS6	_	103	—	index
dex [0-255] for the given in- put signal condition as meas-		3 dB above SENS Opt4, MCS6	_	124	—	index
ured by the receiver with AGC active.		10 dB above SENS Opt4, MCS6	_	172	—	index
		at -91 dBm, Opt4, MCS6	_	182	—	index
		at -91 dBm and ACR1 Opt4, MCS6	—	122	—	index
		at -40 dBm no interferer Opt4, MCS6	—	214	—	index
		at -40 dBm with a co-channel un- desired signal level adjusted for 10% PER ² Opt4, MCS6	_	104	—	index
		at SENS _{FE} Opt4, MCS6, with 60 ppm	_	99	_	index
Receive Signal Strength Indi-	RSSI	at SENS Opt4, MCS6		-104.3	_	dBm
cator in dB for the given in- put signal condition as meas-		3 dB above SENS Opt4, MCS6	_	-101.4	—	dBm
ured by the receiver with AGC active.		10 dB above SENS Opt4, MCS6	_	-94.4	_	dBm
		at -91 dBm Opt4, MCS6	_	-92.5	—	dBm
		at -91 dBm and Undesired at ACR1 Opt4, MCS6	—	-92.2	—	dBm
		at -40 dBm no interferer Opt4, MCS6		-43.1	_	dBm
		at -40 dBm with a co-channel un- desired signal level adjusted for 10% PER ² Opt4, MCS6	_	-42.5	_	dBm
		at SENS _{FE} Opt4, MCS6, with 60 ppm	—	-105.0	_	dBm

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Note:					•	
1. Min/Max numbers are measured at typical voltage, at typical F_{RANGE} frequency, and at T_A = 25 °C.						
		e modulation type and settings and LTF are excluded from the			out containing	different
10 dB above requ 20-21. At each 2 receiver averaged	uired sensitivity to 50 d dB step, record the inp d over 8 STF symbols.	ion 20.2.2 of IEEE 802.15.4-2 B above required sensitivity of ut signal level at the 50 Ω Ant The Magnitude Error is the at ME = Max(Avg(Rx_meas) - F	the Option in test with enna port along with the solute value of the diffe	MCS0 in 802. e signal level i	15.4-2020 Ta measured by	ble the
4.9.6.4 490 MHz Band RF SUN OFDM Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
RF test frequency range	F _{RANGE}		470	490	510	MHz
Rx Sensitivity for 10% Pack- et Error Rate (PER) with no	SENS	Opt4, MCS0, header MCS0, with PL = 20 octets	_	-116.8	_	dBm
interferer		Opt4, MCS2, header MCS2	_	-114.5	_	dBm
		Opt4, MCS4, header MCS2	—	-111.4	—	dBm
		Opt4, MCS5, header MCS2	—	-108.7	—	dBm
		Opt4, MCS6, header MCS2	_	-105.2	_	dBm
Rx Max Strong Signal Input Level for 10% PER for pack-	RX _{SAT}	Opt4, MCS2, header MCS2, with PL = 20 octets	_	10	—	dBm
et length = 250 octets unless otherwise stated.		Opt4, MCS6, header MCS2	—	10	_	dBm
Adjacent Channel Rejection	ACR1	Opt4, MCS2, header MCS2	_	43.9		dB
U/D ratio for 10% PER ac- cording to IEEE 802.15.4-2020 section 20.5.4 with Desired signal at 3 dB above required sensitivity in Table 20-21, and Undesired signal on an adjacent chan- nel. Requires IR Calibration. ¹		Opt4, MCS6, header MCS2	_	34.0	_	dB
Alternate Adjacent Channel	ACR2	Opt4, MCS2, header MCS2	_	47.8		dB
Rejection U/D ratio for 10% PER according to IEEE 802.15.4-2020 section 20.5.5 with Desired signal at 3 dB above required sensitivity in Table 20-21, and Undesired signal at two frequency channels away. Requires IR Calibration. ¹		Opt4, MCS6, header MCS2	_	37.5	_	dB
Image Rejection U/D Ratio	IR	Opt4, MCS2, header MCS2	—	43.9	_	dB
for 10% PER. Undesired sig- nal is CW at the RX image frequency. Desired signal is 3dB above required sensitivi- ty level according to IEEE 802.15.4-2020 section 20.5.3.		Opt4, MCS6, header MCS2	_	34.0	_	dB
Blocking Selectivity U/D ratio	BLOCK _{10M}	Opt4, MCS2, header MCS2	—	69.0		dB
for 10% PER. Desired signal at 3 dB above required sen- sitivity. Undesired signal is modulated and at \pm 10 MHz frequency offset. ¹		Opt4, MCS6, header MCS2	_	59.8		dB

Table 4.34. 490 MHz Band RF SUN OFDM Receiver Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Co-Channel Rejection U/D	CoChR	Opt4, MCS2, header MCS2	_	-2.2		dB
ratio. Set Desired signal to 3 dB above required sensitivity level according to IEEE 805.15.4-2020 section 20.5.3. Undesired signal lev- el shall be adjusted to make PER = 10%. ¹		Opt4, MCS6, header MCS2	-	-11.4	_	dB
Rx Energy Detection Magni- tude Error, and AGC, aver- aged over 8 symbols of Short Training Field. ²	AGC _{STFME}	Opt4, STF	_	0.5	_	dB
Frequency Error Sensitivity.	SENS _{FE}	Opt4, MCS2, header MCS2	_	-114.0	_	dBm
Receiver signal level for 10% PER with the desired signal's frequency offset by \pm 60 ppm.		Opt4, MCS6, header MCS2	_	-105.0	_	dBm
Signal Quality Estimate in-	SQE	at SENS Opt4, MCS6	_	99	_	index
dex [0-255] for the given in- put signal condition as meas- ured by the receiver with AGC active.		3 dB above SENS Opt4, MCS6	—	119	—	index
		10 dB above SENS Opt4, MCS6	—	166	—	index
		at -91 dBm, Opt4, MCS6	—	187	_	index
		at -91 dBm and ACR1 Opt4, MCS6	—	102	—	index
		at -40 dBm no interferer Opt4, MCS6	_	216	_	index
		at -40 dBm with a co-channel un- desired signal level adjusted for 10% PER ¹ Opt4, MCS6	_	104	—	index
		at SENS _{FE} Opt4, MCS6, with 60 ppm	_	99	_	index
Receive Signal Strength Indi-	RSSI	at SENS Opt4, MCS6	_	-107.1	_	dBm
cator in dB for the given in- put signal condition as meas-		3 dB above SENS Opt4, MCS6		-104.3		dBm
ured by the receiver with AGC active.		10 dB above SENS Opt4, MCS6		-97.4		dBm
		at -91 dBm Opt4, MCS6	_	-93.4	_	dBm
		at -91 dBm and Undesired at ACR1 Opt4, MCS6	_	-92.4	_	dBm
		at -40 dBm no interferer Opt4, MCS6	_	-44.5		dBm
		at -40 dBm with a co-channel un- desired signal level adjusted for 10% PER ¹ Opt4, MCS6	_	-44.2	_	dBm
		at SENS _{FE} Opt4, MCS6, with 60 ppm	_	-106.8	_	dBm

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit		
Note:								
1. The undesired signal shall use the same modulation type and settings as the desired signal being tested, but containing different pseudo random data in its PSDU. STF and LTF are excluded from the frame of the undesired signal.								
2. Using a Short Trair	ing Field signal (secti	on 20.2.2 of IEEE 802.15.4-2020), sw	eep Antenna ir	put level in 2	dB steps star	ting from		

10 dB above required sensitivity to 50 dB above required sensitivity of the Option in test with MCS0 in 802.15.4-2020 Table 20-21. At each 2 dB step, record the input signal level at the 50 Ω Antenna port along with the signal level measured by the receiver averaged over 8 STF symbols. The Magnitude Error is the absolute value of the difference between these two at the 2 dB step with the worst Error. AGC_STFME = Max(|Avg(Rx_meas) - Rx_applied|).

4.10 Oscillators

4.10.1 High Frequency Crystal Oscillator

Unless otherwise indicated, typical conditions are: AVDD = DVDD = RFVDD = PAVDD = VREGVDD = IOVDD0-2 = 3.6 V. DC-DC not used. $T_A = 25$ °C. Minimum and maximum values in this table represent the worst conditions across process variation, operating supply voltage range, and operating temperature range.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Crystal Frequency	F _{HFXO}	see note ¹	38.0	39.0	40.0	MHz
Supported crystal equivalent series resistance (ESR)	ESR _{HFXO}	39.0 MHz, C _L = 10 pF ²		_	60	Ω
Supported range of crystal load capacitance ³	C _{HFXO_LC}	39.0 MHz, ESR = 40 Ohm ⁴	_	10	_	pF
Supply Current	I _{HFXO}			479	_	μA
Startup Time ⁵	T _{STARTUP}	39.0 MHz, ESR = 40 Ω, C _L = 10 pF		201	_	μs
On-chip tuning cap step size ⁶	SS _{HFXO}			0.04	_	pF
HFCLKOUT load capaci- tance	C _{HFCLKOUT}		_	20	30	pF
HFCLKOUT output voltage	V _{HFCLKOUT}		0	_	1.2	V
HFCLKOUT AC output am- plitude, XOUTBIASANA = 5, C _{HFCLKOUT} = 20 pF	VAC _{HFCLKOUT}	XOUTCFANA = 0		470	_	mVpp
		XOUTCFANA = 1		510	_	mVpp
		XOUTCFANA = 2		560	_	mVpp
		XOUTCFANA = 3		615	_	mVpp
HFCLKOUT current con- sumption	IHFCLKOUT	C _{HFCLKOUT} ≤ 10 pF, XOUTBIA- SANA = 3	_	3.1	_	mA
		10 pF < C _{HFCLKOUT} ≤ 20 pF, XOUTBIASANA = 5		3.9	_	mA
		20 pF < C _{HFCLKOUT} ≤ 30 pF, XOUTBIASANA = 15		6.3	_	mA
Frequency shift of HFXTAL when HFCLKOUT is active	FS _{HFCLKOUT}	Assuming crystal pullability of 13 ppm/pF	-1.5	_	4.5	ppm
HFCLKOUT shorting output resistance	RS _{HFCLKOUT}	When output is disabled		137	_	Ω
Total harmonic distortion,	THD _{HFCLKOUT}	XOUTCFANA = 0		8.53	_	%
XOUTBIASANA = 5, C _{HFCLKOUT} = 20 pF		XOUTCFANA = 1		10.05	_	%
		XOUTCFANA = 2		11.98	_	%
		XOUTCFANA = 3	_	14.39	_	%

Table 4.35. High Frequency Crystal Oscillator

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Note:						

- 1. All sub-GHz RF measurements made using a 39 MHz crystal. Other crystal frequencies supported, but RF performance may vary.
- 2. The crystal should have a maximum ESR less than or equal to this maximum rating.
- 3. Total load capacitance as seen by the crystal.
- 4. It is recommended to use a crystal with a 10 pF load capacitance rating. Only crystals with a 10 pF load cap rating have been characterized for RF use.
- 5. Startup time does not include time implemented by programmable TIMEOUTSTEADY delay.
- 6. The tuning step size is the effective step size when incrementing both of the tuning capacitors by one count. The step size for the each of the individual tuning capacitors is twice this value.

4.10.2 Low Frequency Crystal Oscillator

Table 4.36. Low Frequency Crystal Oscillator

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Crystal Frequency	F _{LFXO}		—	32.768	_	kHz
Supported Crystal equivalent	ESR _{LFXO}	GAIN = 0	_	_	80	kΩ
series resistance (ESR)		GAIN = 1 to 3	_	_	100	kΩ
Supported range of crystal	C _{L_LFXO}	GAIN = 0	4	_	6	pF
load capacitance ¹		GAIN = 1	6	_	10	pF
		GAIN = 2 (see note ²)	10	—	12.5	pF
		GAIN = 3 (see note ²)	12.5	_	18	pF
Current consumption	I _{CL12p5}	ESR = 70 kΩ, C _L = 12.5 pF, GAIN ³ = 2, AGC ⁴ = 1	_	295	_	nA
Startup Time	T _{STARTUP}	ESR = 70 kΩ, C _L = 7 pF, GAIN ³ = 1, AGC ⁴ = 1	—	49	_	ms
On-chip tuning cap step size	SS _{LFXO}		_	0.26	_	pF
On-chip tuning capacitor val- ue at minimum setting ⁵	C _{LFXO_MIN}	CAPTUNE = 0	_	7	_	pF
On-chip tuning capacitor val- ue at maximum setting ⁵	C _{LFXO_MAX}	CAPTUNE = 0x4F	_	27.7	_	pF

Note:

1. Total load capacitance seen by the crystal

2. Crystals with a load capacitance of greater than 12 pF require external load capacitors.

3. In LFXO_CAL Register

4. In LFXO_CFG Register

5. The effective load capacitance seen by the crystal will be C_{LFXO}/2. This is because each XTAL pin has a tuning cap and the two caps will be seen in series by the crystal

4.10.3 High Frequency RC Oscillator (HFRCO)

Unless otherwise indicated, typical conditions are: AVDD = DVDD = RFVDD = PAVDD = VREGVDD = IOVDD0-2 = 3.6 V. DC-DC not used. $T_A = 25$ °C. Minimum and maximum values in this table represent the worst conditions across process variation, operating supply voltage range, and operating temperature range.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Frequency Accuracy	F _{HFRCO_ACC}	For all production calibrated fre- quencies	-3	_	3	%
Current consumption on all	I _{HFRCO}	F _{HFRCO} = 4 MHz	—	43	_	μA
supplies ^{1 2}		F _{HFRCO} = 5 MHz ³	—	40	_	μA
		F _{HFRCO} = 7 MHz	_	75		μA
		F _{HFRCO} = 10 MHz ³	—	77	_	μA
		F _{HFRCO} = 13 MHz	—	94	_	μA
		F _{HFRCO} = 16 MHz	—	103	_	μA
		F _{HFRCO} = 19 MHz	_	107		μA
		F _{HFRCO} = 20 MHz ³	_	115		μA
		F _{HFRCO} = 26 MHz	_	132	_	μA
		F _{HFRCO} = 32 MHz	—	155		μA
		F _{HFRCO} = 38 MHz ⁴	_	187		μA
		F _{HFRCO} = 40 MHz ³	—	185	_	μA
		F _{HFRCO} = 48 MHz ⁴		224		μA
		F _{HFRCO} = 56 MHz ⁴	_	246		μA
		F _{HFRCO} = 64 MHz ⁴	_	286		μΑ
		F _{HFRCO} = 80 MHz ⁴	_	303		μA
Clock Out current for HFRCODPLL ^{2 5}	I _{CLKOUT_HFRCOD}	FORCEEN bit of HFRCO0_CTRL = 1	_	2.5		µA/MHz
Clock Out current for HFRCOEM23 ^{2 5}	I _{CLKOUT_HFRCOE} M23	FORCEEN bit of HFRCOEM23_CTRL = 1		1.0	_	µA/MHz
Startup Time ⁶	T _{STARTUP}	FREQRANGE = 0 to 7	—	0.968		μs
		FREQRANGE = 8 to 15		0.6	_	μs

Table 4.37. High Frequency RC Oscillator (HFRCO)

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Band Frequency Limits ⁷	f _{HFRCO_BAND}	FREQRANGE = 0	3.71		5.24	MHz
		FREQRANGE = 1	4.39		6.26	MHz
		FREQRANGE = 2	5.25		7.55	MHz
		FREQRANGE = 3	6.22		9.01	MHz
		FREQRANGE = 4	7.88		11.6	MHz
		FREQRANGE = 5	9.90		14.6	MHz
		FREQRANGE = 6	11.5		17.0	MHz
		FREQRANGE = 7	14.1		20.9	MHz
		FREQRANGE = 8	16.4		24.7	MHz
		FREQRANGE = 9	19.8		30.4	MHz
		FREQRANGE = 10	22.7		34.9	MHz
		FREQRANGE = 11	28.6		44.4	MHz
		FREQRANGE = 12	33.0		51.0	MHz
		FREQRANGE = 13	42.2		64.6	MHz
		FREQRANGE = 14	48.8	_	74.8	MHz
		FREQRANGE = 15	57.6		87.4	MHz

Note:

1. Does not include additional clock tree current. See specifications for additional current when selected as a clock source for a particular clock multiplexer.

2. When HFRCO is activated the FSRCO is also activated. This prevents direct measurement of only the HFRCO current. The specified current for HFRCO does not include the FSRCO current which is typically 41 μA.

3. This frequency is calibrated for the HFRCOEM23 only.

4. This frequency is calibrated for the HFRCODPLL (HFRCO0) only.

5. When the HFRCO is enabled for characterization using the FORCEEN bit, the total current will be the HFRCO core current plus the specified CLKOUT current. When the HFRCO is enabled on demand, the clock current may be different.

6. Hardware delay ensures settling to within ± 0.5%. Hardware also enforces this delay on a band change.

7. The frequency band limits represent the lowest and highest frequency which each band can achieve over the operating range.

4.10.4 Fast Start_Up RC Oscillator (FSRCO)

Table 4.38. Fast Start_Up RC Oscillator (FSRCO)

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
FSRCO frequency	F _{FSRCO}		17.2	20	21.2	MHz

4.10.5 Low Frequency RC Oscillator (LFRCO)

Table 4.39. Low Frequency RC Oscillator (LFRCO)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Nominal oscillation frequen- cy	F _{LFRCO}		_	32.768		kHz
Frequency accuracy	F _{LFRCO_ACC}		-3	_	3	%
Frequency calibration step	F _{TRIM_STEP}	Typical trim step at mid-scale	_	0.33	—	%
Startup time	t _{STARTUP}		—	182	_	μs
Current consumption	I _{LFRCO}		—	191	—	nA

4.10.6 Ultra Low Frequency RC Oscillator

Table 4.40. Ultra Low Frequency RC Oscillator

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Oscillation Frequency	F _{ULFRCO}		0.944	1.0	1.095	kHz

4.11 GPIO Pins (3V GPIO pins)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Leakage current	I _{LEAK_IO}	MODEx = DISABLED, IOVDD = 1.71 V	—	1.9	—	nA
		MODEx = DISABLED, IOVDD = 3.6 V	—	2.5	—	nA
		MODEx = DISABLED, IOVDD = $3.8 \text{ V}, \text{ T}_{\text{A}} = 125 \text{ °C}, \text{ Pins PA00}, \text{PB00-PB01}, \text{PC09-PC10}, \text{ and PD06-PD07}$		_	250	nA
		MODEx = DISABLED, IOVDD = $3.8 \text{ V}, \text{ T}_{\text{A}} = 125 \text{ °C}, \text{ all other GPIO}$	—	—	200	nA
Input low voltage ¹	V _{IL}	Any GPIO pin	—	—	0.3 * IOVDD	V
		RESETn	—	—	0.3 * DVDD	V
Input high voltage ¹	V _{IH}	Any GPIO pin	0.7 * IOVDD	—	—	V
		RESETn	0.7 * DVDD	—	—	V
Hysteresis of input voltage	V _{HYS}	Any GPIO pin	0.05 * IOVDD		—	V
		RESETn	0.05 * DVDD	—	—	V
Output high voltage	V _{OH}	Sourcing 20mA, IOVDD = 3.6 V	0.8 * IOVDD		—	V
		Sourcing 8mA, IOVDD = 1.71 V	0.6 * IOVDD	—	—	V
Output low voltage	V _{OL}	Sinking 20mA, IOVDD = 3.6 V	—	—	0.2 * IOVDD	V
		Sinking 8mA, IOVDD = 1.71 V	—	—	0.4 * IOVDD	V
GPIO rise time	T _{GPIO_RISE}	IOVDD = 3.6 V, C _{load} = 50pF, SLEWRATE = 4, 10% to 90%	—	8.4	_	ns
		IOVDD = 1.7 V, C _{load} = 50pF, SLEWRATE = 4, 10% to 90%	—	13	—	ns
GPIO fall time	T _{GPIO_FALL}	IOVDD = 3.6 V, C _{load} = 50pF, SLEWRATE = 4, 90% to 10%	—	7.1	—	ns
		IOVDD = 1.7 V, C _{load} = 50pF, SLEWRATE = 4, 90% to 10%	—	11.9	-	ns
Pull up/down resistance ²	R _{PULL}	Any GPIO pin. Pull-up to IOVDD: MODEn = DISABLE DOUT=1. Pull-down to VSS: MODEn = WIREDORPULLDOWN DOUT = 0.	35	42	55	kΩ
		RESETn pin. Pull-up to DVDD	35	42	55	kΩ
Maximum filtered glitch width	T _{GF}	MODE = INPUT, DOUT = 1		27	_	ns

Table 4.41. GPIO Pins (3V GPIO pins)

EFR32FG25 Gecko Wireless SoC Family Data Sheet Electrical Specifications

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
RESETn low time to ensure pin reset	T _{RESET}		100	_	_	ns
Note:						

1. GPIO input thresholds are proportional to the IOVDD pin. RESETn input thresholds are proportional to DVDD.

2. GPIO pull-ups connect to IOVDD supply, pull-downs connect to VSS. RESETn pull-up connects to DVDD.

4.12 Analog to Digital Converter (IADC)

Specified at 1 Msps, ADCCLK = 10 MHz, OSR=2, unless otherwise indicated.

Table 4.42.	Analog to	Digital Converte	er (IADC)
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Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Main analog supply	V _{AVDD}	Normal mode	1.71	_	3.8	V
Maximum Input Range ¹	V _{IN_MAX}	Maximum allowable input voltage	0	_	AVDD	V
Full-Scale Voltage	V _{FS}	Voltage required for Full-Scale measurement	_	V _{REF} / Gain	_	V
Input Measurement Range	V _{IN}	Differential Mode - Plus and Mi- nus inputs	-V _{FS}	-	+V _{FS}	V
		Single Ended Mode - One input tied to ground	0	-	V_{FS}	V
Input Sampling Capacitance	Cs	Analog Gain = 1x	_	1.8		pF
		Analog Gain = 2x		3.6	_	pF
		Analog Gain = 3x	_	5.4	_	pF
		Analog Gain = 4x	—	7.2	—	pF pF MHz MHz
		Analog Gain = 0.5x	_	0.9	_	pF
ADC clock frequency	f _{ADC_CLK}	Normal mode, Gain = 1x or 0.5x	—	_	10	MHz
		Normal mode, Gain = 2x	_	_	5	MHz
		Normal mode, Gain = 3x or 4x	—	_	2.5	MHz
Input sampling frequency	f _S	Normal Mode	—	f _{ADC_CLK} /4	_	MHz
Throughput rate	f _{SAMPLE}	Normal mode, f _{ADC_CLK} = 10 MHz, OSR = 2	_	-	1	Msps
		Normal mode, f _{ADC_CLK} = 10 MHz, OSR = 32	_	-	76.9	ksps
Current from all supplies, Continuous operation	I _{ADC_CONT}	Normal Mode, 1 Msps, OSR = 2, f _{ADC_CLK} = 10 MHz	—	305	385	μA
Current in Standby mode. ADC is not functional but can wake up in 1us.	I _{STBY}	Normal mode	—	14.8	—	μA
ADC Startup Time	t _{startup}	From power down state	_	5	_	μs
		From standby state	_	1	_	μs
Normal Mode ADC Resolu-	Resolution	OSR = 2	_	12	_	bits
tion ²		OSR = 32	_	16		bits
Differential Nonlinearity	DNL	Normal mode. Differential Input. OSR = 2 (No missing codes)	-1	+/- 0.25	+1.5	LSB12
Integral Nonlinearity	INL	Normal mode. Differential Input, OSR = 2	-2.5	+/- 0.65	+2.5	LSB12

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Effective number of bits ³	ENOB	Normal mode. Differential Input. Gain = 1x, OSR = 2, f _{IN} = 10 kHz, Internal VREF = 1.21 V.	10.7	11.7	_	bits
		Normal Mode, Differential Input. Gain = 1x, OSR = 32, f _{IN} = 2.5 kHz, Internal VREF = 1.21 V.	_	13.5	_	bits
Signal to Noise + Distortion Ratio Normal Mode ³	SNDR	Normal mode. Differential Input. Gain = 1x, OSR = 2, f _{IN} = 10 kHz, Internal VREF = 1.21 V	66	72.3	_	dB
		Normal mode. Differential Input. Gain = 4x, OSR = 2, f _{IN} = 10 kHz, Internal VREF = 1.21 V	_	68.8	_	dB
		Differential Input. Gain = 1x, OSR = 64, f _{IN} = 1.25 kHz, Internal VREF = 1.21 V	_	83.9	_	dB
Total Harmonic Distortion	THD	Normal mode, Differential Input. Gain = 1x, OSR = 2, f _{IN} = 10 kHz, Internal VREF = 1.21 V	_	-80.8	-70	dB
Spurious-Free Dynamic Range	SFDR	Normal mode, Differential Input. Gain = 1x, OSR = 2, f _{IN} = 10 kHz, Internal VREF = 1.21 V	72	86.5	_	dB
Common Mode Rejection Ratio	CMRR	Normal mode. DC to 100 Hz	—	87.0	_	dB
		Normal mode. AC high frequency.	_	68.6	_	dB
Power Supply Rejection Ra-	PSRR	Normal mode. DC to 100 Hz	_	80.4	_	dB
tio		Normal mode. AC high frequency, using internal VBGR	_	33.4	_	dB
		Normal mode. AC high frequency, using VREF pad	_	65.2	_	dB
External reference voltage range ¹	V _{EVREF}		1.0	-	AVDD	V
Offset Error, Normal mode	OFFSET	GAIN = 1 and 0.5, Differential In- put	-4.5	0.27	4.5	LSB12
		GAIN = 2, Differential Input	-5.5	0.27	5.5	LSB12
		GAIN = 3, Differential Input	-5.5	0.25	5.5	LSB12
		GAIN = 4, Differential Input	-5.5	0.29	5.5	LSB12
Gain Error, Normal mode	GE	GAIN = 1 and 0.5, using external VREF, direct mode, f _{ADC_CLK} = 10 MHz	-0.3	0.069	0.3	%
		GAIN = 2, using external VREF, direct mode, f _{ADC_CLK} = 5 MHz	-0.4	0.151	0.4	%
		GAIN = 3, using external VREF, direct mode, f _{ADC_CLK} = 2.5 MHz	-0.7	0.186	0.7	%
		GAIN = 4, using external VREF, direct mode, f _{ADC_CLK} = 2.5 MHz	-1.1	0.227	1.1	%
		Internal VREF ⁴ , all GAIN settings	-1.5	0.023	1.5	%
Internal Reference voltage	VIVREF			1.21	_	V

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Note:			Ľ			
2. ADC output resolution bits at OSR = 2, 1	ution depends on the O 3 bits at OSR = 4, 14 b	pins, the maximum pin volta SR and digital averaging setti its at OSR = 8, 15 bits at OSI utput resolution. See the prod	ngs. With no digital av R = 16, 16 bits at OSR	eraging, ADC = 32 and 17 b	output resolut bits at OSR = 6	tion is 12
3. The relationship b	etween ENOB and SN	DR is specified according to t	ne equation: ENOB =	(SNDR - 1.76)	/ 6.02.	
4. Includes error from	m internal VREF drift.					

4.13 Analog Comparator (ACMP)

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
ACMP Supply current	I _{ACMP}	BIAS = 2 ¹ , HYST = DISABLED	—	675	_	nA
		BIAS = 3 ¹ , HYST = DISABLED		2.5		nA μA μA μA μA μA μA μA μA μA μ
		BIAS = 4, HYST = DISABLED		5.4		μA
		BIAS = 5, HYST = DISABLED	_	10.7	_	μΑ
		BIAS = 6, HYST = DISABLED		26.9		μΑ
		BIAS = 7, HYST = DISABLED		49.9	85	μΑ
ACMP Supply current with	IACMP_WHYS	BIAS = 2 ¹ , HYST = SYM30MV		945	_	nA
Hysteresis		BIAS = 3 ¹ , HYST = SYM30MV		3.4	_	μA
		BIAS = 4, HYST = SYM30MV		7.3		μA
		BIAS = 5, HYST = SYM30MV		15.2		μA
		BIAS = 6, HYST = SYM30MV		38.5		μA
		BIAS = 7, HYST = SYM30MV		71.3		μA
Current consumption from	I _{VREFDIV}	NEGSEL = VREFDIVAVDD		3.9		μA
VREFDIV in continuous mode		NEGSEL = VREFDIV1V25		4.4	_	μA
		NEGSEL = VREFDIV2V5		7.2		μA
Current consumption from	IVREFDIV_SH	NEGSEL = VREFDIV2V5LP		76	_	nA
VREFDIV in sample/hold mode		NEGSEL = VREFDIV1V25LP		72	_	nA
		NEGSEL = VREFDIVAVDDLP		72	_	nA
Current consumption from VSENSEDIV in continuous mode	IVSENSEDIV	NEGSEL = VSENSE01DIV4	_	2.0	_	μA
Current consumption from VSENSEDIV in sample/hold mode	I _{VSENSEDIV_SH}	NEGSEL = VSENSE01DIV4LP		56	_	nA
Hysteresis (BIAS = 2)	V _{HYST}	HYST = SYM10MV ²		28	_	mV
		HYST = SYM20MV ²		52	_	mV
		HYST = SYM30MV ²		74		mV
Reference Voltage	V _{ACMPREF}	Internal 1.25 V Reference	1.18	1.25	1.30	V
		Internal 2.5 V Reference	2.36	2.5	2.61	V
Input offset voltage	V _{OFFSET}	BIAS = 2, VCM = 0.15 to AVDD - 0.15 V	-25	-	25	mV
		BIAS = 3, VCM = 0.15 to AVDD - 0.15 V	-25	_	25	mV
		BIAS = 4, VCM = 0.15 to AVDD - 0.15 V	-25	-	25	mV
		BIAS = 7, VCM = 0.15 to AVDD - 0.15 V	-25	-	25	mV

Table 4.43. Analog Comparator (ACMP)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Input Range	V _{IN}	Input Voltage Range	0	—	AVDD	V
Comparator delay with 100	T _{DELAY}	BIAS = 2	_	1.3	_	μs
mV overdrive		BIAS = 3		0.55	_	μs
		BIAS = 4		199	_	ns
		BIAS = 5		110	_	ns
		BIAS = 6	—	59	—	V μs ns ns ns ns kΩ kΩ
		BIAS = 7	—	41	_	
Capacitive Sense Oscillator	R _{CSRESSEL}	CSRESSEL = 0	—	15	_	kΩ
Resistance		CSRESSEL = 1	—	24	_	kΩ
		CSRESSEL = 2		42	_	kΩ
		CSRESSEL = 3	—	61	_	kΩ
		CSRESSEL = 4		78	_	kΩ
		CSRESSEL = 5	_	96	_	kΩ
		CSRESSEL = 6		115	_	kΩ

Note:

1. When using the 1.25 V or 2.5 V VREF in continuous mode (VREFDIV1V25 or VREFDIV2V5) and BIAS < 4, an additional 1 µA of supply current is required.

 $2. V_{CM}$ = 1.25 V

4.14 Digital to Analog Converter (VDAC)

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Output voltage	V _{DACOUT}		0	—	VREF	V
Output Current	IDACOUT		-10	_	+10	mA
DAC clock frequency	f _{DAC}		_	_	1	MHz
Sample rate	SR _{DAC}	$f_{DAC} = f_{DAC(max)}$	_	_	500	ksps
Resolution	NRESOLUTION		_	12	_	bits
Load Capacitance ¹	C _{LOAD}	High Power and Lower Power Modes	_	_	50	pF
		High Capacitance Load Mode	25	_	_	nF
Load Resistance	R _{LOAD}		5	_	_	kΩ
Current consumption, Dy-	I _{DAC_1_500}	High Power Mode	_	345	_	μA
namic, 500 ksps, 1 channel active ²		Low Power Mode	—	245	_	μA
Current consumption, Dy- namic, 500 ksps, 2 channels active ²	I _{DAC_2_500}	High Power Mode	_	531	_	μA
		Low Power Mode	_	335	_	μA
Current consumption, Static,	I _{DAC_1_STAT}	High Power Mode	_	134		μA
1 channel active ³		Low Power Mode	_	30	_	μA
		High Capacitance Mode	_	42	_	μA
Current consumption, Static,	IDAC_2_STAT	High Power Mode	_	261	400	μA
2 channels active ³		Low Power Mode	_	53	90	μA
		High Capacitance Mode	_	77	_	μA
Startup time	t _{DACSTARTUP}	Enable to 90% full scale output, settling to 10 LSB	_	4.2	4.7	μs
Settling time	t _{DACSETTLE}	High Power Mode, 25% to 75% of full scale, settling to 10 LSB	_	1.1	1.6	μs
		Low Power Mode, 25% to 75% of full scale, settling to 1%	—	2.7	_	μs
Output impedance	R _{OUT}	Main Output, High Power Mode	_	2.4	_	Ω
		Main Output, Low Power Mode	_	3.3	—	Ω
Power supply rejection ratio ⁴	PSRR	Vout = 50% full scale, DC output	—	84.4	-	dB
Signal to noise and distortion ratio	SNDR _{DAC}	High Power mode, 500 ksps, in- ternal 2.5 V reference, 1 kHz sine wave input, BW limited to 250 kHz	64.8	66.8	_	dB
		High Power mode, 500 ksps, in- ternal 2.5 V reference, 1 kHz sine wave input, BW limited to 22 kHz	68.2	70.7	_	dB
Total Harmonic Distortion	THD	High Power Mode, internal 2.5 V reference, 1 kHz sine wave input	_	-71.3	-67.2	dB

Table 4.44. Digital to Analog Converter (VDAC)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Integral Non-Linearity	INL _{DAC}	High Power Mode, Across full temperature range	-5	_	5	LSB
Differential Non-Linearity ⁵	DNL _{DAC}	High Power Mode, Across full temperature range	-1	_	1.3	LSB
Offset error ⁶	V _{OFFSET}	High Power mode	-15	_	15	mV
		Low Power Mode	-25	_	25	mV
		High Capacitance Load mode	-40	_	40	mV
Gain error ⁶	V _{GAIN}	1.25 V internal reference	-1.5	_	1.5	%
		2.5 V internal reference	-2	_	2	%
		External Reference	-0.6	_	0.6	%
External Reference Voltage ⁷	V _{EXTREF}		1.1	-	V_AVDD	V

Note:

1. Main outputs only.

2. Dynamic current specifications are for VDAC circuitry operating at max clock frequency with the output updated at the specified sampling rate using DMA transfers. Output is a 1 kHz sine wave from 10% to 90% full scale. Specified current does not include current required to drive the external load. Measurement includes all current from AVDD and DVDD supplies.

3. Static current specifications are for VDAC circuitry operating after a one-time update to a static output at 50% full scale, with the VDAC APB clock disabled. Specified current does not include current required to drive the external load. Measurement includes all current from AVDD and DVDD supplies.

- 4. PSRR calculated as 20 * log₁₀(Δ VDD / Δ V_{OUT}).
- 5. Entire range is monotonic and has no missing codes.
- 6. Gain is calculated by measuring the slope from 10% to 90% of full scale. Offset is calculated by comparing actual VDAC output at 10% of full scale to ideal VDAC output at 10% of full scale with the measured gain.
- 7. External reference voltage on PA00 when used for VREFP

4.15 Temperature Sensor

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Temperature sensor range ¹	T _{RANGE}		-40	—	125	°C
Temperature sensor resolu- tion	T _{RESOLUTION}		_	0.25	_	°C
Measurement noise (RMS)	T _{NOISE}	Single measurement	_	0.6	_	°C
		16-sample average (TEMPAVG- NUM = 0)	_	0.17	-	2° 2° 2° 2° 2°
		64-sample average (TEMPAVG- NUM = 1)	_	0.12	_	°C
Temperature offset	T _{OFF}	Mean error of uncorrected output across full temperature range	_	0.84	_	°C
Temperature sensor accura- cy ^{2 3}	T _{ACC}	Direct output accuracy after mean error (T _{OFF}) removed	_	+/-3	_	°C
		After linearization in software, no calibration	_	+/-2	-	°C
		After linearization in software, with single-temperature calibration at $25 \ ^{\circ}C^{4}$	_	+/-1.5	-	°C
Measurement interval	t _{MEAS}		_	250	_	ms

Table 4.45. Temperature Sensor

Note:

1. The sensor reports absolute die temperature in Kelvin (K). All specifications are in °C to match the units of the specified product temperature range.

2. Error is measured as the deviation of the mean temperature reading from the expected die temperature. Accuracy numbers represent statistical minimum and maximum using ± 4 standard deviations of measured error.

3. The raw output of the temperature sensor is a predictable curve. It can be linearized with a polynomial function for additional accuracy.

4. Assuming calibration accuracy of ± 0.25 °C.

4.16 Brown Out Detectors

4.16.1 DVDD BOD

BOD thresholds on DVDD in EM0 and EM1 only, unless otherwise noted. Typical conditions are at $T_A = 25$ °C. Minimum and maximum values in this table represent the worst conditions across process variation, operating supply voltage range, and operating temperature range.

Table 4.46. DVDD BOD

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
BOD threshold	V _{DVDD_BOD}	Supply Rising	-	1.68	1.71	V
		Supply Falling	1.62	1.65	—	V
BOD response time	tdvdd_bod_de- Lay	Supply dropping at 100 mV/µs slew rate ¹	-	0.95	_	μs
BOD hysteresis	V _{DVDD_BOD_HYS} T		_	22	_	mV

Note:

1. If the supply slew rate exceeds the specified slew rate, the BOD may trip later than expected (at a threshold below the minimum specified threshold), or the BOD may not trip at all (e.g., if the supply ramps down and then back up at a very fast rate)

4.16.2 LE DVDD BOD

BOD thresholds on DVDD pin for low energy modes EM2 to EM4, unless otherwise noted.

Table 4.47. LE DVDD BOD

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
BOD threshold	V _{DVDD_LE_BOD}	Supply Falling	1.5	_	1.71	V
BOD response time	t _{DVDD_LE_BOD_D} ELAY	Supply dropping at 2 mV/µs slew rate ¹	—	55	_	μs
BOD hysteresis	V _{DVDD_LE_BOD_} HYST		_	20		mV

Note:

1. If the supply slew rate exceeds the specified slew rate, the BOD may trip later than expected (at a threshold below the minimum specified threshold), or the BOD may not trip at all (e.g., if the supply ramps down and then back up at a very fast rate)

4.16.3 AVDD and IOVDD BODs

BOD thresholds for AVDD BOD and IOVDD BOD. Available in all energy modes.

Table 4.48. AVDD and IOVDD BODs

Symbol	Test Condition	Min	Тур	Max	Unit
V _{BOD}	Supply falling	1.45	_	1.71	V
tBOD_DELAY	Supply dropping at 2 mV/µs slew rate ¹		55	_	μs
V _{BOD_HYST}			20		mV
	V _{BOD}	VBOD Supply falling tBOD_DELAY Supply dropping at 2 mV/µs slew rate ¹	VBOD Supply falling 1.45 tBOD_DELAY Supply dropping at 2 mV/µs slew rate ¹ —	VBOD Supply falling 1.45 tBOD_DELAY Supply dropping at 2 mV/µs slew rate ¹ —	VBOD Supply falling 1.45 — 1.71 tBOD_DELAY Supply dropping at 2 mV/µs slew rate ¹ — 55 —

Note:

1. If the supply slew rate exceeds the specified slew rate, the BOD may trip later than expected (at a threshold below the minimum specified threshold), or the BOD may not trip at all (e.g., if the supply ramps down and then back up at a very fast rate)

4.17 Pulse Counter

Table 4.49. Pulse Counter

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Input frequency	F _{IN}	Asynchronous Single and Quad- rature Modes	_	_	1.0	MHz
		Sampled Modes with Debounce filter set to 0.	_	_	8	kHz
Setup time in asynchronous external clock mode	t _{SU_S1N_S0N}	S1N (data) to S0N (clock)	54	_	_	ns
Hold time in asynchronous external clock mode	thd_son_s1n	S0N (clock) to S1N (data)	47	_		ns

4.18 EUSART SPI Main Timing



Figure 4.1. SPI Main Timing

4.18.1 EUSART SPI Main Timing, Voltage Scaling = VSCALE2

Timing specifications are for all SPI signals routed to the same DBUS (DBUSAB or DBUSCD) on consecutive pins. All GPIO set to slew rate = 6.

Table 4.50.	. EUSART SPI Main	Timing, Volta	ge Scaling = VSCALE2
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Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
SCLK period ^{1 2 3}	t _{SCLK}		tclk	_	_	ns
CS to MOSI ^{1 2}	t _{cs_mo}		-11		7	ns
SCLK to MOSI ^{1 2}	t _{SCLK_MO}		-3	_	8	ns
MISO setup time ^{1 2}	t _{su_мi}		6	_	—	ns
MISO hold time ^{1 2}	t _{H_MI}		-21		_	ns

Note:

1. Applies for both CLKPHA = 0 and CLKPHA = 1.

2. Measurement done with 15 pF output loading at 10% and 90% of $V_{\text{DD}}.$

3. t_{CLK} is one period of the selected peripheral clock: EM01GRPCCLK for EUSART1/2, EUSART0CLK for EUSART0.





4.19.1 EUSART SPI Secondary Timing, Voltage Scaling = VSCALE2

Timing specifications are for all SPI signals routed to the same DBUS (DBUSAB or DBUSCD) on consecutive pins. All GPIO set to slew rate = 6.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
SCLK high time ^{1 2}	t _{SCLK_HI}		50	_	_	ns
SCLK low time ^{1 2}	t _{SCLK_LO}		50	_	_	ns
CS active to MISO ^{1 2}	t _{CS_ACT_MI}		5	_	55	ns
CS disable to MISO ^{1 2}	t _{CS_DIS_MI}		5	_	41	ns
MOSI setup time ^{1 2}	t _{su_мо}		5	_	_	ns
MOSI hold time ^{1 2}	t _{H_MO}		7	_	_	ns
SCLK to MISO ^{1 2}	t _{SCLK_MI}	IOVDD = 1.8 V	9	_	40	ns
		IOVDD = 3.3 V	9		30	ns
Note:						

1. Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0).

2. Measurement done with 15 pF output loading at 10% and 90% of V_{DD} (figure shows 50% of V_{DD}).

4.19.2 EUSART SPI Secondary Timing, Voltage Scaling = VSCALE0

Timing specifications at VSCALE0 apply to EUSART0 only, routed to DBUSAB on consecutive pins. All GPIO set to slew rate = 6.

Table 4.52. EUSART SPI Secondary Timing, Voltage Scaling = VSCALE0

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
SCLK high time ^{1 2}	t _{SCLK_HI}		100	_	_	ns
SCLK low time ^{1 2}	t _{SCLK_LO}		100	_	_	ns
CS active to MISO ^{1 2}	t _{CS_ACT_MI}		8	_	110	ns
CS disable to MISO ^{1 2}	t _{CS_DIS_MI}		8	_	76	ns
MOSI setup time ^{1 2}	t _{SU_MO}		10	_	_	ns
MOSI hold time ^{1 2}	t _{H_MO}		33	_	_	ns
SCLK to MISO ^{1 2}	t _{SCLK_MI}	IOVDD = 1.8 V	12	_	93	ns
		IOVDD = 3.3 V	12	_	84	ns

Note:

1. Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0).

2. Measurement done with 15 pF output loading at 10% and 90% of V_{DD} (figure shows 50% of V_{DD}).

4.20 I2C Electrical Specifications

4.20.1 I2C Standard-mode (Sm)

CLHR set to 0 in the I2Cn_CTRL register.

Table 4.53. I2C Standard-mode (Sm)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
SCL clock frequency ¹	f _{SCL}		0	_	100	kHz
SCL clock low time	t _{LOW}		4.7		_	μs
SCL clock high time	tнigн		4	_	_	μs
SDA set-up time	t _{SU_DAT}		250	_	_	ns
SDA hold time	t _{HD_DAT}		0			ns
Repeated START condition set-up time	t _{SU_STA}		4.7	_	_	μs
Repeated START condition hold time	t _{HD_STA}		4.0	_	_	μs
STOP condition set-up time	t _{SU_STO}		4.0	_	_	μs
Bus free time between a STOP and START condition	t _{BUF}		4.7		_	μs

Note:

1. The maximum SCL clock frequency listed is assuming that an arbitrary clock frequency is available. The maximum attainable SCL clock frequency may be slightly less using the HFXO or HFRCO due to the limited frequencies available. The CLKDIV should be set to a value that keeps the SCL clock frequency below the max value listed.

4.20.2 I2C Fast-mode (Fm)

CLHR set to 1 in the I2Cn_CTRL register.

Table 4.54.	I2C Fast-mode	(Fm)
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Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
SCL clock frequency ¹	f _{SCL}		0	_	400	kHz
SCL clock low time	t _{LOW}		1.3	_	_	μs
SCL clock high time	tніgн		0.6	_	_	μs
SDA set-up time	t _{SU_DAT}		100	_	_	ns
SDA hold time	t _{HD_DAT}		0	_	_	ns
Repeated START condition set-up time	t _{SU_STA}		0.6	_	_	μs
Repeated START condition hold time	t _{HD_STA}		0.6	_	_	μs
STOP condition set-up time	t _{SU_STO}		0.6	_	_	μs
Bus free time between a STOP and START condition	t _{BUF}		1.3	_	_	μs

Note:

1. The maximum SCL clock frequency listed is assuming that an arbitrary clock frequency is available. The maximum attainable SCL clock frequency may be slightly less using the HFXO or HFRCO due to the limited frequencies available. The CLKDIV should be set to a value that keeps the SCL clock frequency below the max value listed.

4.20.3 I2C Fast-mode Plus (Fm+)

CLHR set to 1 in the I2Cn_CTRL register.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
SCL clock frequency ¹	f _{SCL}		0	_	1000	kHz
SCL clock low time	t _{LOW}		0.5	_	_	μs
SCL clock high time	t _{HIGH}		0.26	_	_	μs
SDA set-up time	t _{SU_DAT}		50	_	_	ns
SDA hold time	t _{HD_DAT}		0	_	_	ns
Repeated START condition set-up time	t _{SU_STA}		0.26			μs
Repeated START condition hold time	t _{HD_STA}		0.26			μs
STOP condition set-up time	t _{SU_STO}		0.26	_	_	μs
Bus free time between a STOP and START condition	t _{BUF}		0.5	_	_	μs

Note:

1. The maximum SCL clock frequency listed is assuming that an arbitrary clock frequency is available. The maximum attainable SCL clock frequency may be slightly less using the HFXO or HFRCO due to the limited frequencies available. The CLKDIV should be set to a value that keeps the SCL clock frequency below the max value listed.

4.21 Boot Timing

Secure boot impacts the recovery time from all sources of device reset. In addition to the root code authentication process, which cannot be disabled or bypassed, the root code can authenticate a bootloader, and the bootloader can authenticate the application. In projects that include only an application and no bootloader, the root code can authenticate the application directly. The duration of each authentication operation depends on two factors: the computation of the associated image hash, which is proportional to the size of the image, and the verification of the image signature, which is independent of image size.

The duration for the root code to authenticate the bootloader will depend on the SE firmware version as well as on the size of the bootloader.

The duration for the bootloader to authenticate the application can depend on the size of the application.

The configurations below assume that the associated bootloader and application code images do not contain a bootloader certificate or an application certificate. Authenticating a bootloader certificate or an application certificate will extend the boot time by an additional 6 to 7 ms.

The table below provides the durations from the termination of reset until the completion of the secure boot process (start of main() function in the application image) under various conditions.

Conditions:

- SE firmware version: 2.1.7
- Gecko Bootloader size: 24 kB

Timing is expected to be similar for subsequent SE firmware versions. Refer to SE firmware release notes for any significant changes.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Boot time	t _{BOOT}	Secure boot application check dis- abled, no bootloader	_	31.6	_	ms
		Secure boot application check dis- abled, second stage bootloader check enabled, 50 kB application size	_	37.6	_	ms
		Secure boot application check en- abled, second stage bootloader check enabled, 50 kB application size	_	47.9	_	ms
		Secure boot application check en- abled, second stage bootloader check enabled, 150 kB application size	_	49.8	_	ms
		Secure boot application check en- abled, second stage bootloader check enabled, 350 kB application size	_	53.9	-	ms

Table 4.56. Boot Timing

4.22 Crypto Operation Timing for SE Manager API

Values in this table represent timing from SE Manager API call to return. The Cortex-M33 HCLK frequency is 39.0 MHz. The timing specifications below are measured at the SE Manager function call API. Each duration in the table contains some portion that is influenced by SE Manager build compilation and Cortex-M33 operating frequency and some portion that is influenced by the Hardware Secure Engine's firmware version and its operating speed (typically 80 MHz). The contributions of the Cortex-M33 properties to the overall specification timing are most pronounced for the shorter operations such as AES and hash when operating on small payloads. The overhead of command processing at the mailbox interface can also dominate the timing for shorter operations.

Conditions:

- SE firmware version: 2.1.7
- GSDK version: 4.0.0

Timing is expected to be similar for subsequent SE firmware versions. Refer to SE firmware release notes for any significant changes.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
AES-128 timing	t _{AES128}	AES-128 CCM encryption, PT 1 kB	_	560	_	μs
		AES-128 CCM encryption, PT 32 kB	_	1746	_	μs
		AES-128 CTR encryption, PT 1 kB	_	464	_	μs
		AES-128 CTR encryption, PT 32 kB	_	1032	_	μs
		AES-128 GCM encryption, PT 1 kB	_	512	_	μs
		AES-128 GCM encryption, PT 32 kB	_	1073	_	μs
AES-256 timing	t _{AES256}	AES-256 CCM encryption, PT 1 kB	_	573	_	μs
		AES-256 CCM encryption, PT 32 kB	—	2181	—	μs
		AES-256 CTR encryption, PT 1 kB	—	471	_	μs
		AES-256 CTR encryption, PT 32 kB	—	1242	—	μs
		AES-256 GCM encryption, PT 1 kB	_	519	_	μs
		AES-256 GCM encryption, PT 32 kB	_	1289	_	μs
ECC P-256 timing	t _{ECC_P256}	ECC key generation, P-256	_	5.5		ms
		ECC signing, P-256		5.9	_	ms
		ECC verification, P-256	_	6.2	_	ms
ECC P-521 timing ¹	tecc_p521	ECC key generation, P-521	_	30.5		ms
		ECC signing, P-521	_	31.0	_	ms
		ECC verification, P-521	_	36.2		ms
ECC P-25519 timing ²	tecc_p25519	ECC key generation, P-25519	_	4.5	_	ms
		ECC signing, P-25519	_	8.9		ms
		ECC verification, P-25519	_	6.3	—	ms
ECDH compute secret timing	g t _{ecdh}	ECDH compute secret, P-521 ¹	_	30.3	_	ms
		ECDH compute secret, P-25519 ²	_	4.5		ms
		ECDH compute secret, P-256		5.7		ms

Table 4.57. Crypto Operation Timing for SE Manager API

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
ECJPAKE client timing	^t ecjpake_c	ECJPAKE client write round one		21.4	_	ms
		ECJPAKE client read round one	_	11.8	_	ms
		ECJPAKE client write round two	_	15.3	_	ms
		ECJPAKE client read round two	_	6.4		ms
		ECJPAKE client derive secret	_	8.8	_	ms
ECJPAKE server timing	tecjpake_s	ECJPAKE server write round one	_	21.5		ms
		ECJPAKE server read round one	_	11.7	_	ms
		ECJPAKE server write round two	_	15.3	_	ms
		ECJPAKE server read round two	_	6.3		ms
		ECJPAKE server derive secret	_	8.8	_	ms
POLY-1305 timing ¹	t _{POLY1305}	POLY-1305, PT 1 kB	_	508		μs
		POLY-1305, PT 32 kB		1171		μs
SHA-256 timing	t _{SHA256}	SHA-256, PT 1 kB	_	303	_	μs
		SHA-256, PT 32 kB	_	733		μs
SHA-512 timing ¹	t _{SHA512}	SHA-512, PT 1 kB	_	301	_	μs
		SHA-512, PT 32 kB	_	615	_	μs

1. Option is only available on OPNs with Secure Vault High feature set.

2. Option is not available on Secure Vault Mid devices with SE firmware earlier than v2.1.7.

4.23 Crypto Operation Average Current for SE Manager API

Values in this table represent current consumed by security core during the operation, and represent additions to the current consumed by the Cortex-M33 application CPU due to the Hardware Secure Engine CPU and its associated crypto accelerators. The current measurements below represent the average value of the current for the duration of the crypto operation. Instantaneous peak currents may be higher.

Conditions:

- SE firmware version: 2.1.7
- GSDK version: 4.0.0

Current consumption is expected to be similar for subsequent SE firmware versions. Refer to SE firmware release notes for any significant changes.

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
AES-128 current	I _{AES128}	AES-128 CCM encryption, PT 1 kB	_	1.0		mA
		AES-128 CCM encryption, PT 32 kB	_	3.3		mA
		AES-128 CTR encryption, PT 1 kB	_	0.8		mA
		AES-128 CTR encryption, PT 32 kB	_	3.4		mA
		AES-128 GCM encryption, PT 1 kB	_	0.9	_	mA
		AES-128 GCM encryption, PT 32 kB	_	3.4		mA
AES-256 current	I _{AES256}	AES-256 CCM encryption, PT 1 kB	_	1.0		mA
		AES-256 CCM encryption, PT 32 kB	_	3.4		mA
		AES-256 CTR encryption, PT 1 kB	_	0.9		mA
		AES-256 CTR encryption, PT 32 kB	_	3.4		mA
		AES-256 GCM encryption, PT 1 kB	_	0.9		mA
		AES-256 GCM encryption, PT 32 kB	_	3.4	_	mA
ECC P-256 current	I _{ECCP256}	ECC key generation, P-256	_	1.6		mA
		ECC signing, P-256	_	1.6	_	mA
		ECC verification, P-256	_	1.6		mA
ECC P-521 current ¹	I _{ECCP521}	ECC key generation, P-521	_	1.8		mA
		ECC signing, P-521	_	1.8		mA
		ECC verification, P-521	_	1.8		mA
ECC P-25519 current ²	IECCP25519	ECC key generation, P-25519	_	1.6		mA
		ECC signing, P-25519	_	1.6		mA
		ECC verification, P-25519	_	1.6		mA
ECDH compute secret cur-	IECDH	ECDH compute secret, P-521 ¹	_	1.8		mA
rent		ECDH compute secret, P-25519 ²	_	1.5	_	mA
		ECDH compute secret, P-256		1.6	_	mA

Table 4.58. Crypto Operation Average Current for SE Manager API

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Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
ECJPAKE client current	IECJPAKE_C	ECJPAKE client write round one		1.7	_	mA
		ECJPAKE client read round one	_	1.7	_	mA
		ECJPAKE client write round two	_	1.7	_	mA
		ECJPAKE client read round two	_	1.6	_	mA
		ECJPAKE client derive secret	_	1.7	_	mA
ECJPAKE server current	IECJPAKE_S	ECJPAKE server write round one		1.7	_	mA
		ECJPAKE server read round one	_	1.7	_	mA
		ECJPAKE server write round two		1.7	_	mA
		ECJPAKE server read round two	_	1.6	_	mA
		ECJPAKE server derive secret	-	1.7	_	mA
POLY-1305 current ¹	I _{POLY1305}	POLY-1305, PT 1 kB	_	0.7	_	mA
		POLY-1305, PT 32 kB	_	1.7	_	mA
SHA-256 current	I _{SHA256}	SHA-256, PT 1 kB	_	0.8	_	mA
		SHA-256, PT 32 kB	_	2.3	_	mA
SHA-512 current ¹	I _{SHA512}	SHA-512, PT 1 kB		0.7	_	mA
		SHA-512, PT 32 kB		2.0		mA

1. Option is only available on OPNs with Secure Vault High feature set.

2. Option is not available on Secure Vault Mid devices with SE firmware earlier than v2.1.7.

4.24 Typical Performance Curves

Typical performance curves indicate typical characterized performance under the stated conditions.



Figure 4.3. EM0 and EM1 Typical Supply Current vs. Temperature



Figure 4.4. EM2 and EM4 Typical Supply Current vs. Temperature



Figure 4.5. Typical Radio Supply Current and Output Power vs. Temperature

4.24.2 IADC

Typical performance is shown using 10 MHz ADC clock for fastest sampling speed and adjusting oversampling ratio (OSR).



Figure 4.6. Typical ENOB vs. Oversampling Ratio

5. Typical Connection Diagrams

5.1 Power

Typical power supply connections are shown in the following figures.



Figure 5.1. EFR32FG25 Typical Application Circuit: Direct Supply Configuration without DCDC



Figure 5.2. EFR32FG25 Typical Application Circuit: DCDC Configuration


Figure 5.3. EFR32FG25 Typical Application Circuit: DCDC Configuration, USB PHY Powered Separately

Note: IOVDD2 voltage shall be supplied when the system is powered.

5.2 RF Matching Networks

5.2.1 Matching Network for 868, 915, and 920 MHz Bands

The recommended RF matching network circuit schematic for the 868, 915, and 920 MHz bands is shown in Figure 5.4 Typical differential TX and single ended RX RF impedance-matching network circuit for 868, 915, and 920 MHz Bands on page 146. Typical component values optimized for different RF Bands are shown in Table 5.1 RF Matching Component Values for 868, 915, and 920 MHz Bands on page 146. Please refer to the develoment board Bill of Materials for specific part recommendation including tolerance, component size, recommended manufacturer, and recommended part number.



Figure 5.4. Typical differential TX and single ended RX RF impedance-matching network circuit for 868, 915, and 920 MHz Bands

Table 5.1. RF Matching Component Values for 868, 915, and 920 MHz Bands

Designator	Component Value			
	868 MHz	915 & 920 MHz		
LN1 and LP1	1 nH	0.8 nH		
LN2 and LP2	1 nH	0.9 nH		
CN1 and CP1	5.9 pF	5.7 pF		
C2	5.4 pF	4.2 pF		
CN3 and CP3	220 pF	220 pF		
T1	MMCZ1601G7T_0088A1	MMCZ1601G7T_0088A1		
LT1	7.5 nH	7.5 nH		
CT1	4.0 pF	4.4 pF		
CT2	2.6 pF	2.2 pF		

EFR32FG25 Gecko Wireless SoC Family Data Sheet Typical Connection Diagrams

Designator	Component Value		
	868 MHz	915 & 920 MHz	
LR1	18 nH	18 nH	
CR1	DNP	DNP	

5.2.2 Matching Network for 470 MHz Band

The recommended RF matching network circuit schematic for the 470 MHz band is shown in Figure 5.5 Typical differential TX and single ended RX RF impedance-matching network circuit for 470 MHz Band on page 148. Typical component values optimized for different RF Bands are shown in Table 5.2 RF Matching Component Values for 470 MHz Band on page 148. Please refer to the develoment board Bill of Materials for specific part recommendation including tolerance, component size, recommended manufacturer, and recommended part number.





Designator	Component Value
	470 MHz
LN1 and LP1	4.2 nH
LN2 and LP2	16 nH
CN1	18 pF
CP1	20 pF
CN2	9 pF
CP2	7 pF
CN3 and CP3	220 pF
LT1	16 nH
LT2	13 nH
CT1	5.0 pF
CT2	9.5 pF
СТЗ	8.0 pF
LR1	68 nH

Designator	Component Value	
	470 MHz	
CR1	DNP	

5.3 Other Connections

Other components or connections may be required to meet the system-level requirements. Application Note AN0002: "Hardware Design Considerations" contains detailed information on these connections. Application Notes can be accessed on the Silicon Labs website (www.silabs.com/32bit-appnotes).

6. Pin Definitions

6.1 QFN56 / Standard Device Pinout



Figure 6.1. QFN56 / Standard Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 6.3 Alternate Function Table, 6.4 Analog Peripheral Connectivity, and 6.5 Digital Peripheral Connectivity.

Table 6.1.	QFN56 /	Standard	Device	Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PC00	1	GPIO	PC01	2	GPIO
PC02	3	GPIO	PC03	4	GPIO
PC04	5	GPIO	PC05	6	GPIO
PC06	7	GPIO	IOVDD0	8	IOVDD Supply 0
PC07	9	GPIO	PC08	10	GPIO

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PC09	11	GPIO	PC10	12	GPIO
HFXTAL_I	13	High-Frequency Crystal Input	HFXTAL_O	14	High-Frequency Crystal Output
RESETn	15	RESET	RFVDD	16	RFVDD Supply
RFVSS	17	RF Ground	SUBG_I	18	Sub-GHz Input
PAVSS	19	PA Ground	SUBG_OP	20	Sub-GHz Output (Positive)
SUBG_ON	21	Sub-GHz Output (Negative)	PAVDD	22	PAVDD Supply
PB05	23	GPIO	PB04	24	GPIO
PB03	25	GPIO	PB02	26	GPIO
PB01	27	GPIO	PB00	28	GPIO
PA00	29	GPIO	PA01	30	GPIO
PA02	31	GPIO	PA03	32	GPIO
PA04	33	GPIO	PA05	34	GPIO
PA06	35	GPIO	PA07	36	GPIO
PA08	37	GPIO	PA09	38	GPIO
PA10	39	GPIO	PA11	40	GPIO
IOVDD1	41	IOVDD Supply 1	DECOUPLE	42	Decouple Capactor
VREGSW	43	VREG Switch output	VREGVDD	44	VREG Input
VREGVSS	45	DCDC Ground	DVDD	46	Digital DVDD Supply
AVDD	47	Analog AVDD Supply	PD07	48	GPIO
PD06	49	GPIO	IOVDD2	50	IOVDD Supply 2
PD05	51	GPIO	PD04	52	GPIO
PD03	53	GPIO	PD02	54	GPIO
PD01	55	GPIO	PD00	56	GPIO



Figure 6.2. QFN56 / Clock Out Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 6.3 Alternate Function Table, 6.4 Analog Peripheral Connectivity, and 6.5 Digital Peripheral Connectivity.

Table 6.2. QFN56 / Clock Out Device Pine
--

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description	
PC00	1	GPIO	PC01	2	GPIO	
PC02	3	GPIO	PC03	4	GPIO	
PC04	5	GPIO	PC05	6	GPIO	
PC06	7	GPIO	IOVDD0	8	IOVDD Supply 0	
PC07	9	GPIO	PC08	10	GPIO	
PC09	11	GPIO	HFCLKOUT	12	High-Frequency Clock Out	
HFXTAL_I	13	High-Frequency Crystal Input	HFXTAL_O	14	High-Frequency Crystal Output	

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
RESETn	15	RESET	RFVDD	16	RFVDD Supply
RFVSS	17	RF Ground	SUBG_I	18	Sub-GHz Input
PAVSS	19	PA Ground	SUBG_OP	20	Sub-GHz Output (Positive)
SUBG_ON	21	Sub-GHz Output (Negative)	PAVDD	22	PAVDD Supply
PB05	23	GPIO	PB04	24	GPIO
PB03	25	GPIO	PB02	26	GPIO
PB01	27	GPIO	PB00	28	GPIO
PA00	29	GPIO	PA01	30	GPIO
PA02	31	GPIO	PA03	32	GPIO
PA04	33	GPIO	PA05	34	GPIO
PA06	35	GPIO	PA07	36	GPIO
PA08	37	GPIO	PA09	38	GPIO
PA10	39	GPIO	PA11	40	GPIO
IOVDD1	41	IOVDD Supply 1	DECOUPLE	42	Decouple Capactor
VREGSW	43	VREG Switch output	VREGVDD	44	VREG Input
VREGVSS	45	DCDC Ground	DVDD	46	Digital DVDD Supply
AVDD	47	Analog AVDD Supply	PD07	48	GPIO
PD06	49	GPIO	IOVDD2	50	IOVDD Supply 2
PD05	51	GPIO	PD04	52	GPIO
PD03	53	GPIO	PD02	54	GPIO
PD01	55	GPIO	PD00	56	GPIO

6.3 Alternate Function Table

A wide selection of alternate functionality is available for multiplexing to various pins. The following table shows GPIO pins with support for dedicated functions across the different package options.

GPIO	Alternate Functions	QFN56 / Standard Package ¹	QFN56 / Clock Out Package ²
PA01	GPIO.SWCLK	Yes	Yes
PA02	GPIO.SWDIO	Yes	Yes
	GPIO.SWV	Yes	Yes
PA03	GPIO.TDO	Yes	Yes
PAUS	GPIO.TRACEDATA0	Yes	Yes
	LESENSE.EN_0	Yes	Yes
	GPIO.TDI	Yes	Yes
PA04	GPIO.TRACECLK	Yes	Yes
	LESENSE.EN_1	Yes	Yes
	ETAMPDET.ETAMPIN0	Yes	Yes
DAGE	GPIO.TRACEDATA1	Yes	Yes
PA05	GPIO.EM4WU0	Yes	Yes
	LESENSE.EN_2	Yes	Yes
D 400	ETAMPDET.ETAMPOUT0	Yes	Yes
PA06	GPIO.TRACEDATA2	Yes	Yes
PA07	GPIO.TRACEDATA3	Yes	Yes
PA11	GPIO.EM4WU1	Yes	Yes
PB00	VDAC0.CH0_MAIN_OUT	Yes	Yes
5504	GPIO.EM4WU3	Yes	Yes
PB01	VDAC0.CH1_MAIN_OUT	Yes	Yes
PB03	GPIO.EM4WU4	Yes	Yes
PC00	GPIO.EM4WU6	Yes	Yes
PC04	RAC.FEM_DATA0	Yes	Yes
	GPIO.EM4WU7	Yes	Yes
PC05	RAC.FEM_DATA1	Yes	Yes
PC06	RAC.FEM_DATA2	Yes	Yes
	GPIO.EM4WU8	Yes	Yes
PC07	RAC.AUXADC_IN6_SHIM_EN	Yes	Yes
	RAC.FEM_DATA3	Yes	Yes
PC08	RAC.AUXADC_IN8_SHIM_EN	Yes	Yes
	GPIO.THMSW_EN		Yes
PC09	GPIO.THMSW_HALFSWITCH		Yes

Table 6.3. GPIO Alternate Function Table

GPIO	Alternate Functions	QFN56 / Standard Package ¹	QFN56 / Clock Out Package ²
PC10	GPIO.THMSW_EN	Yes	
PCIU	GPIO.THMSW_HALFSWITCH	Yes	
PD00	LFXO.LFXTAL_O	Yes	Yes
PD01	LFXO.LFXTAL_I	Yes	Yes
PD01	LFXO.LF_EXTCLK	Yes	Yes
PD02	GPIO.EM4WU9	Yes	Yes
PD04	ETAMPDET.ETAMPOUT1	Yes	Yes
PD05	ETAMPDET.ETAMPIN1	Yes	Yes
PD05	GPIO.EM4WU10	Yes	Yes
PD06	USB.USB_DPLUS	Yes	Yes
PD07	USB.USB_DMINUS	Yes	Yes

Note:

1. QFN56 / Standard Package includes OPNs EFR32FG25A111F1152IM56-B, EFR32FG25A121F1152IM56-B, EFR32FG25A211F1920IM56-B, EFR32FG25A221F1920IM56-B, EFR32FG25B111F1152IM56-B, EFR32FG25B121F1152IM56-B, EFR32FG25B21F1920IM56-B, and EFR32FG25B221F1920IM56-B

2. QFN56 / Clock Out Package includes OPNs EFR32FG25B212F1920IM56-B and EFR32FG25B222F1920IM56-B

6.4 Analog Peripheral Connectivity

Many analog resources are routable and can be connected to numerous GPIO's. The table below indicates which peripherals are available on each GPIO port. When a differential connection is being used Positive inputs are restricted to the EVEN pins and Negative inputs are restricted to the ODD pins. When a single ended connection is being used positive input is available on all pins. See the device Reference Manual for more details on the ABUS and analog peripherals. Note that some functions may not be available on all device variants.

Table 6.4. ABUS Routing Table

Peripheral	Signal	1	PA	1	РВ		РС		PD
		EVEN	ODD	EVEN	ODD	EVEN	ODD	EVEN	ODD
ACMP0	ANA_NEG	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
	ANA_POS	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
ACMP1	ANA_NEG	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
	ANA_POS	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
IADC0	ANA_NEG	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
	ANA_POS	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
VDAC0	CH0_ABUS_OUT	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
	CH1_ABUS_OUT	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes

6.5 Digital Peripheral Connectivity

Many digital resources are routable and can be connected to numerous GPIO's. The table below indicates which peripherals are available on each GPIO port. Note that some functions may not be available on all device variants.

Table 6.5. DBUS Routing Table

Peripheral.Resource		PC	RT	Т	
	РА	РВ	PC	PD	
ACMP0.DIGOUT	Available	Available	Available	Available	
ACMP1.DIGOUT	Available	Available	Available	Available	
CMU.CLKIN0			Available	Available	
CMU.CLKOUT0			Available	Available	
CMU.CLKOUT1			Available	Available	
CMU.CLKOUT2	Available	Available			
EUSART0.CS	Available	Available			
EUSART0.CTS	Available	Available			
EUSART0.RTS	Available	Available			
EUSART0.RX	Available	Available			
EUSART0.SCLK	Available	Available			
EUSART0.TX	Available	Available			
EUSART1.CS	Available	Available	Available	Available	
EUSART1.CTS	Available	Available	Available	Available	
EUSART1.RTS	Available	Available	Available	Available	
EUSART1.RX	Available	Available	Available	Available	
EUSART1.SCLK	Available	Available	Available	Available	
EUSART1.TX	Available	Available	Available	Available	
EUSART2.CS			Available	Available	
EUSART2.CTS			Available	Available	
EUSART2.RTS			Available	Available	
EUSART2.RX			Available	Available	
EUSART2.SCLK			Available	Available	
EUSART2.TX			Available	Available	
EUSART3.CS	Available	Available			
EUSART3.CTS	Available	Available			
EUSART3.RTS	Available	Available			
EUSART3.RX	Available	Available			
EUSART3.SCLK	Available	Available			
EUSART3.TX	Available	Available			
EUSART4.CS			Available	Available	

Peripheral.Resource		PC	RT	
	РА	РВ	PC	PD
EUSART4.CTS			Available	Available
EUSART4.RTS			Available	Available
EUSART4.RX			Available	Available
EUSART4.SCLK			Available	Available
EUSART4.TX			Available	Available
FRC.DCLK			Available	Available
FRC.DFRAME			Available	Available
FRC.DOUT			Available	Available
HFX00.BUFOUT_REQ_IN_ASYNC	Available	Available		
I2C0.SCL	Available	Available	Available	Available
I2C0.SDA	Available	Available	Available	Available
I2C1.SCL			Available	Available
I2C1.SDA			Available	Available
LESENSE.CH0OUT	Available	Available		
LESENSE.CH1OUT	Available	Available		
LESENSE.CH2OUT	Available	Available		
LESENSE.CH3OUT	Available	Available		
LESENSE.CH4OUT	Available	Available		
LESENSE.CH5OUT	Available	Available		
LESENSE.CH6OUT	Available	Available		
LESENSE.CH7OUT	Available	Available		
LESENSE.CH8OUT	Available	Available		
LESENSE.CH9OUT	Available	Available		
LESENSE.CH10OUT	Available	Available		
LESENSE.CH11OUT	Available	Available		
LESENSE.CH12OUT	Available	Available		
LESENSE.CH13OUT	Available	Available		
LESENSE.CH14OUT	Available	Available		
LESENSE.CH15OUT	Available	Available		
LETIMER0.OUT0	Available	Available		
LETIMER0.OUT1	Available	Available		
MODEM.ANT0	Available	Available	Available	Available
MODEM.ANT1	Available	Available	Available	Available
MODEM.ANT_ROLL_OVER			Available	Available
MODEM.ANT_RR0			Available	Available
MODEM.ANT_RR1			Available	Available

Peripheral.Resource			PORT		
	PA	РВ	PC	PD	
MODEM.ANT_RR2			Available	Available	
MODEM.ANT_RR3			Available	Available	
MODEM.ANT_RR4			Available	Available	
MODEM.ANT_RR5			Available	Available	
MODEM.ANT_SW_EN			Available	Available	
MODEM.ANT_SW_US			Available	Available	
MODEM.ANT_TRIG			Available	Available	
MODEM.ANT_TRIG_STOP			Available	Available	
MODEM.DCLK	Available	Available			
MODEM.DIN	Available	Available			
MODEM.DOUT	Available	Available			
PCNT0.S0IN	Available	Available			
PCNT0.S1IN	Available	Available			
PRS.ASYNCH0	Available	Available			
PRS.ASYNCH1	Available	Available			
PRS.ASYNCH2	Available	Available			
PRS.ASYNCH3	Available	Available			
PRS.ASYNCH4	Available	Available			
PRS.ASYNCH5	Available	Available			
PRS.ASYNCH6			Available	Available	
PRS.ASYNCH7			Available	Available	
PRS.ASYNCH8			Available	Available	
PRS.ASYNCH9			Available	Available	
PRS.ASYNCH10			Available	Available	
PRS.ASYNCH11			Available	Available	
PRS.SYNCH0	Available	Available	Available	Available	
PRS.SYNCH1	Available	Available	Available	Available	
PRS.SYNCH2	Available	Available	Available	Available	
PRS.SYNCH3	Available	Available	Available	Available	
TIMER0.CC0	Available	Available	Available	Available	
TIMER0.CC1	Available	Available	Available	Available	
TIMER0.CC2	Available	Available	Available	Available	
TIMER0.CDTI0	Available	Available	Available	Available	
TIMER0.CDTI1	Available	Available	Available	Available	
TIMER0.CDTI2	Available	Available	Available	Available	
TIMER1.CC0	Available	Available	Available	Available	

Peripheral.Resource	PORT			
	РА	РВ	PC	PD
TIMER1.CC1	Available	Available	Available	Available
TIMER1.CC2	Available	Available	Available	Available
TIMER1.CDTI0	Available	Available	Available	Available
TIMER1.CDTI1	Available	Available	Available	Available
TIMER1.CDTI2	Available	Available	Available	Available
TIMER2.CC0	Available	Available		
TIMER2.CC1	Available	Available		
TIMER2.CC2	Available	Available		
TIMER2.CDTI0	Available	Available		
TIMER2.CDTI1	Available	Available		
TIMER2.CDTI2	Available	Available		
TIMER3.CC0			Available	Available
TIMER3.CC1			Available	Available
TIMER3.CC2			Available	Available
TIMER3.CDTI0			Available	Available
TIMER3.CDTI1			Available	Available
TIMER3.CDTI2			Available	Available
TIMER4.CC0	Available	Available		
TIMER4.CC1	Available	Available		
TIMER4.CC2	Available	Available		
TIMER4.CDTI0	Available	Available		
TIMER4.CDTI1	Available	Available		
TIMER4.CDTI2	Available	Available		
TIMER5.CC0			Available	Available
TIMER5.CC1			Available	Available
TIMER5.CC2			Available	Available
TIMER5.CDTI0			Available	Available
TIMER5.CDTI1			Available	Available
TIMER5.CDTI2			Available	Available
TIMER6.CC0	Available	Available		
TIMER6.CC1	Available	Available		
TIMER6.CC2	Available	Available		
TIMER6.CDTI0	Available	Available		
TIMER6.CDTI1	Available	Available		
TIMER6.CDTI2	Available	Available		
TIMER7.CC0			Available	Available

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Peripheral.Resource	PORT				
	РА	РВ	PC	PD	
TIMER7.CC1			Available	Available	
TIMER7.CC2			Available	Available	
TIMER7.CDTI0			Available	Available	
TIMER7.CDTI1			Available	Available	
TIMER7.CDTI2			Available	Available	
USB.USB_VBUS_SENSE	Available	Available	Available	Available	

7. QFN56 Package Specifications

7.1 QFN56 Package Dimensions





Dimension	Min	Тур	Мах	
A	0.80	0.85	0.90	
A1	0.00	0.02	0.05	
A3		0.20 REF		
b	0.15	0.20	0.25	
D	6.90	7.00	7.10	
E	6.90	7.00	7.10	
D2	4.60	4.70	4.80	
E2	4.60	4.70	4.80	
е	0.40 BSC			
L	0.30	0.40	0.50	
К	0.20	_	_	
R	0.075		0.125	
ааа	0.10			
bbb	0.07			
ССС	0.10			
ddd	0.05			
eee	0.08			
fff	0.10			
Note:	•			

Table 7.1. QFN56 Package Dimensions

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.

2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.

3. This drawing conforms to the JEDEC Solid State Outline MO-247.

4. Recommended card reflow profile is per the JEDEC J-STD-020C specification for small body, lead-free components.

7.2 QFN56 PCB Land Pattern



Figure 7.2. QFN56 PCB Land Pattern Drawing

Table 7.2. QFN5	6 PCB Land Patterr	Dimensions
-----------------	--------------------	------------

Dimension	Тур
C1	6.87
C2	6.87
W1	4.80
L1	4.80
e	0.40
L	0.86
W	0.22
R	0.11

EFR32FG25 Gecko Wireless SoC Family Data Sheet QFN56 Package Specifications

Dimension	Тур			
Note:				
1. All dimensions shown are in millimeters (mm) unless otherwise	noted.			
2. Dimensioning and Tolerancing is per the ANSI Y14.5M-1994 specification.				
3. This Land Pattern Design is based on the IPC-SM-782 guidelines.				
 All dimensions shown are at Maximum Material Condition (MM cation Allowance of 0.05 mm. 	C). Least Material Condition (LMC) is calculated based on a Fabri-			
 All pads are to be non-solder mask defined (NSMD). Clearance mum, all the way around the pad. 	e between the solder mask and the metal pad is to be 60 μm mini-			
6. A stainless steel, laser-cut and electro-polished stencil with tra	bezoidal walls should be used to assure good solder paste release.			
7. The stencil thickness should be 0.100 mm (4 mils).				

- 8. The ratio of stencil aperture to land pad size should be 1:1 for the perimeter pads.
- 9. A No-Clean, Type-3 solder paste is recommended.
- 10. The recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.
- 11. Above notes and stencil design are shared as recommendations only. A customer or user may find it necessary to use different parameters and fine tune their SMT process as required for their application and tooling.

7.3 QFN56 Package Marking



Figure 7.3. QFN56 Package Marking

The package marking consists of:

- · FFFF The product family codes.
 - 1. Family Code (F)
 - 2. G (Gecko)
 - 3. Series (2)
 - 4. Device Configuration (5)
- PPPPP The product option codes.
 - 1. Security (A = Secure Vault Mid | B = Secure Vault High)
 - 2-4. Product Feature Codes
 - 5. Flash (U = 1920k | T = 1152k)
 - 6. Temperature grade (I = -40 to 125 °C)
- TTTTTT A trace or manufacturing code. The first letter is the device revision.
- YY The last 2 digits of the assembly year.
- WW The 2-digit workweek when the device was assembled.

8. Revision History

Revision 1.0

January, 2023

- Entered min/max specs values for TBDs
- Added new specs for different testing conditions

Revision 0.5

December, 2022

Entered typical spec values for TBDs

Revision 0.43

October, 2022

- · Changed tests in 490 MHz Band RF SUN OFDM Transmitter Characteristics table
- · Updated the detailed block diagram
- Updated Package Marking
- · Changed test conditions
- Entered typical spec values for TBDs
- Removed Thermistor Driver Spec Table
- · Added typical performance curves

Revision 0.42

October, 2022

· Entered typical spec values for TBDs

Revision 0.41

September, 2022

- Entered typical spec values for TBDs
- · Removed some tests
- · Removed O-QPSK tables

Revision 0.4

September, 2022

- Added OPN Decoder
- Changed test conditions
- Entered typical spec values for TBDs
- · Renamed test symbol
- Added matching network for 470 MHz

Revision 0.3

June, 2022

- Clarify test conditions
- · Update tested parameters
- Include Crypto Operation Characterization

Revision 0.2

January, 2022

- · Changed Test Conditions and footnotes for several specifications to correct errors and clarify
- · Changed Operating Conditions to be more clear
- Updated some security system details
- Changed Typical Connection Diagrams and matching network
- Corrected errors

Revision 0.1

July, 2021

Initial release.

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